e·MMC™ and Mobile LPDDR 153-Ball MCP

MT29KZZZ4D4RGFAK-5 W.6Y4

Features

- Micron® *e*·MMC and LPDDR components
- MLC NAND in *e*·MMC
- RoHS-compliant, "green" package
- Separate *e*·MMC and LPDDR interfaces
- Space-saving multichip package
- Low-voltage operation V_{DD} (1.70–1.95V)
- Dual voltage V_{CCQM} (1.70–1.95V, 2.7–3.6V)
- Wireless temperature range: –25°C to +85°C

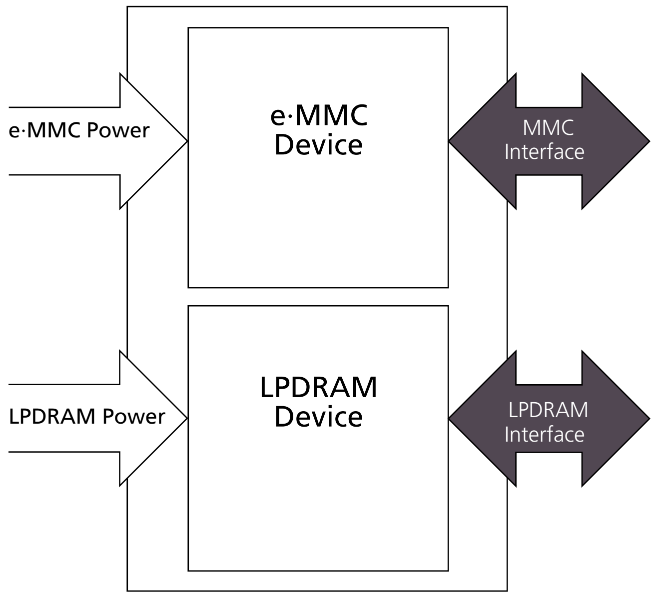
e·MMC-Specific Features

MMC System Specification Version 4.41-compliant (JEDEC Standard No. 84-A441) - SPI mode not supported [1]

- Advanced 11-signal interface
- x1, x4, and x8 I/Os, selectable by host
- MMC mode operation
- Command classes:
  - Class 0 (basic)
  - Class 2 (block read)
  - Class 4 (block write)
  - Class 5 (erase)
  - Class 6 (write protection)
  - Class 7 (lock card)
- MMC*plus*™ and MMC*mobile*™ protocols
- Temporary write protection
- 52 MHz clock speed (MAX)
- Boot operation (high-speed boot)
- Sleep mode
- Reliable WRITE
- Replay-protected memory block (RPMB)
- Secure erase and trim
- Hardware reset signal
- Multiple partitions with enhanced attribute
- Permanent and power-on write protection
- Backward-compatible with previous MMC modes

Note: 1. The JEDEC specification is available at www.jedec.org/sites/default/files/docs/JESD84-A441.pdf.

Figure 1: MCP Block Diagram



Mobile LPDDR-Specific Features

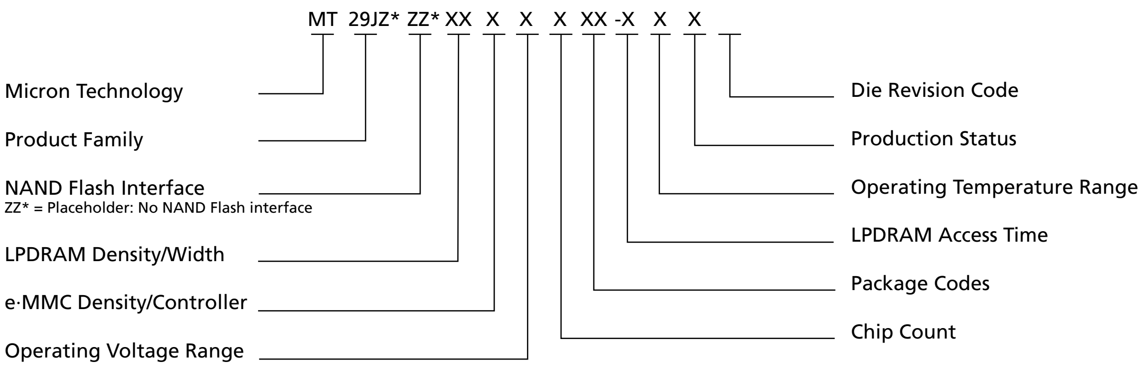
- No external voltage reference required
- No minimum clock rate requirement
- 1.8V LVCMOS-compatible inputs
- Programmable burst lengths
- Partial-array self refresh (PASR)
- Deep power-down (DPD) mode
- Selectable output drive strength
- STATUS REGISTER READ (SRR) supported[1]

Notes: 1. Contact factory for remapped SRR output.
2. For physical part markings, see Part Numbering Information (page 2).

Part Numbering Information

Micron *e*·MMC and LPDRAM devices are available in different configurations and densities. The MCP/PoP part numbering guide is available at www.micron.com/numbering.

Figure 2: Part Number Chart



Device Marking

Due to the size of the package, the Micron-standard part number is not printed on the top of the device. Instead, an abbreviated device mark consisting of a 5-digit alphanumeric code is used. The abbreviated device marks are cross-referenced to the Micron part numbers at the FBGA Part Marking Decoder site: www.micron.com/decoder. To view the location of the abbreviated mark on the device, refer to customer service note CSN-11, “Product Mark/ Label,” at www.micron.com/csn.

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MCP General Description

Micron MCP products combine *e*·MMC and Mobile LPDRAM devices in a single MCP. These products target mobile applications with low-power, high-performance, and minimal package-footprint design requirements. The NAND Flash and Mobile LPDRAM devices are also members of the Micron discrete memory products portfolio.

The *e*·MMC and Mobile LPDRAM devices are packaged with separate interfaces (no shared address, control, data, or power balls). This bus architecture supports an optimized interface to processors with separate *e*·MMC and Mobile LPDRAM buses. The *e*·MMC and Mobile LPDRAM devices have separate core power connections and share a common ground (that is, V_{SS} is tied together on the two devices).

The bus architecture of this device also supports separate *e*·MMC and Mobile LPDRAM functionality without concern for device interaction.

Ball Assignments and Descriptions

Figure 3: 153-Ball FBGA (e·MMC x4; LPDDR x32) Ball Assignments

	1	2	3	4	5	6	7	8	9	10	11	12	13	14
A	DNU	NC	DAT0	DAT1	DAT2	NC	NC	V_{DDQ}	V_{SSQ}	V_{SS}	V_{DD}	V_{SSQ}	NC	DNU
B	NC	DAT3	DAT4	DAT5	DAT6	DAT7	DQ30	DQ28	DQ26	DQ24	DQS3	DQ23	V_{DDQ}	NC
C	V_{SS}	V_{DDIM}	A4	V_{SSQM}	NC	V_{CCQM}	DQ31	DQ29	DQ27	DQ25	DM3	DQ22	DQ21	V_{DDQ}
D	A5	A6	A7	TQ								DQ19	DQ20	V_{SSQ}
E	A12	A11	A8		NC	V_{CCM}	V_{SS}	NC	NC	NC		DQ18	DQ17	DQ16
F	V_{DD}	A13	A9		V_{CCM}					NC		DQS2	DM2	V_{SSQ}
G	CKE0	CS0#	RFU		V_{SS}					NC		CK	V_{DDQ}	V_{DD}
H	V_{DDQ}	RAS#	WE#		NC					V_{SS}		CK#	V_{DDQ}	V_{SS}
J	CKE1	CAS#	CS1#		NC					V_{CCM}		DQS1	DM1	V_{SSQ}
K	BA1	V_{SS}	A10		RSTn	NC	NC	V_{SS}	V_{CCM}	NC		DQ13	DQ14	DQ15
L	BA0	A0	A1									DQ11	DQ12	V_{SSQ}
M	V_{SS}	V_{DD}	A2	V_{CCQM}	CMD	CLK	DQ1	DQ3	DQ5	DQ7	DM0	DQ9	DQ10	V_{DDQ}
N	NC	V_{SSQM}	A3	V_{CCQM}	V_{SSQM}	V_{SSQ}	DQ0	DQ2	DQ4	DQ6	DQS0	DQ8	V_{DDQ}	NC
P	DNU	NC	V_{CCQM}	V_{SSQM}	V_{CCQM}	V_{SSQM}	NC	V_{DDQ}	V_{SSQ}	NC	V_{DD}	V_{SSQ}	NC	DNU

Top View – Ball Down

LPDDR   e·MMC   Supply   Ground

Table 1: LPDDR Ball Descriptions

Symbol	Type	Description
A[13:0]	Input	Address inputs: Specifies the row or column address. Also used to load the mode registers. The maximum LPDDR address is determined by density and configuration. Consult the LPDDR product data sheet for the maximum address for a given density and configuration. Unused address balls become RFU.[1]
BA0, BA1	Input	Bank address inputs: Specifies one of the 4 banks.
CAS#	Input	Column select: Specifies which command to execute.
CK, CK#	Input	CK is the system clock. CK and CK# are differential clock inputs. All address and control signals are sampled and referenced on the crossing of the rising edge of CK with the falling edge of CK#.
CKE0, CKE1	Input	Clock enable. CKE0 is used for a single LPDDR product. CKE1 is used for dual LPDDR products and is considered RFU for single LPDDR MCPs.
CS0#, CS1#	Input	Chip select: CS0# is used for a single LPDDR product. CS1# is used for dual LPDDR products and is considered RFU for single LPDDR MCPs.
DM[3:0]	Input	Data mask: Determines which bytes are written during WRITE operations.
RAS#	Input	Row select: Specifies the command to execute.
WE#	Input	Write enable: Specifies the command to execute.
DQ[31:0]	Input/ output	Data bus: Data inputs/outputs. DQ[31:16] are RFU for x16 LPDDR devices.
DQS[3:0]	Input/ output	Data strobe: Coordinates READ/WRITE transfers of data; one DQS per DQ byte. For x16 LPDDR, unused DQS balls become RFU.
TQ	Output	Temperature sensor output: TQ HIGH when LPDDR T_J exceeds 85°C.
V_{DD}	Supply	V_{DD}: LPDDR power supply.
V_{DDQ}	Supply	V_{DDQ}: LPDDR I/O power supply.
V_{SSQ}	Supply	V_{SSQ}: LPDDR I/O ground.

Note: 1. Balls marked RFU may or may not be connected internally. These balls should not be used. Contact factory for details.

Table 2: e·MMC Ball Descriptions

Symbol	Type	Description
CLK	Input	Clock: Each cycle directs a 1-bit transfer on the command and DAT lines.
CMD	Input	Command: A bidirectional channel used for device initialization and command transfers. Command has two operating modes: 1) Open drain for initialization. 2) Push-pull for fast command transfer.
DAT[7:0]	Input	Data bus: Bidirectional channel used for data transfer.
RSTn	Input	Reset
V_{CCM}	Supply	V_{CCM}: NAND I/F I/O and NAND power supply (2.7–3.6V).
V_{CCQM}	Supply	V_{CCQM}: e·MMC controller core and e·MMC I/F I/O power supply (1.70–1.95V or 2.7–3.6V).
V_{SSQM}	Supply	V_{SSQM}: e·MMC controller core and e·MMC I/F ground connection.
V_{DDIM}	–	V_{DDIM}: Connect 0.1µF (MIN) capacitor from V_{DDIM} to ground. Use of a 1µF capacitor is recommended.

Table 3: Non-Device-Specific Descriptions

Symbol	Type	Description
V_{SS}	Supply	V_{SS}: Shared ground.
Symbol	**Type**	**Description**
DNU	–	Do not use: Must be grounded or left floating.
NC	–	No connect: Not internally connected.
RFU[1]	–	Reserved for future use.

Note: 1. Balls marked RFU may or may not be connected internally. These balls should not be used. Contact factory for details.

Electrical Specifications

Table 4: Absolute Maximum Ratings

Parameters/Conditions	Symbol	Min	Max	Unit
V_{DD}, V_{DDQ} supply voltage relative to V_{SS}	V_{DD}, V_{DDQ}	–1.0	2.4	V
V_{CC}, V_{CCQ} supply voltage relative to V_{SS}	V_{CCM}, V_{CCQM}	–0.5	3.6	V
Voltage on any pin relative to V_{SS}	V_{IN}	–0.5	2.4 or (supply voltage[1] + 0.3V), whichever is less	V
Storage temperature range	–	–40	+85	°C

Note: 1. Supply voltage references V_{DDQ} or V_{CCQM}.

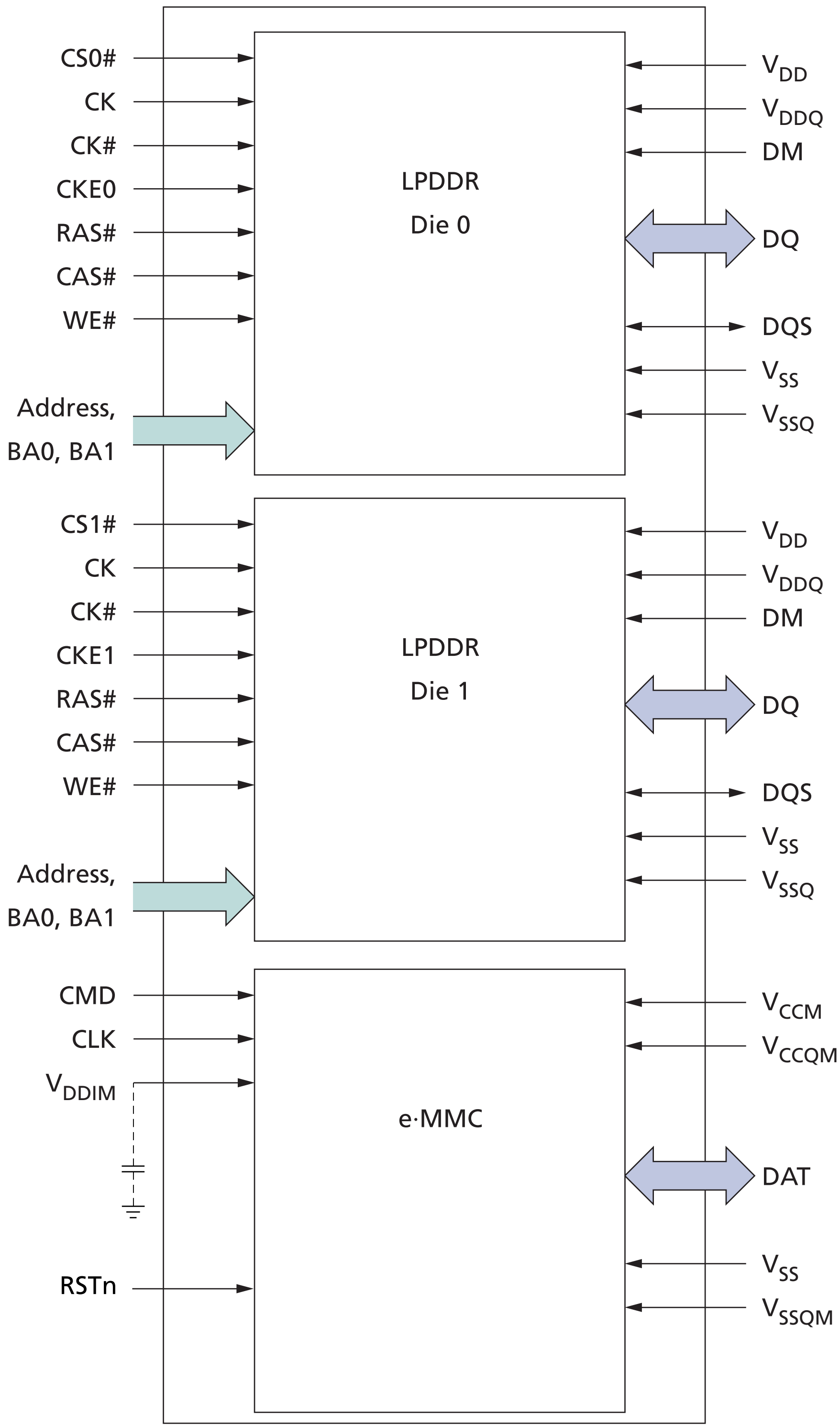
Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Table 5: Recommended Operating Conditions

Parameters	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{DD}	1.70	1.80	1.95	V
	V_{CCM}	2.70	–	3.6	V
I/O supply voltage	V_{DDQ}	1.70	1.80	1.95	V
	V_{CCQM}	1.65	–	1.95	V
		2.70	–	3.60	V
Operating temperature range	–	–25	–	+85	°C

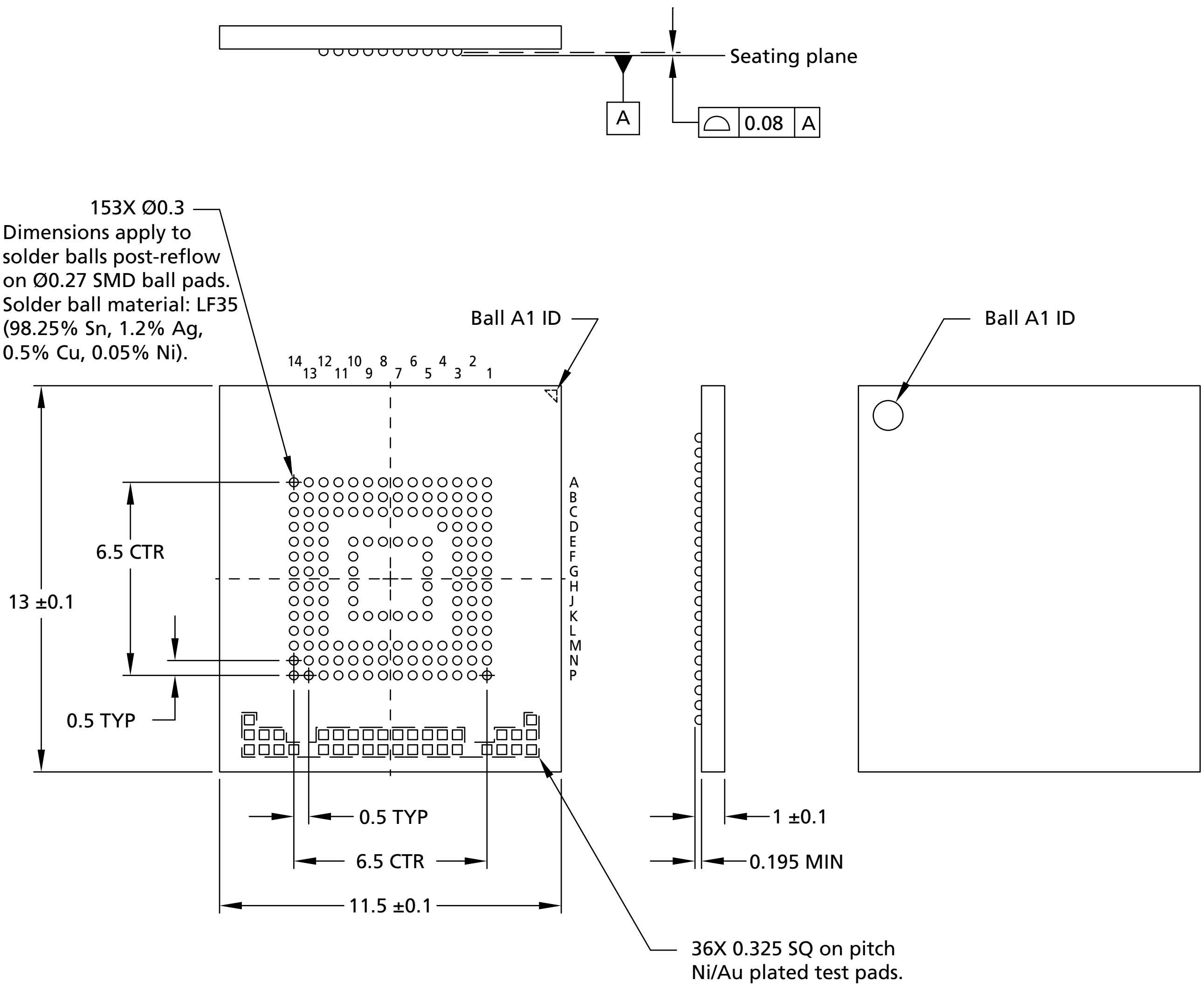
Device Diagrams

Figure 4: 153-Ball Functional Block Diagram



Package Dimensions

Figure 5: 153-Ball VFBGA (Package Code: AK)



Note: 1. All dimensions are in millimeters.

MLC e·MMC

General Description

Micron *e*·MMC is a communication and mass data storage device that includes a MultiMediaCard (MMC) interface, a NAND Flash component, and a controller on an advanced 11-signal bus, which is compliant with the MMC system specification. Its low cost, small size, Flash technology independence, and high data throughput make *e*·MMC ideal for smart phones, digital cameras, PDAs, MP3 players, and other portable applications.

The nonvolatile *e*·MMC draws no power to maintain stored data, delivers high performance across a wide range of operating temperatures, and resists shock and vibration disruption.

Architecture

MMC Protocol Independent of NAND Flash Technology

The MMC specification defines the communication protocol between a host and a device. The protocol is independent of the NAND Flash features included in the device. The device has an intelligent on-board controller that manages the MMC communication protocol.

The controller also handles block management functions such as logical block allocation and wear leveling. These management functions require complex algorithms and depend entirely on NAND Flash technology (generation or memory cell type).

The device handles these management functions internally, making them invisible to the host processor.

Defect and Error Management

Micron *e*·MMC incorporates advanced technology for defect and error management. If a defective block is identified, the device completely replaces the defective block with one of the spare blocks. This process is invisible to the host and does not affect data space allocated for the user.

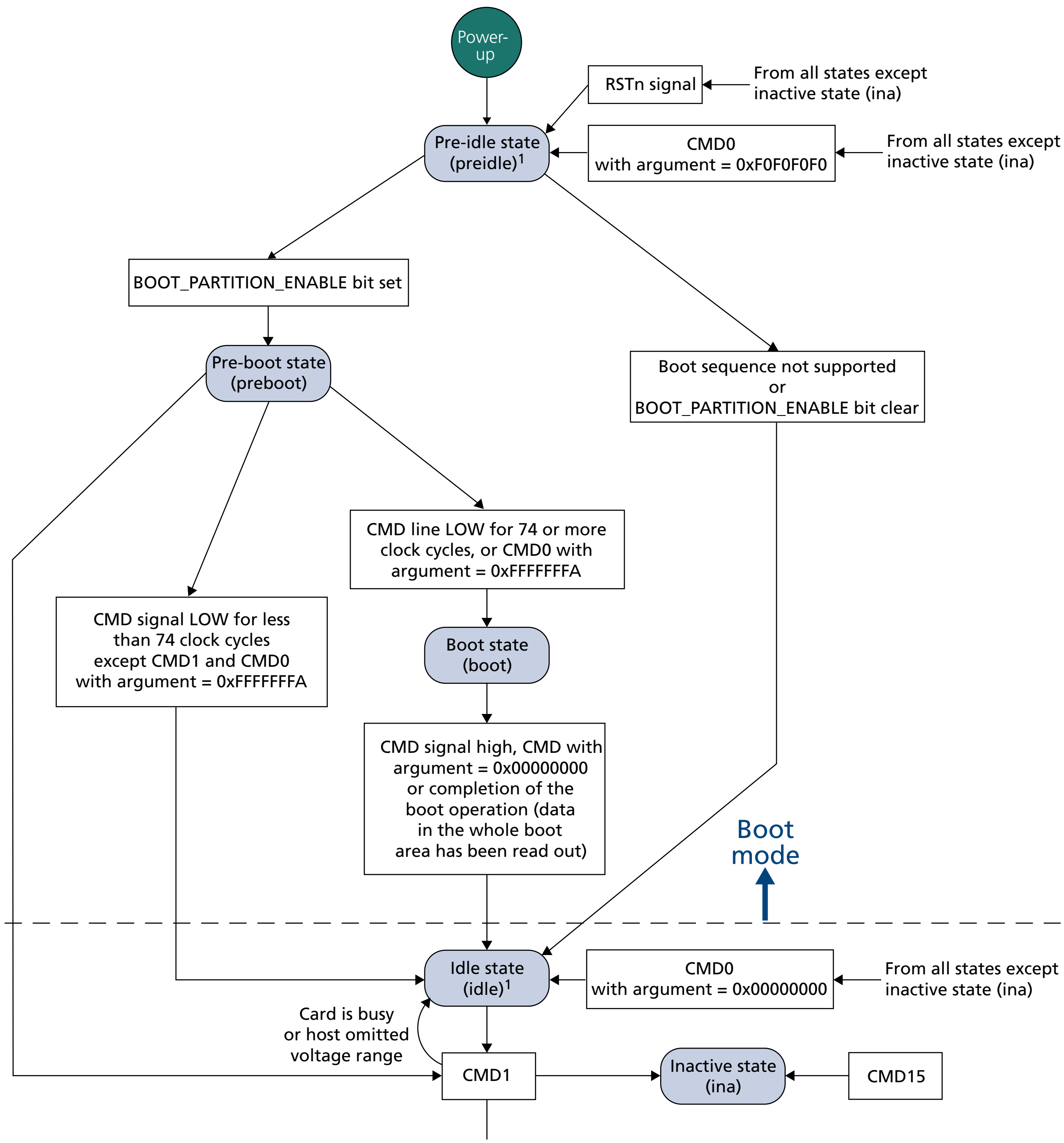
The device also includes a built-in error correction code (ECC) algorithm to ensure that data integrity is maintained.

To make the best use of these advanced technologies and ensure proper data loading and storage over the life of the device, the host must exercise the following precautions:

- Check the status after WRITE, READ, and ERASE operations.
- Avoid power-down during WRITE and ERASE operations.

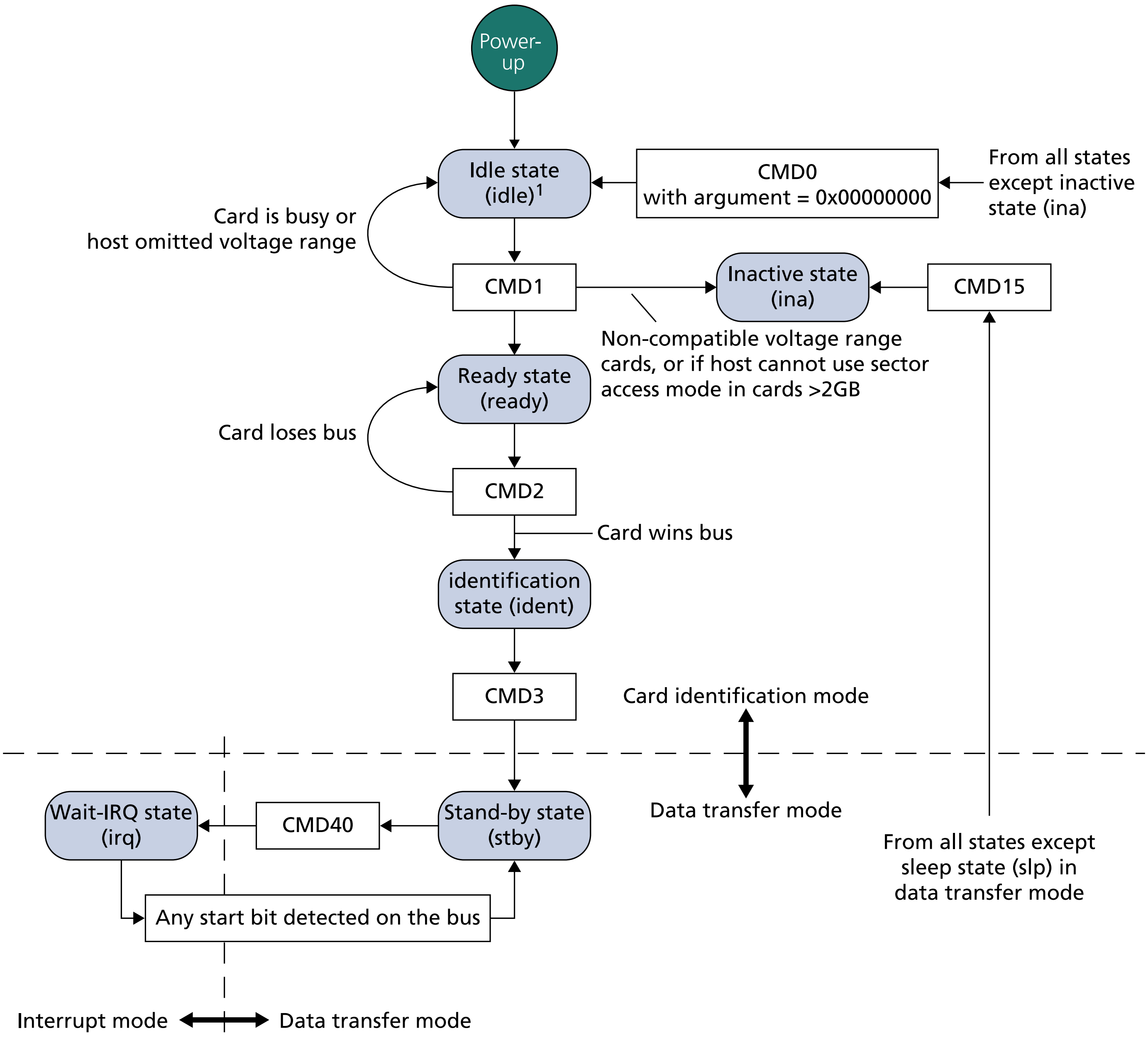
State Diagrams

Figure 6: Boot Mode



Note: 1. When the part is in idle or pre-idle state, any invalid command may show ILLEGAL_COMMAND in the status register on the first command with R1 response. For example, CMD55 may cause a CMD3 response to show an illegal command status during the initialization sequence.

Figure 7: Card Identification Mode



Note: 1. When the part is in idle or pre-idle state, any invalid command may show ILLEGAL_COMMAND in the status register on the first command with R1 response. For example, CMD55 may cause a CMD3 response to show an illegal command status during the initialization sequence.

Figure 8: Interrupt Mode

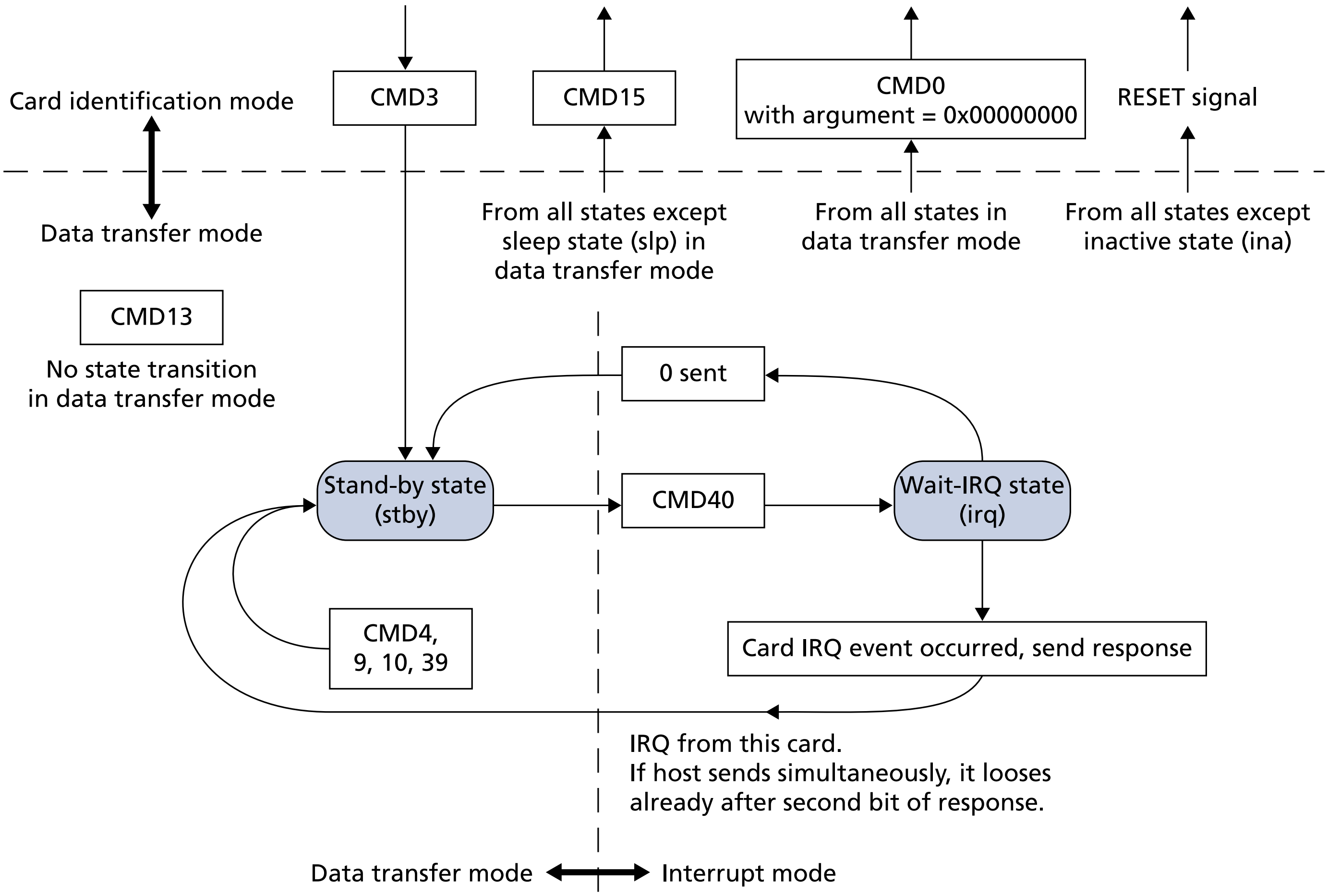
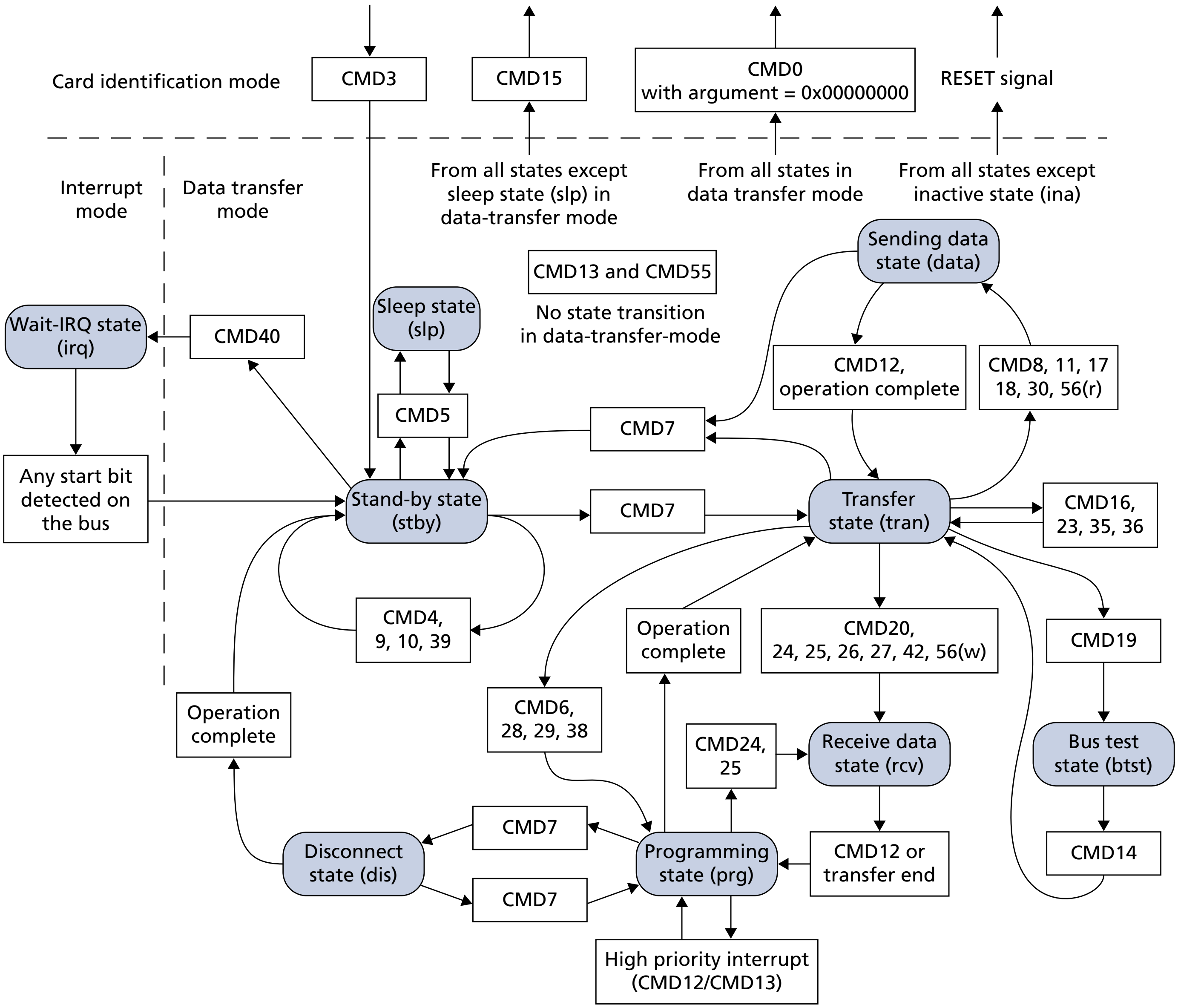


Figure 9: Data Transfer Mode



CID Register

The card identification (CID) register is 128 bits wide. It contains the device identification information used during the card identification phase as required by *e*·MMC protocol. Each device is created with a unique identification number.

Table 6: CID Register Field Parameters

Name	Field	Width	CID Bits	CID Value	Notes
Manufacturer ID	MID	8	[127:120]	0x13	
Reserved	–	6	[119:114]	–	
Card/BGA	CBX	2	[113:112]	01	
OEM/application ID	OID	8	[111:104]	–	1
Product name	PNM	48	[103:56]	0x005265762e52	2
Product revision	PRV	8	[55:48]	–	3
Product serial number	PSN	32	[47:16]	–	4
Manufacturing date	MDT	8	[15:8]	–	1
CRC7 checksum	CRC	7	[7:1]	–	1
Not used; always 1	–	1	0	–	

Notes:
1. Description is the same as e·MMC JEDEC standard.
2. Product name of "<NUL>Rev.R".
3. PRV is composed of the revision count of controller and the revision count of firmware patch.
4. A 32-bit unsigned binary integer (random number).

CSD Register

The card-specific data (CSD) register provides information about accessing the device contents. The CSD register defines the data format, error correction type, maximum data access time, and data transfer speed, as well as whether the DS register can be used. The programmable part of the register (entries marked with W or E in the following table) can be changed by the PROGRAM_CSD (CMD27) command.

Table 7: CSD Register Field Parameters

Name	Field	Width	Cell Type[1]	CSD Bits	CSD Value	Value Description
CSD structure	CSD_STRUCTURE	2	R	[127:126]	3h	Refer to EXT_CSD
System specification version	SPEC_VERS	4	R	[125:122]	4h	Version 4.4
Reserved[2]	–	2	–	[121:120]	–	–
Data read access time 1	TAAC	8	R	[119:112]	5Fh	50ms
Data read access time 2 in CLK cycles (NSAC × 100)	NSAC	8	R	[111:104]	01h	100
Maximum bus clock frequency	TRAN_SPEED	8	R	[103:96]	32h	26 MHz
Card command classes	CCC	12	R	[95:84]	0F5h	0, 2, 4, 5, 6, 7
Maximum read data block length	READ_BL_LEN	4	R	[83:80]	9h	512 bytes
Partial blocks for reads supported	READ_BL_PARTIAL	1	R	79	0b	No
Write block misalignment	WRITE_BLK_MISALIGN	1	R	78	0b	No
Read block misalignment	READ_BLK_MISALIGN	1	R	77	0b	No
DS register implemented	DSR_IMP	1	R	76	0b	No
Reserved	–	2	–	[75:74]	–	–
Device size:	C_SIZE	12	R	[73:62]	FFFh	>2GB
Maximum read current at $V_{DD,min}$	VDD_R_CURR_MIN	3	R	[61:59]	6h	60mA
Maximum read current at $V_{DD,max}$	VDD_R_CURR_MAX	3	R	[58:56]	6h	80mA
Maximum write current at $V_{DD,min}$	VDD_W_CURR_MIN	3	R	[55:53]	6h	60mA
Maximum write current at $V_{DD,max}$	VDD_W_CURR_MAX	3	R	[52:50]	6h	80mA
Device size multiplier	C_SIZE_MULT	3	R	[49:47]	7h	>2GB
Erase group size	ERASE_GRP_SIZE	5	R	[46:42]	1Fh	32
Erase group size multiplier	ERASE_GRP_MULT	5	R	[41:37]	1Fh	32
Write protect group size	WP_GRP_SIZE 4GB, 8GB	5	R	[36:32]	07h	8
Write protect group enable	WP_GRP_ENABLE	1	R	31	1b	Yes
Manufacturer default ECC	DEFAULT_ECC	2	R	[30:29]	0h	None
Write-speed factor	R2W_FACTOR	3	R	[28:26]	2h	4
Maximum write data block length	WRITE_BL_LEN	4	R	[25:22]	9h	512 bytes
Partial blocks for writes supported	WRITE_BL_PARTIAL	1	R	21	0b	No
Reserved	–	4	–	[20:17]	–	

Table 7: CSD Register Field Parameters (Continued)

Name	Field	Width	Cell Type[1]	CSD Bits	CSD Value	Value Description
Content protection application	CONTENT_PROT_APP	1	R	16	0b	Not supported
File-format group	FILE_FORMAT_GRP	1	R/W	15	0b	HDD-like file system
Copy flag (OTP)	COPY	1	R/W	14	1b	Copy
Permanent write protection	PERM_WRITE_PROTECT	1	R/W	13	0b	No
Temporary write protection	TMP_WRITE_PROTECT	1	R/W/E	12	0b	No
File format	FILE_FORMAT	2	R/W	[11:10]	0b	HDD-like file system
ECC	ECC	2	R/W/E	[9:8]	0h	None
CRC	CRC	7	R/W/E	[7:1]		
Not used; always 1	–	1	–	0	1b	1

Notes: 1. R = Read-only

R/W = One-time programmable and readable

R/W/E = Multiple writable with value kept after a power cycle, assertion of the RST_n signal, and any CMD0 reset, and readable

TBD = To be determined

2. Reserved bits should be read as 0.

ECSD Register

The 512-byte extended card-specific data (ECSD) register defines device properties and selected modes. The most significant 320 bytes are the properties segment. This segment defines device capabilities and cannot be modified by the host. The lower 192 bytes are the modes segment. The modes segment defines the configuration in which the device is working. The host can change the properties of modes segments using the SWITCH command.

Table 8: ECSD Register Field Parameters

Name		Field	Size (Bytes)	Cell Type[1]	ECSD Bytes	ECSD Value
Properties Segment						
Reserved[2]		–	7	–	[511:505]	–
Supported command sets		S_CMD_SET	1	R	504	1h
HPI features		HPI_FEATURES	1	R	503	3h
Background operations support		BKOPS_SUPPORT	1	R	502	1h
Reserved[2]		–	255	–	[501:247]	–
Background operations status		BKOPS_STATUS	1	R	246	–
Number of correctly programmed sectors		CORRECTLY_PRG_ SECTORS_NUM	4	R	[245:242]	–
First initialization time after partitioning (first CMD1 to device ready)		INI_TIMEOUT_AP	1	R	241	14h
Reserved[2]		–	1	–	240	–
Power class for 52 MHz, DDR at 3.6V		PWR_CL_DDR_52_360	1	R	239	0h
Power class for 52 MHz, DDR at 1.95V		PWR_CL_DDR_52_195	1	R	238	0h
Reserved[2]		–	2	–	[237:236]	–
Minimum write performance for 8-bit at 52 MHz in DDR mode		MIN_PERF_DDR_W_8_52	1	R	235	08h
Minimum read performance for 8-bit at 52 MHz in DDR mode		MIN_PERF_DDR_R_8_52	1	R	234	08h
Reserved[2]		–	1	–	233	–
TRIM multiplier		TRIM_MULT	1	R	232	1h
Secure feature support		SEC_FEATURE_SUPPORT	1	R	231	15h
SECURE ERASE multiplier		SEC_ERASE_MULT	1	R	230	20h
SECURE TRIM multiplier		SEC_TRIM_MULT	1	R	229	84h
Boot information		BOOT_INFO	1	R	228	7h
Reserved[2]		–	1	–	227	–
Boot partition size		BOOT_SIZE_MULT	1	R	226	10h
Access size	4GB, 8GB	ACC_SIZE	1	R	225	6h
High-capacity erase unit size	4GB, 8GB	HC_ERASE_GP_SIZE	1	R	224	8h
High-capacity erase timeout		ERASE_TIMEOUT_MULT	1	R	223	1h
Reliable write-sector count		REL_WR_SEC_C	1	R	222	1h

Table 8: ECSD Register Field Parameters (Continued)

Name		Field	Size (Bytes)	Cell Type[1]	ECSD Bytes	ECSD Value
High-capacity write protect group size	4GB, 8GB	HC_WP_GRP_SIZE	1	R	221	8h
Sleep current (V_{CC})	4GB, 8GB	S_C_VCC	1	R	220	7h
Sleep current (V_{CCQ})		S_C_VCCQ	1	R	219	06h
Reserved[2]		–	1	–	218	–
Sleep/awake timeout		S_A_TIMEOUT	1	R	217	10h
Reserved[2]		–	1	–	216	–
Sector count	4GB, 8GB	SEC_COUNT	4	R	[215:212]	748000h, EA8000h
Reserved[2]		–	1	–	211	–
Minimum write performance for 8-bit at 52 MHz		MIN_PERF_W_8_52	1	R	210	08h
Minimum read performance for 8-bit at 52 MHz		MIN_PERF_R_8_52	1	R	209	08h
Minimum write performance for 8-bit at 26 MHz and 4-bit at 52 MHz		MIN_PERF_W_8_26_4_52	1	R	208	08h
Minimum read performance for 8-bit at 26 MHz and 4-bit at 52 MHz		MIN_PERF_R_8_26_4_52	1	R	207	08h
Minimum write performance for 4-bit at 26 MHz		MIN_PERF_W_4_26	1	R	206	08h
Minimum read performance for 4-bit at 26 MHz		MIN_PERF_R_4_26	1	R	205	08h
Reserved[2]		–	1	–	204	–
Power class for 26 MHz at 3.6V		PWR_CL_26_360	1	R	203	00h
Power class for 52 MHz at 3.6V		PWR_CL_52_360	1	R	202	00h
Power class for 26 MHz at 1.95V		PWR_CL_26_195	1	R	201	00h
Power class for 52 MHz at 1.95V		PWR_CL_52_195	1	R	200	00h
Partition switching timing		PARTI-TION_SWITCH_TIME	1	R	199	1h
Out-of-interrupt busy timing		OUT_OF_INTER-RUPT_TIME	1	R	198	1h
Reserved[2]		–	1	–	197	–
Card type		CARD_TYPE	1	R	196	7h
Reserved		–	1	–	195	–
CSD structure version		CSD_STRUCTURE	1	R	194	2h
Reserved[2]		–	1	–	193	–
Extended CSD revision		EXT_CSD_REV	1	R	192	5h
Modes Segment						
Command set		CMD_SET	1	R/W/E_P	191	0h
Reserved[2]		–	1	–	190	–
Command set revision		CMD_SET_REV	1	R	189	0h
Reserved[2]		–	1	–	188	–
Power class		POWER_CLASS	1	R/W/E_P	187	0h

Table 8: ECSD Register Field Parameters (Continued)

Name		Field	Size (Bytes)	Cell Type[1]	ECSD Bytes	ECSD Value
Reserved[2]		–	1	–	186	–
High-speed interface timing		HS_TIMING	1	R/W/E_P	185	0h
Reserved[2]		–	1	–	184	–
Bus width mode		BUS_WIDTH	1	W/E_P	183	0h
Reserved[2]		–	1	–	182	–
Erased memory content		ERASED_MEM_CONT	1	R	181	0h
Reserved[2]		–	1	–	180	–
Partition configuration		PARTITION_CONFIG	1	R/W/E, R/W/E_P	179	0h
Boot configuration protection		BOOT_CONFIG_PROT	1	R/W, R/W/C_P	178	0h
Boot bus width		BOOT_BUS_WIDTH	1	R/W/E	177	0h
Reserved[2]		–	1	–	176	–
High-density erase group definition		ERASE_GROUP_DEF	1	R/W/E_P	175	0h
Reserved[2]		–	1	–	174	–
Boot area write protection register		BOOT_WP	1	R/W, R/W/C_P	173	0h
Reserved[2]		–	1	–	172	–
User write protection register		USER_WP	1	R/W, R/W/C_P, R/W/E_P	171	0h
Reserved[2]		–	1	–	170	–
Firmware configuration		FW_CONFIG	1	R/W	169	0h
RPMB size		RPMB_SIZE_MULT	1	R	168	1h
Write reliability setting register[3]		WR_REL_SET	1	R/W	167	0h
Write reliability parameter register[3]		WR_REL_PARAM	1	R	166	5h
Reserved[2]		–	1	–	165	–
Manually start background operations		BKOPS_START	1	W/E_P	164	–
Enable background operations handshake		BKOPS_EN	1	R/W	163	0h
Hardware reset function		RST_n_FUNCTION	1	R/W	162	0h
HPI management		HPI_MGMT	1	R/W/E_P	161	0h
Partitioning support		PARTITIONING_SUPPORT	1	R	160	3h
Maximum enhanced area size	4GB, 8GB	MAX_ENH_SIZE_MULT	3	R	[159:157]	30h, 64h
Partitions attribute		PARTITIONS_ATTRIBUTE	1	R/W	156	0h
Partitioning setting[4]		PARTITION_SET-TING_COMPLETED	1	R/W	155	0h
General-purpose partition size		GP_SIZE_MULT	12	R/W	[154:143]	0h
Enhanced user data area size		ENH_SIZE_MULT	3	R/W	[142:140]	0h
Enhanced user data start address		ENH_START_ADDR	4	R/W	[139:136]	0h

Table 8: ECSD Register Field Parameters (Continued)

Name	Field	Size (Bytes)	Cell Type[1]	ECSD Bytes	ECSD Value
Reserved[2]	–	1	–	135	–
Bad block management mode	SEC_BAD_BLK_MGMNT	1	R/W	134	0h
Reserved[2]	–	134	–	[133:0]	–

Notes:
1. R = Read-only

   R/W = One-time programmable and readable

   R/W/E = Multiple writable with the value kept after a power cycle, assertion of the RST_n signal, and any CMD0 reset and readable

   R/W/C_P = Writable after the value is cleared by a power cycle and assertion of the RST_n signal (the value not cleared by CMD0 reset) and readable

   R/W/E_P = Multiple writable with the value reset after a power cycle, assertion of the RST_n signal, and any CMD0 reset and readable

   W/E_P = Multiple writable with the value reset after power cycle, assertion of the RST_n signal, and any CMD0 reset and not readable

   TBD = To be determined
2. Reserved bits should be read as 0.
3. Open-ended, enhanced reliable write is not supported.
4. Setting this bit to 1 reduces the SEC_COUNT values.

DC Electrical Specifications – Device Power

The device current consumption for various device configurations is defined in the power class fields of the ECSD register.

During power-on (except during a BOOT operation), the current consumption of any device must not exceed 10mA before the host sends a valid OC register range.

V_{CC} is used for the NAND Flash device and its interface voltage; V_{CCQ} is used for the controller and the *e*·MMC interface voltage. The core regulator is optional and only required when V_{CCQ} is in the 3V range. A C_{REG} capacitor must be connected to the V_{DDI} terminal to stabilize regulator output on the system.

Figure 10: Device Power Diagram

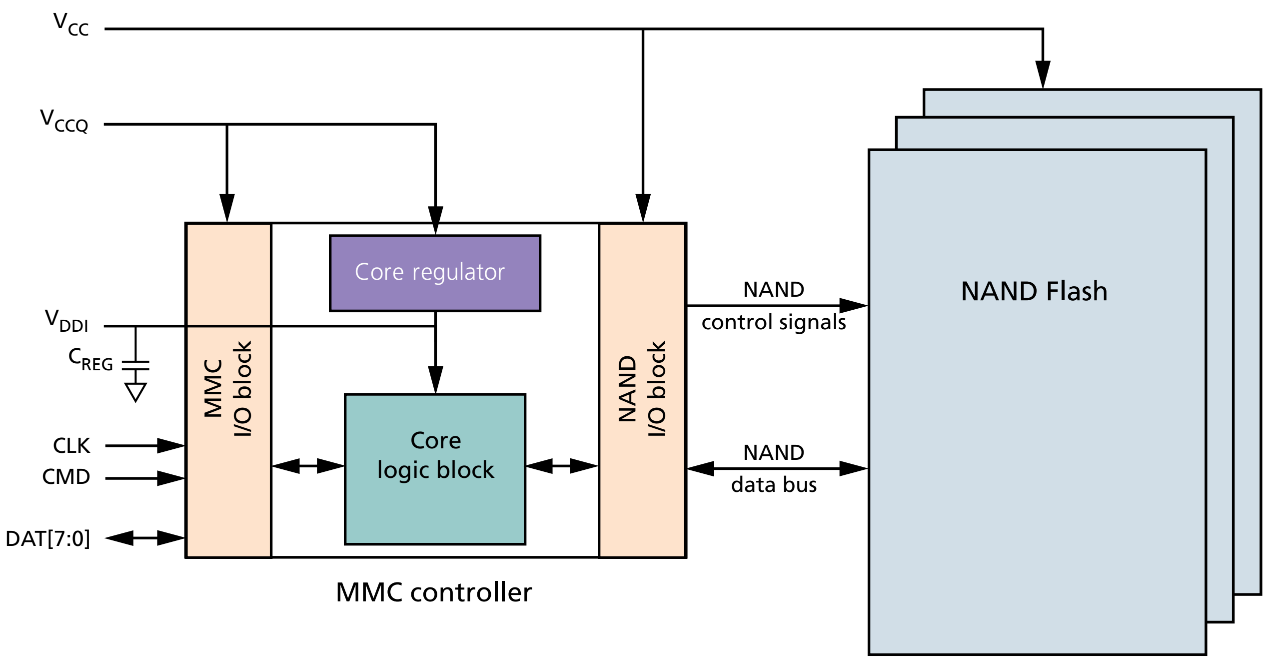


Table 9: Operating Conditions

Parameters	Symbol	Min	Typ	Max	Unit
Supply power-on for 3.3V	^tPRUH	–	–	35	ms
Supply power-on for 1.8V	^tPRUL	–	–	25	ms
V_{DDI} capacitance value	C_{REG}[1]	0.1	–	–	µF

Note: 1. C_{REG} is used to stabilize the internal regulator output to controller core logic voltages. Micron recommends using the following capacitor values:
C_{VCC} (capacitor for V_{CC}) = 4.3µF
C_{VCCQ} (capacitor for V_{CCQ}) = 4.3µF
C_{REG} = 1.0µF

AC Electrical Specifications

Table 10: Timing Values

Symbol	Min	Max	Unit
N_{AC}	2	10 × (TAAC × F_{OP} + 100 × NSAC)[1, 2]	Clock cycles
N_{CC}	8	–	Clock cycles
N_{CD}	56	–	Clock cycles
N_{CP}	74	–	Clock cycles
N_{CR}	2	64	Clock cycles
N_{ID}	5	5	Clock cycles
N_{RC}	8	–	Clock cycles
N_{SC}	8	–	Clock cycles
N_{ST}	2	2	Clock cycles
N_{WR}	2	–	Clock cycles
^{t}BA	–	50	ms
^{t}BD	–	1	s

Notes: 1. See the following table for timing parameters.
2. F_{OP} = Operating frequency.

Table 11: Hardware Reset Timing Parameters

Symbol	Description	Min	Max	Unit
$^{t}RSTW$	RST_n pulse width	1	–	µs
$^{t}RSCA$	RST_n to command time[1]	200	–	µs
$^{t}RSTH$	RST_n high period (interval time)	1	–	µs

Note: 1. 74 clock cycles required before issuing CMD1 or CMD0 with argument 0xFFFFFFFA.

Table 12: Interface Timing (High-Speed Interface)

Parameter	Symbol	Min	Max	Unit	Conditions
CLK[1]					
Clock frequency data transfer mode (PP)[2]	F_{PP}	0	52[3]	MHz	C_L ≤30pF Tolerance: +100 kHz
Clock frequency identification mode (OD)	F_{OD}	0	400	kHz	Tolerance: +20 kHz
Clock high time	^tWH	6.5	–	ns	C_L ≤30pF
Clock low time	^tWL	6.5	–	ns	C_L ≤30pF
Clock rise time[4]	^tTLH	–	3	ns	C_L ≤30pF
Clock fall time	^tTHL	–	3	ns	C_L ≤30pF
Inputs CMD, DAT (Referenced to CLK)					
Input set-up time	^tISU	3	–	ns	C_L ≤30pF
Input hold time	^tIH	3	–	ns	C_L ≤30pF
Outputs CMD, DAT (Referenced to CLK)					
Output delay time during data transfer	^tODLY	–	13.7	ns	C_L ≤30pF
Output hold time	^tOH	2.5	–	ns	C_L ≤30pF
Signal rise time[5]	^tRISE	–	3	ns	C_L ≤30pF
Signal fall time	^tFALL	–	3	ns	C_L ≤30pF

Notes:
1. CLK timing is measured at 50% of V_{CCQ}.
2. Micron e·MMC devices support the full frequency range of 0–52 MHz.
3. The device can also operate at a clock frequency of 26 MHz.
4. CLK rise and fall times are measured by $V_{IH,min}$ and $V_{IL,max}$.
5. Rise and fall times for inputs CMD and DAT are measured by $V_{IH,min}$ and $V_{IL,max}$. Rise and fall times for outputs CMD and DAT are measured by $V_{OH,min}$ and $V_{OL,max}$.

Table 13: Interface Timing (Standard Interface)

Parameter	Symbol	Min	Max	Unit	Conditions[1]
CLK[2]					
Clock frequency data transfer mode (PP)[3]	F_{PP}	0	26	MHz	C_L ≤30pF
Clock frequency identification mode (OD)	F_{OD}	0	400	kHz	
Clock high time	^tWH	10	–	ns	C_L ≤30pF
Clock low time	^tWL	10	–	ns	C_L ≤30pF
Clock rise time[4]	^tTLH	–	10	ns	C_L ≤30pF
Clock fall time	^tTHL	–	10	ns	C_L ≤30pF
Inputs CMD, DAT (Referenced to CLK)					
Input set-up time	^tISU	3	–	ns	C_L ≤30pF
Input hold time	^tIH	3	–	ns	C_L ≤30pF
Outputs CMD, DAT (Referenced to CLK)					
Output set-up time[5]	^tOSU	11.7	–	ns	C_L ≤30pF
Output hold time[5]	^tOH	8.3	–	ns	C_L ≤30pF

Notes:
1. The device must always start with the standard interface timing. The timing mode can be switched to high-speed interface timing by the host sending the SWITCH (CMD6) command with the argument for high-speed interface selected.
2. CLK timing is measured at 50% of V_{CCQ}.
3. For compatibility with cards that support the v4.2 standard or earlier, the host should not use >20 MHz before switching to high-speed interface timing.
4. CLK rise and fall times are measured by $V_{IH,min}$ and $V_{IL,max}$.
5. ^tOSU and ^tOH are defined as values from the clock's rising edge. However, there may be devices that use the clock's falling edge to output data in backward compatibility mode. Therefore, it is recommended that the host either sets the ^tWL value to be as long as possible within the range defined by ^tCK through ^tOHmin, or that it uses a slow clock frequency so that it can have a data setup margin for those devices. In this case, each device that uses the clock's falling edge may show a correlation between ^tWL and ^tOSU, or between ^tCK and ^tOSU, as a note in the device's data sheet or as an application note.

AC Electrical Specifications (DDR Mode)

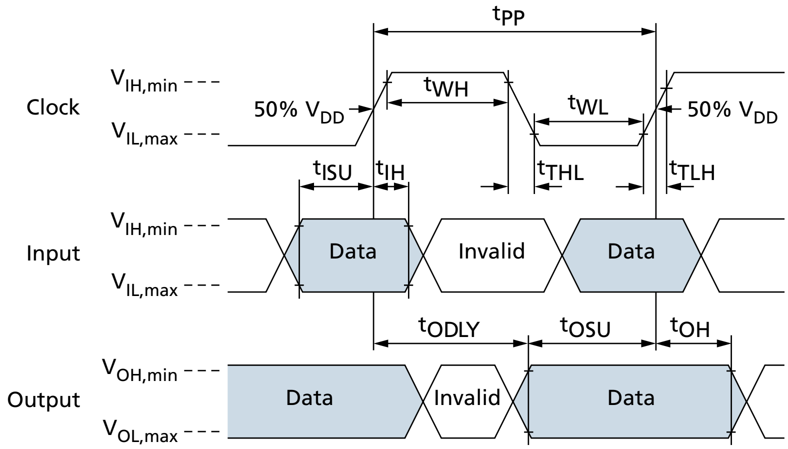
Table 14: Interface Timing (High-Speed Interface, DDR Mode)

Parameter	Symbol	Min	Max	Unit	Conditions
Input CLK[1]					
Clock duty cycle	–	45	55	%	Includes jitter, phase hoise
Input DAT (Referenced to CLK-DDR Mode)					
Input set-up time	^{t}ISU,ddr	2.5	–	ns	C_L ≤20pF
Input hold time	^{t}IH,ddr	2.5	–	ns	C_L ≤20pF
Outputs DAT (Referenced to CLK-DDR Mode)					
Output delay time during data transfer	^{t}ODLY,ddr	1.5	7	ns	C_L ≤20pF
Signal rise time (all signals)[2]	^{t}RISE	–	2	ns	C_L ≤20pF
Signal fall time (all signals)	^{t}FALL	–	2	ns	C_L ≤20pF

Notes:
1. CLK timing is measured at 50% of V_{CCQ}.
2. Rise and fall times for inputs CMD and DAT are measured by $V_{IH,min}$ and $V_{IL,max}$. Rise and fall times for outputs CMD and DAT are measured by $V_{OH,min}$ and $V_{OL,max}$.

Bus and Device Interface Timing

Figure 11: Bus and Device Interface Timing

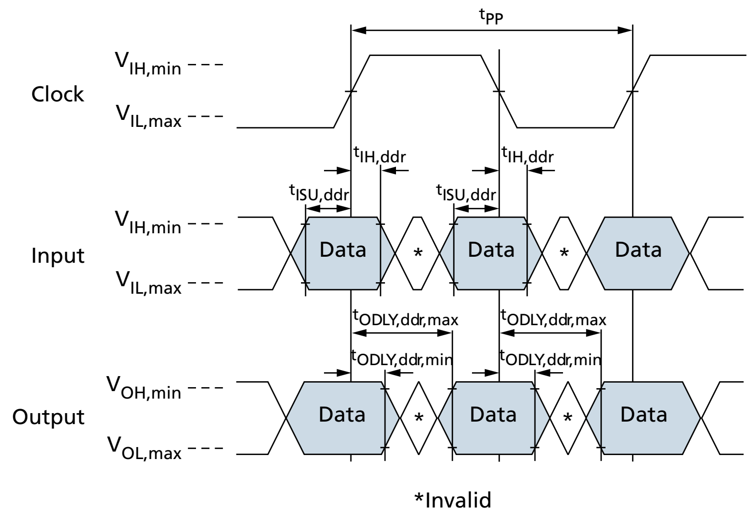


Note: 1. Data must always be sampled on the rising edge of the clock.

Bus and Device Interface Timing (DDR mode)

These timings apply to the DAT[7:0] signals only when the device is configured for dual data rate (DDR) mode operation. In DDR mode, the DAT signals operate synchronously on both the rising and falling edges of the clock (CLK). The CMD signal operates synchronously on rising edge of CLK, in compliance with the bus timing specified by JEDEC Standard No. 84-A44. Therefore, there are no timing changes for the CMD signal.

Figure 12: Bus and Device Interface Timing (DDR mode)



Note: 1. In DDR mode, DAT[7:0] lines are sampled on both edges of the clock (not applicable for the CMD line).

2Gb: x16, x32 Mobile LPDDR SDRAM

Features

- V_{DD}/V_{DDQ} = 1.70–1.95V
- Bidirectional data strobe per byte of data (DQS)
- Internal, pipelined double data rate (DDR) architecture; two data accesses per clock cycle
- Differential clock inputs (CK and CK#)
- Commands entered on each positive CK edge
- DQS edge-aligned with data for READs; center-aligned with data for WRITEs
- 4 internal banks for concurrent operation
- Data masks (DM) for masking write data; one mask per byte
- Programmable burst lengths (BL): 2, 4, 8, or 16
- Concurrent auto precharge option is supported
- Auto refresh and self refresh modes
- 1.8V LVCMOS-compatible inputs
- Temperature-compensated self refresh (TCSR)
- Partial-array self refresh (PASR)
- Deep power-down (DPD)
- Status read register (SRR)
- Selectable output drive strength (DS)
- Clock stop capability
- 64ms refresh

Table 15: Configuration Addressing – 2Gb

Architecture	128 Meg x 16	64 Meg x 32	Reduced Page-Size Option 128 Meg x 16	Reduced Page-Size Option 64 Meg x 32
Configuration	32 Meg x 16 x 4 banks	16 Meg x 32 x 4 banks	32 Meg x 16 x 4 banks	16 Meg x 32 x 4 banks
Refresh count	8K	8K	8K	8K
Row addressing	16K A[13:0]	16K A[13:0]	32K A[14:0]	32K A[14:0]
Column addressing	2K A11, A[9:0]	1K A[9:0]	1K A[9:0]	512K A[8:0]

General Description

The 2Gb Mobile low-power DDR SDRAM is a high-speed CMOS, dynamic random-access memory containing 2,147,483,648 bits. It is internally configured as a quad-bank DRAM. Each of the x16's 536,870,912-bit banks is organized as 16,384 rows by 2048 columns by 16 bits. Each of the x32's 536,870,912-bit banks is organized as 16,384 rows by 1024 columns by 32 bits. In the reduced page-size (LG) option, each of the x32's 536,870,912-bit banks is organized as 32,768 rows by 512 columns by 32 bits. In the reduced page-size (R4) option, each of the x16's 536,870,912-bit banks is organized as 32,768 rows by 1024 columns x 16 bits.

Note:

1. Throughout this data sheet, various figures and text refer to DQs as "DQ." DQ should be interpreted as any and all DQ collectively, unless specifically stated otherwise. Additionally, the x16 is divided into 2 bytes: the lower byte and the upper byte. For the lower byte (DQ[7:0]), DM refers to LDM and DQS refers to LDQS. For the upper byte (DQ[15:8]), DM refers to UDM and DQS refers to UDQS. The x32 is divided into 4 bytes. For DQ[7:0], DM refers to DM0 and DQS refers to DQS0. For DQ[15:8], DM refers to DM1 and DQS refers to DQS1. For DQ[23:16], DM refers to DM2 and DQS refers to DQS2. For DQ[31:24], DM refers to DM3 and DQS refers to DQS3.

2. Complete functionality is described throughout the document; any page or diagram may have been simplified to convey a topic and may not be inclusive of all requirements.

3. Any specific requirement takes precedence over a general statement.

Functional Block Diagrams

Figure 13: Functional Block Diagram (x16)

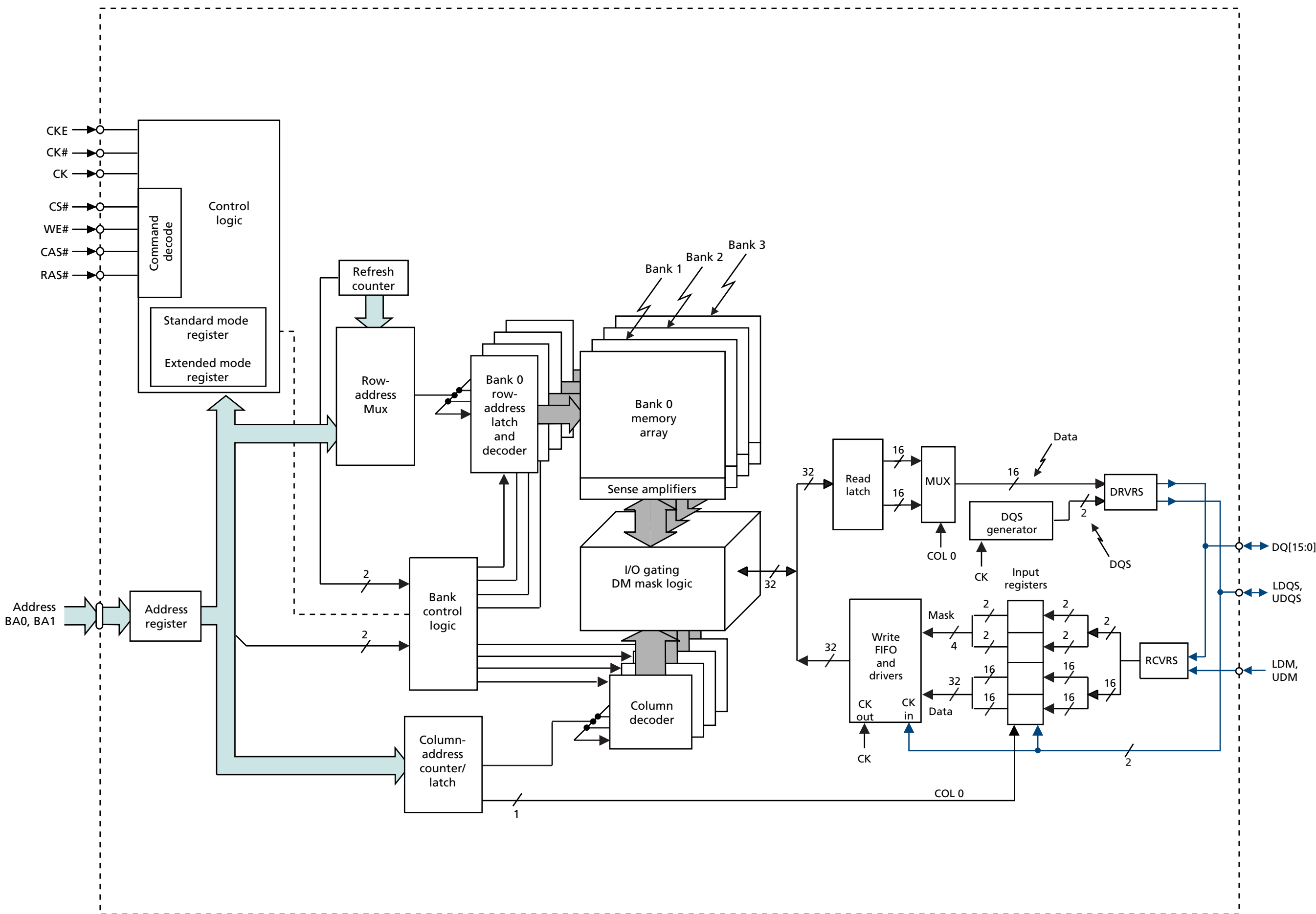
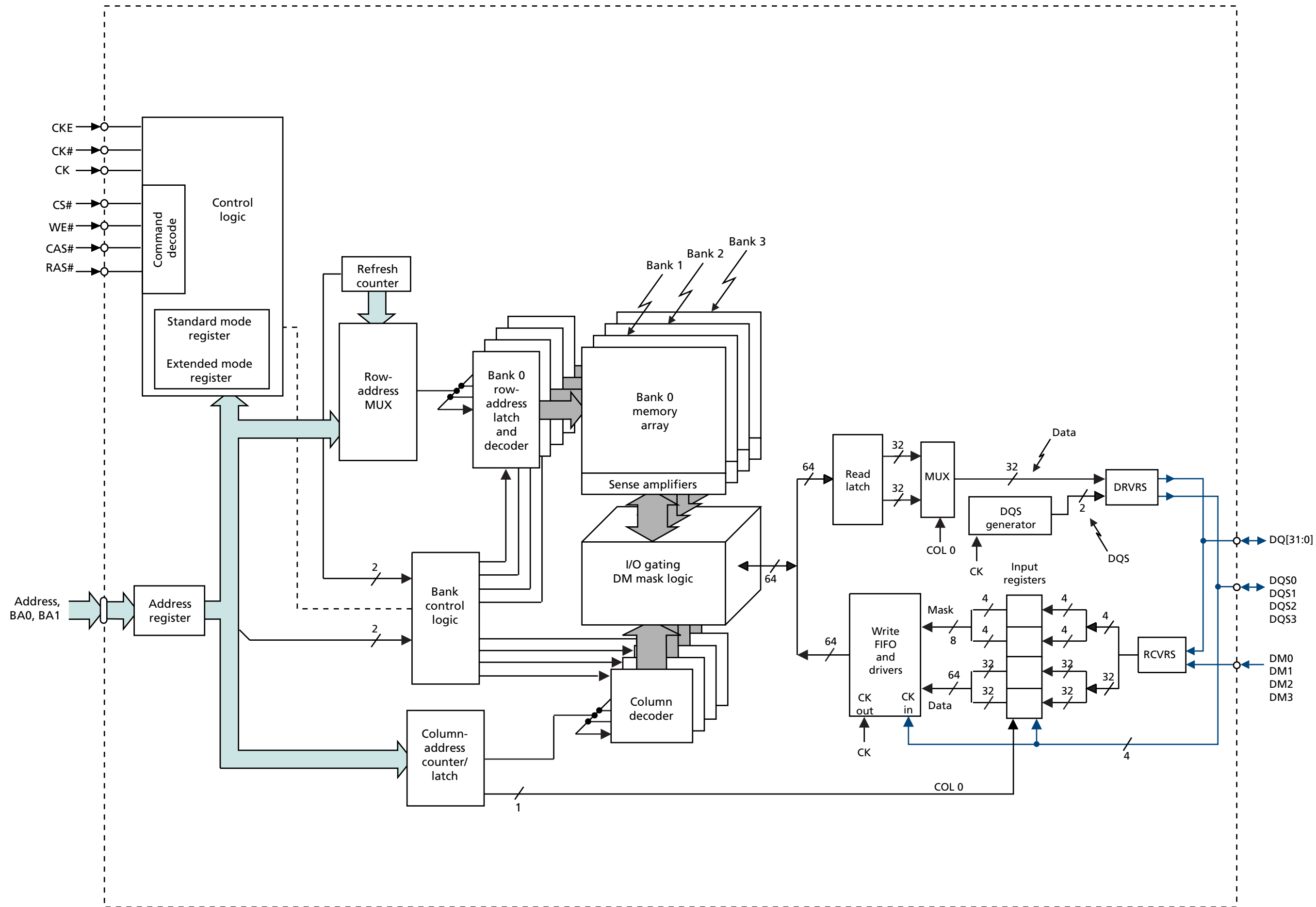


Figure 14: Functional Block Diagram (x32)



Electrical Specifications

Stresses greater than those listed may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Table 16: Absolute Maximum Ratings

Note 1 applies to all parameters in this table

Parameter	Symbol	Min	Max	Unit
V_{DD}/V_{DDQ} supply voltage relative to V_{SS}	V_{DD}/V_{DDQ}	–1.0	2.4	V
Voltage on any pin relative to V_{SS}	V_{IN}	–0.5	2.4 or (V_{DDQ} + 0.3V), whichever is less	V
Storage temperature (plastic)	T_{STG}	–55	150	˚C

Note: 1. V_{DD} and V_{DDQ} must be within 300mV of each other at all times. V_{DDQ} must not exceed V_{DD}.

Table 17: AC/DC Electrical Characteristics and Operating Conditions

Notes 1–5 apply to all parameters/conditions in this table; V_{DD}/V_{DDQ} = 1.70–1.95V

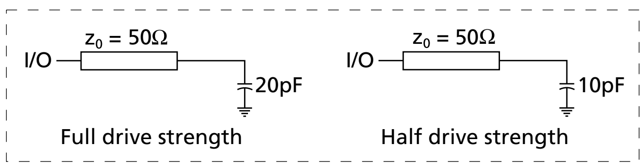
Parameter/Condition	Symbol	Min	Max	Unit	Notes
Supply voltage	V_{DD}	1.70	1.95	V	6, 7
I/O supply voltage	V_{DDQ}	1.70	1.95	V	6, 7
Address and command inputs					
Input voltage high	V_{IH}	0.8 × V_{DDQ}	V_{DDQ} + 0.3	V	8, 9
Input voltage low	V_{IL}	–0.3	0.2 × V_{DDQ}	V	8, 9
Clock inputs (CK, CK#)					
DC input voltage	V_{IN}	–0.3	V_{DDQ} + 0.3	V	10
DC input differential voltage	$V_{ID(DC)}$	0.4 × V_{DDQ}	V_{DDQ} + 0.6	V	10, 11
AC input differential voltage	$V_{ID(AC)}$	0.6 × V_{DDQ}	V_{DDQ} + 0.6	V	10, 11
AC differential crossing voltage	V_{IX}	0.4 × V_{DDQ}	0.6 × V_{DDQ}	V	10, 12
Data inputs					
DC input high voltage	$V_{IH(DC)}$	0.7 × V_{DDQ}	V_{DDQ} + 0.3	V	8, 9, 13
DC input low voltage	$V_{IL(DC)}$	–0.3	0.3 × V_{DDQ}	V	8, 9, 13
AC input high voltage	$V_{IH(AC)}$	0.8 × V_{DDQ}	V_{DDQ} + 0.3	V	8, 9, 13
AC input low voltage	$V_{IL(AC)}$	–0.3	0.2 × V_{DDQ}	V	8, 9, 13
Data outputs					
DC output high voltage: Logic 1 (I_{OH} = –0.1mA)	V_{OH}	0.9 × V_{DDQ}	–	V	
DC output low voltage: Logic 0 (I_{OL} = 0.1mA)	V_{OL}	–	0.1 × V_{DDQ}	V	
Leakage current					
Input leakage current Any input 0V ≤ V_{IN} ≤ V_{DD} (All other pins not under test = 0V)	I_I	–1	1	µA	

Table 17: AC/DC Electrical Characteristics and Operating Conditions (Continued)

Notes 1–5 apply to all parameters/conditions in this table; V_{DD}/V_{DDQ} = 1.70–1.95V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Output leakage current (DQ are disabled; 0V ≤ V_{OUT} ≤ V_{DDQ})	I_{OZ}	–1.5	1.5	µA	
Operating temperature					
Commercial	T_A	0	70	˚C	
Industrial	T_A	–40	85	˚C	
Automotive	T_A	–40	105	˚C	

Notes:
1. All voltages referenced to V_{SS}.
2. All parameters assume proper device initialization.
3. Tests for AC timing, I_{DD}, and electrical AC and DC characteristics may be conducted at nominal supply voltage levels, but the related specifications and device operation are guaranteed for the full voltage range specified.
4. Outputs measured with equivalent load; transmission line delay is assumed to be very small:



5. Timing and I_{DD} tests may use a V_{IL}-to-V_{IH} swing of up to 1.5V in the test environment, but input timing is still referenced to $V_{DDQ/2}$ (or to the crossing point for CK/CK#). The output timing reference voltage level is $V_{DDQ/2}$.
6. Any positive glitch must be less than one-third of the clock cycle and not more than +200mV or 2.0V, whichever is less. Any negative glitch must be less than one-third of the clock cycle and not exceed either –150mV or +1.6V, whichever is more positive.
7. V_{DD} and V_{DDQ} must track each other and V_{DDQ} must be less than or equal to V_{DD}.
8. To maintain a valid level, the transitioning edge of the input must:
   8a. Sustain a constant slew rate from the current AC level through to the target AC level, $V_{IL(AC)}$ Or $V_{IH(AC)}$.
   8b. Reach at least the target AC level.
   8c. After the AC target level is reached, continue to maintain at least the target DC level, $V_{IL(DC)}$ or $V_{IH(DC)}$.
9. V_{IH} overshoot: V_{IHmax} = V_{DDQ} + 1.0V for a pulse width ≤3ns and the pulse width cannot be greater than one-third of the cycle rate. V_{IL} undershoot: V_{ILmin} = –1.0V for a pulse width ≤3ns and the pulse width cannot be greater than one-third of the cycle rate.
10. CK and CK# input slew rate must be ≥1 V/ns (2 V/ns if measured differentially).
11. V_{ID} is the magnitude of the difference between the input level on CK and the input level on CK#.
12. The value of V_{IX} is expected to equal $V_{DDQ/2}$ of the transmitting device and must track variations in the DC level of the same.
13. DQ and DM input slew rates must not deviate from DQS by more than 10%. 50ps must be added to ^tDS and ^tDH for each 100 mV/ns reduction in slew rate. If slew rate exceeds 4 V/ns, functionality is uncertain.

Table 18: Capacitance (x16, x32)

Note 1 applies to all the parameters in this table

Parameter	Symbol	Min	Max	Unit	Notes
Input capacitance: CK, CK#	C_{CK}	1.5	3.5	pF	
Delta input capacitance: CK, CK#	C_{DCK}	–	0.25	pF	2
Input capacitance: command and address	C_I	1.5	3.5	pF	
Delta input capacitance: command and address	C_{DI}	–	0.5	pF	2
Input/output capacitance: DQ, DQS, DM	C_{IO}	2.0	4.5	pF	
Delta input/output capacitance: DQ, DQS, DM	C_{DIO}	–	0.5	pF	3

Notes:
1. This parameter is sampled. V_{DD}/V_{DDQ} = 1.70–1.95V, f = 100 MHz, T_A = 25°C, $V_{OUT(DC)}$ = $V_{DDQ}/2$, V_{OUT} (peak-to-peak) = 0.2V. DM input is grouped with I/O pins, reflecting the fact that they are matched in loading.
2. The input capacitance per pin group will not differ by more than this maximum amount for any given device.
3. The I/O capacitance per DQS and DQ byte/group will not differ by more than this maximum amount for any given device.

Electrical Specifications – I_{DD} Parameters

Table 19: I_{DD} Specifications and Conditions, –40°C to +85°C (x16)

Notes 1–5 apply to all the parameters/conditions in this table; V_{DD}/V_{DDQ} = 1.70–1.95V

Parameter/Condition		Symbol	Max -5	Max -54	Max -6	Max -75	Unit	Notes
Operating 1 bank active precharge current: $^tRC = {}^tRC$ (MIN); $^tCK = {}^tCK$ (MIN); CKE is HIGH; CS is HIGH between valid commands; Address inputs are switching every 2 clock cycles; Data bus inputs are stable		I_{DD0}	100	100	80	70	mA	6
Precharge power-down standby current: All banks idle; CKE is LOW; CS is HIGH; $^tCK = {}^tCK$ (MIN); Address and control inputs are switching; Data bus inputs are stable		I_{DD2P}	900	900	900	900	µA	7, 8
Precharge power-down standby current: Clock stopped; All banks idle; CKE is LOW; CS is HIGH; CK = LOW, CK# = HIGH; Address and control inputs are switching; Data bus inputs are stable		I_{DD2PS}	900	900	900	900	µA	7
Precharge nonpower-down standby current: All banks idle; CKE = HIGH; CS = HIGH; $^tCK = {}^tCK$ (MIN); Address and control inputs are switching; Data bus inputs are stable		I_{DD2N}	15	15	15	12	mA	9
Precharge nonpower-down standby current: Clock stopped; All banks idle; CKE = HIGH; CS = HIGH; CK = LOW, CK# = HIGH; Address and control inputs are switching; Data bus inputs are stable		I_{DD2NS}	9	9	8	8	mA	9
Active power-down standby current: 1 bank active; CKE = LOW; CS = HIGH; $^tCK = {}^tCK$ (MIN); Address and control inputs are switching; Data bus inputs are stable		I_{DD3P}	5	5	5	5	mA	8
Active power-down standby current: Clock stopped; 1 bank active; CKE = LOW; CS = HIGH; CK = LOW; CK# = HIGH; Address and control inputs are switching; Data bus inputs are stable		I_{DD3PS}	5	5	5	5	mA	
Active nonpower-down standby: 1 bank active; CKE = HIGH; CS = HIGH; $^tCK = {}^tCK$ (MIN); Address and control inputs are switching; Data bus inputs are stable		I_{DD3N}	17	17	16	15	mA	6
Active nonpower-down standby: Clock stopped; 1 bank active; CKE = HIGH; CS = HIGH; CK = LOW; CK# = HIGH; Address and control inputs are switching; Data bus inputs are stable		I_{DD3NS}	14	14	13	12	mA	6
Operating burst read: 1 bank active; BL = 4; $^tCK = {}^tCK$ (MIN); Continuous READ bursts; Iout = 0mA; Address inputs are switching every 2 clock cycles; 50% data changing each burst		I_{DD4R}	130	125	115	105	mA	6
Operating burst write: 1 bank active; BL = 4; $^tCK = {}^tCK$ (MIN); Continuous WRITE bursts; Address inputs are switching; 50% data changing each burst		I_{DD4W}	130	125	115	105	mA	6
Auto refresh: Burst refresh; CKE = HIGH; Address and control inputs are switching; Data bus inputs are stable	^tRFC = 138ns	I_{DD5}	170	170	170	170	mA	10
	$^tRFC = {}^tREFI$	I_{DD5A}	12	12	12	12	mA	10, 11
Deep power-down current: Address and control balls are stable; Data bus inputs are stable		I_{DD8}	10	10	10	10	µA	7, 13

Table 20: I_{DD} Specifications and Conditions, –40°C to +85°C (x32)

Notes 1–5 apply to all the parameters/conditions in this table; V_{DD}/V_{DDQ} = 1.70–1.95V

Parameter/Condition		Symbol	Max -5	Max -54	Max -6	Max -75	Unit	Notes
Operating 1 bank active precharge current: $^tRC = {}^tRC$ (MIN); $^tCK = {}^tCK$ (MIN); CKE is HIGH; CS is HIGH between valid commands; Address inputs are switching every 2 clock cycles; Data bus inputs are stable		I_{DD0}	100	100	80	70	mA	6
Precharge power-down standby current: All banks idle; CKE is LOW; CS is HIGH; $^tCK = {}^tCK$ (MIN); Address and control inputs are switching; Data bus inputs are stable		I_{DD2P}	900	900	900	900	µA	7, 8
Precharge power-down standby current: Clock stopped; All banks idle; CKE is LOW; CS is HIGH, CK = LOW, CK# = HIGH; Address and control inputs are switching; Data bus inputs are stable		I_{DD2PS}	900	900	900	900	µA	7
Precharge nonpower-down standby current: All banks idle; CKE = HIGH; CS = HIGH; $^tCK = {}^tCK$ (MIN); Address and control inputs are switching; Data bus inputs are stable		I_{DD2N}	15	15	15	12	mA	9
Precharge nonpower-down standby current: Clock stopped; All banks idle; CKE = HIGH; CS = HIGH; CK = LOW, CK# = HIGH; Address and control inputs are switching; Data bus inputs are stable		I_{DD2NS}	9	9	8	8	mA	9
Active power-down standby current: 1 bank active; CKE = LOW; CS = HIGH; $^tCK = {}^tCK$ (MIN); Address and control inputs are switching; Data bus inputs are stable		I_{DD3P}	5	5	5	5	mA	8
Active power-down standby current: Clock stopped; 1 bank active; CKE = LOW; CS = HIGH; CK = LOW; CK# = HIGH; Address and control inputs are switching; Data bus inputs are stable		I_{DD3PS}	5	5	5	5	mA	
Active nonpower-down standby: 1 bank active; CKE = HIGH; CS = HIGH; $^tCK = {}^tCK$ (MIN); Address and control inputs are switching; Data bus inputs are stable		I_{DD3N}	17	17	16	15	mA	6
Active nonpower-down standby: Clock stopped; 1 bank active; CKE = HIGH; CS = HIGH; CK = LOW; CK# = HIGH; Address and control inputs are switching; Data bus inputs are stable		I_{DD3NS}	14	14	13	12	mA	6
Operating burst read: 1 bank active; BL = 4; CL = 3; $^tCK = {}^tCK$ (MIN); Continuous READ bursts; Iout = 0mA; Address inputs are switching every 2 clock cycles; 50% data changing each burst		I_{DD4R}	150	145	140	120	mA	6
Operating burst write: One bank active; BL = 4; $^tCK = {}^tCK$ (MIN); Continuous WRITE bursts; Address inputs are switching; 50% data changing each burst		I_{DD4W}	150	145	140	120	mA	6
Auto refresh: Burst refresh; CKE = HIGH; Address and control inputs are switching; Data bus inputs are stable	^tRFC = 138ns	I_{DD5}	170	170	170	170	mA	10
	$^tRFC = {}^tREFI$	I_{DD5A}	12	12	12	12	mA	10, 11
Deep power-down current: Address and control pins are stable; Data bus inputs are stable		I_{DD8}	10	10	10	10	µA	7, 13

Table 21: I_{DD} Specifications and Conditions, –40°C to +105°C (x16)

Notes 1–5 apply to all the parameters/conditions in this table; V_{DD}/V_{DDQ} = 1.70–1.95V

Parameter/Condition	Symbol	Max				Unit	Notes
		-5	-54	-6	-75		
Operating 1 bank active precharge current: ^{t}RC = ^{t}RC (MIN); ^{t}CK = ^{t}CK (MIN); CKE is HIGH; CS is HIGH between valid commands; Address inputs are switching every 2 clock cycles; Data bus inputs are stable	I_{DD0}	100	100	80	70	mA	6
Precharge power-down standby current: All banks idle; CKE is LOW; CS is HIGH; ^{t}CK = ^{t}CK (MIN); Address and control inputs are switching; Data bus inputs are stable	I_{DD2P}	1500	1500	1500	1500	µA	7, 8
Precharge power-down standby current: Clock stopped; All banks idle; CKE is LOW; CS is HIGH; CK = LOW, CK# = HIGH; Address and control inputs are switching; Data bus inputs are stable	I_{DD2PS}	1500	1500	1500	1500	µA	7
Precharge nonpower-down standby current: All banks idle; CKE = HIGH; CS = HIGH; ^{t}CK = ^{t}CK (MIN); Address and control inputs are switching; Data bus inputs are stable	I_{DD2N}	19	19	19	16	mA	9
Precharge nonpower-down standby current: Clock stopped; All banks idle; CKE = HIGH; CS = HIGH; CK = LOW, CK# = HIGH; Address and control inputs are switching; Data bus inputs are stable	I_{DD2NS}	13	13	12	12	mA	9
Active power-down standby current: 1 bank active; CKE = LOW; CS = HIGH; ^{t}CK = ^{t}CK (MIN); Address and control inputs are switching; Data bus inputs are stable	I_{DD3P}	9	9	9	9	mA	8
Active power-down standby current: Clock stopped; 1 bank active; CKE = LOW; CS = HIGH; CK = LOW; CK# = HIGH; Address and control inputs are switching; Data bus inputs are stable	I_{DD3PS}	9	9	9	9	mA	
Active nonpower-down standby: 1 bank active; CKE = HIGH; CS = HIGH; ^{t}CK = ^{t}CK (MIN); Address and control inputs are switching; Data bus inputs are stable	I_{DD3N}	21	21	20	19	mA	6
Active nonpower-down standby: Clock stopped; 1 bank active; CKE = HIGH; CS = HIGH; CK = LOW; CK# = HIGH; Address and control inputs are switching; Data bus inputs are stable	I_{DD3NS}	18	18	17	15	mA	6
Operating burst read: 1 bank active; BL = 4; ^{t}CK = ^{t}CK (MIN); Continuous READ bursts; Iout = 0mA; Address inputs are switching every 2 clock cycles; 50% data changing each burst	I_{DD4R}	130	125	115	105	mA	6
Operating burst write: 1 bank active; BL = 4; ^{t}CK = ^{t}CK (MIN); Continuous WRITE bursts; Address inputs are switching; 50% data changing each burst	I_{DD4W}	130	125	115	105	mA	6
Auto refresh: Burst refresh; CKE = HIGH; Address and control inputs are switching; Data bus inputs are stable: ^{t}RFC = 138ns	I_{DD5}	170	170	170	170	mA	10
Auto refresh: Burst refresh; CKE = HIGH; Address and control inputs are switching; Data bus inputs are stable: ^{t}RFC = ^{t}REFI	I_{DD5A}	13	13	13	13	mA	10, 11
Deep power-down current: Address and control balls are stable; Data bus inputs are stable	I_{DD8}	15	15	15	15	µA	7, 13

Table 22: I_{DD} Specifications and Conditions, –40°C to +105°C (x32)

Notes 1–5 apply to all the parameters/conditions in this table; V_{DD}/V_{DDQ} = 1.70–1.95V

Parameter/Condition		Symbol	Max				Unit	Notes
			-5	-54	-6	-75		
Operating 1 bank active precharge current: $^tRC = {}^tRC$ (MIN); $^tCK = {}^tCK$ (MIN); CKE is HIGH; CS is HIGH between valid commands; Address inputs are switching every 2 clock cycles; Data bus inputs are stable		I_{DD0}	100	100	80	70	mA	6
Precharge power-down standby current: All banks idle; CKE is LOW; CS is HIGH; $^tCK = {}^tCK$ (MIN); Address and control inputs are switching; Data bus inputs are stable		I_{DD2P}	1500	1500	1500	1500	µA	7, 8
Precharge power-down standby current: Clock stopped; All banks idle; CKE is LOW; CS is HIGH, CK = LOW, CK# = HIGH; Address and control inputs are switching; Data bus inputs are stable		I_{DD2PS}	1500	1500	1500	1500	µA	7
Precharge nonpower-down standby current: All banks idle; CKE = HIGH; CS = HIGH; $^tCK = {}^tCK$ (MIN); Address and control inputs are switching; Data bus inputs are stable		I_{DD2N}	19	19	19	16	mA	9
Precharge nonpower-down standby current: Clock stopped; All banks idle; CKE = HIGH; CS = HIGH; CK = LOW, CK# = HIGH; Address and control inputs are switching; Data bus inputs are stable		I_{DD2NS}	13	13	12	12	mA	9
Active power-down standby current: 1 bank active; CKE = LOW; CS = HIGH; $^tCK = {}^tCK$ (MIN); Address and control inputs are switching; Data bus inputs are stable		I_{DD3P}	9	9	9	9	mA	8
Active power-down standby current: Clock stopped; 1 bank active; CKE = LOW; CS = HIGH; CK = LOW; CK# = HIGH; Address and control inputs are switching; Data bus inputs are stable		I_{DD3PS}	9	9	9	9	mA	
Active nonpower-down standby: 1 bank active; CKE = HIGH; CS = HIGH; $^tCK = {}^tCK$ (MIN); Address and control inputs are switching; Data bus inputs are stable		I_{DD3N}	21	21	20	19	mA	6
Active nonpower-down standby: Clock stopped; 1 bank active; CKE = HIGH; CS = HIGH; CK = LOW; CK# = HIGH; Address and control inputs are switching; Data bus inputs are stable		I_{DD3NS}	18	18	17	15	mA	6
Operating burst read: 1 bank active; BL = 4; CL = 3; $^tCK = {}^tCK$ (MIN); Continuous READ bursts; Iout = 0mA; Address inputs are switching every 2 clock cycles; 50% data changing each burst		I_{DD4R}	150	145	140	120	mA	6
Operating burst write: One bank active; BL = 4; $^tCK = {}^tCK$ (MIN); Continuous WRITE bursts; Address inputs are switching; 50% data changing each burst		I_{DD4W}	150	145	140	120	mA	6
Auto refresh: Burst refresh; CKE = HIGH; Address and control inputs are switching; Data bus inputs are stable	^tRFC = 138ns	I_{DD5}	170	170	170	170	mA	10
	$^tRFC = {}^tREFI$	I_{DD5A}	13	13	13	13	mA	10, 11
Deep power-down current: Address and control pins are stable; Data bus inputs are stable		I_{DD8}	15	15	15	15	µA	7, 13

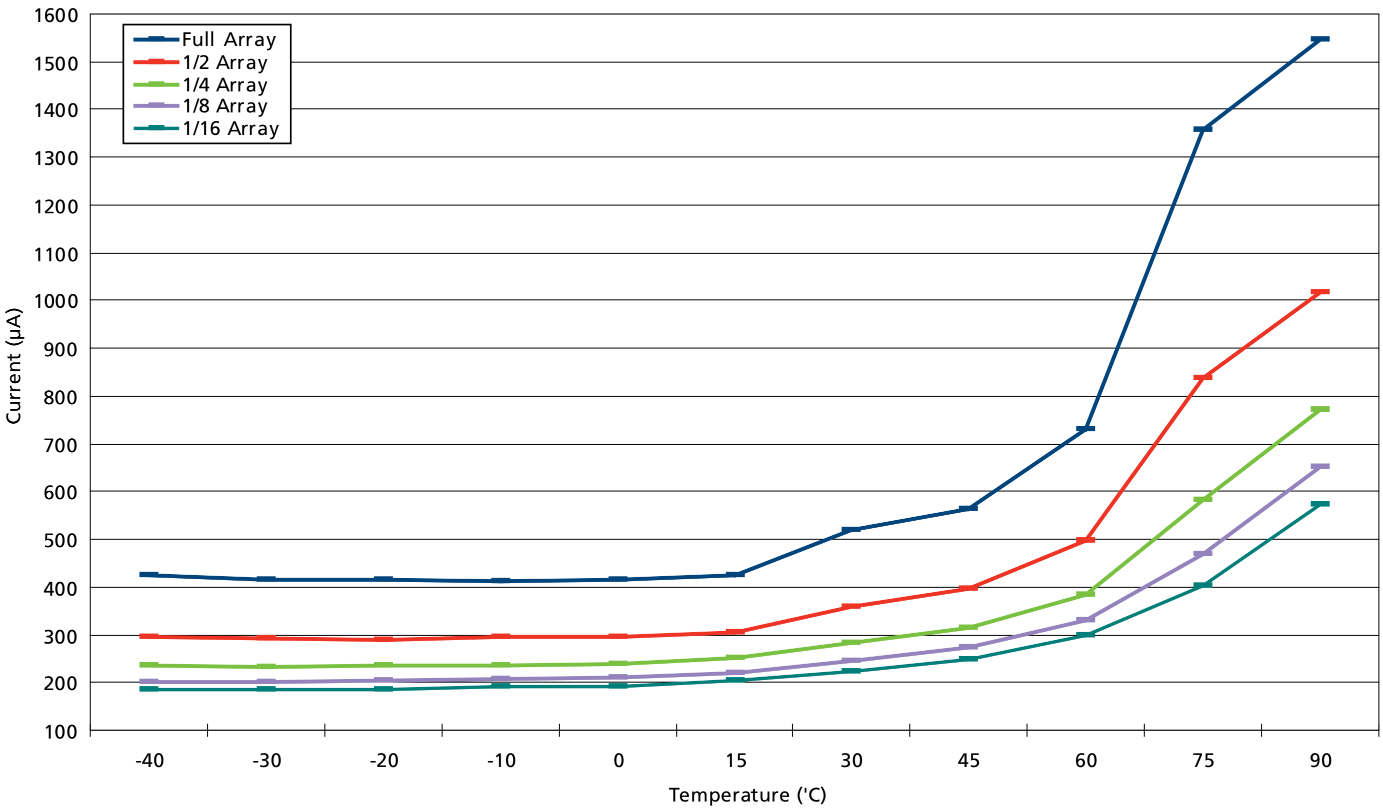
Table 23: $I_{DD}6$ Specifications and Conditions

Notes 1–5, 7, and 12 apply to all the parameters/conditions in this table; V_{DD}/V_{DDQ} = 1.70–1.95V

Parameter/Condition		Symbol	Value	Units
Self refresh: CKE = LOW; ^tCK = ^tCK (MIN); Address and control inputs are stable; Data bus inputs are stable	Full array, 105˚C	I_{DD6}	n/a[14]	µA
	Full array, 85˚C		2000	µA
	Full array, 45˚C		900	µA
	1/2 array, 85˚C		1450	µA
	1/2 array, 45˚C		700	µA
	1/4 array, 85˚C		1230	µA
	1/4 array, 45˚C		600	µA
	1/8 array, 85˚C		1090	µA
	1/8 array, 45˚C		575	µA
	1/16 array, 85˚C		1020	µA
	1/16 array, 45˚C		550	µA

Notes:
1. All voltages referenced to V_{SS}.
2. Tests for I_{DD} characteristics may be conducted at nominal supply voltage levels, but the related specifications and device operation are guaranteed for the full voltage range specified.
3. Timing and I_{DD} tests may use a V_{IL}-to-V_{IH} swing of up to 1.5V in the test environment, but input timing is still referenced to $V_{DDQ/2}$ (or to the crossing point for CK/CK#). The output timing reference voltage level is $V_{DDQ/2}$.
4. I_{DD} is dependent on output loading and cycle rates. Specified values are obtained with minimum cycle time with the outputs open.
5. I_{DD} specifications are tested after the device is properly initialized and values are averaged at the defined cycle rate.
6. MIN (^tRC or ^tRFC) for I_{DD} measurements is the smallest multiple of ^tCK that meets the minimum absolute value for the respective parameter. ^tRASmax for I_{DD} measurements is the largest multiple of ^tCK that meets the maximum absolute value for ^tRAS.
7. Measurement is taken 500ms after entering into this operating mode to provide settling time for the tester.
8. V_{DD} must not vary more than 4% if CKE is not active while any bank is active.
9. I_{DD2N} specifies DQ, DQS, and DM to be driven to a valid high or low logic level.
10. CKE must be active (HIGH) during the entire time a REFRESH command is executed. From the time the AUTO REFRESH command is registered, CKE must be active at each rising clock edge until ^tRFC later.
11. This limit is a nominal value and does not result in a fail. CKE is HIGH during REFRESH command period (^tRFC (MIN)) else CKE is LOW (for example, during standby).
12. Values for I_{DD6} 85˚C are guaranteed for the entire temperature range. All other I_{DD6} values are estimated.
13. Typical values at 25˚C, not a maximum value.
14. Self refresh is not supported for AT (85˚C to 105˚C) operation.

Figure 15: Typical Self Refresh Current vs. Temperature



Electrical Specifications – AC Operating Conditions

Table 24: Electrical Characteristics and Recommended AC Operating Conditions

Notes 1–9 apply to all the parameters in this table; V_{DD}/V_{DDQ} = 1.70–1.95V

Parameter		Symbol	-5		-54		-6		-75		Unit	Notes
			Min	Max	Min	Max	Min	Max	Min	Max		
Access window of DQ from CK/CK#	CL = 3	^{t}AC	2.0	5.0	2.0	5.0	2.0	5.0	2.0	6.0	ns	
	CL = 2		2.0	6.5	2.0	6.5	2.0	6.5	2.0	6.5		
Clock cycle time	CL = 3	^{t}CK	5.0	–	5.4	–	6	–	7.5	–	ns	10
	CL = 2		12	–	12	–	12	–	12	–		
CK high-level width		^{t}CH	0.45	0.55	0.45	0.55	0.45	0.55	0.45	0.55	^{t}CK	
CK low-level width		^{t}CL	0.45	0.55	0.45	0.55	0.45	0.55	0.45	0.55	^{t}CK	
CKE minimum pulse width (high and low)		^{t}CKE	1	–	1	–	1	–	1	–	^{t}CK	11
Auto precharge write recovery + precharge time		^{t}DAL	–	–	–	–	–	–	–	–	–	12
DQ and DM input hold time relative to DQS (fast slew rate)		$^{t}DH_{f}$	0.48	–	0.54	–	0.6	–	0.8	–	ns	13, 14, 15
DQ and DM input hold time relative to DQS (slow slew rate)		$^{t}DH_{s}$	0.58	–	0.64	–	0.7	–	0.9	–	ns	
DQ and DM input setup time relative to DQS (fast slew rate)		$^{t}DS_{f}$	0.48	–	0.54	–	0.6	–	0.8	–	ns	13, 14, 15
DQ and DM input setup time relative to DQS (slow slew rate)		$^{t}DS_{s}$	0.58	–	0.64	–	0.7	–	0.9	–	ns	
DQ and DM input pulse width (for each input)		^{t}DIPW	1.8	–	1.9	–	2.1	–	1.8	–	ns	16
Access window of DQS from CK/CK#	CL = 3	^{t}DQSCK	2.0	5.0	2.0	5.0	2.0	5.0	2.0	6.0	ns	
	CL = 2		2.0	6.5	2.0	6.5	2.0	6.5	2.0	6.5	ns	
DQS input high pulse width		^{t}DQSH	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	^{t}CK	
DQS input low pulse width		^{t}DQSL	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	^{t}CK	
DQS–DQ skew, DQS to last DQ valid, per group, per access		^{t}DQSQ	–	0.4	–	0.45	–	0.45	–	0.6	ns	13, 17
WRITE command to first DQS latching transition		^{t}DQSS	0.75	1.25	0.75	1.25	0.75	1.25	0.75	1.25	^{t}CK	
DQS falling edge from CK rising – hold time		^{t}DSH	0.2	–	0.2	–	0.2	–	0.2	–	^{t}CK	
DQS falling edge to CK rising – setup time		^{t}DSS	0.2	–	0.2	–	0.2	–	0.2	–	^{t}CK	

Table 24: Electrical Characteristics and Recommended AC Operating Conditions (Continued)

Notes 1–9 apply to all the parameters in this table; V_{DD}/V_{DDQ} = 1.70–1.95V

Parameter		Symbol	-5 Min	-5 Max	-54 Min	-54 Max	-6 Min	-6 Max	-75 Min	-75 Max	Unit	Notes
Data valid output window (DVW)		n/a	^tQH - ^tDQSQ		^tQH - ^tDQSQ		^tQH - ^tDQSQ		^tQH - ^tDQSQ		ns	17
Half-clock period		^tHP	^tCH, ^tCL	–	^tCH, ^tCL	–	^tCH, ^tCL	–	^tCH, ^tCL	–	ns	18
Data-out High-Z window from CK/CK#	CL = 3	^tHZ	–	5.0	–	5.0	–	5.0	–	6.0	ns	19, 20
	CL = 2		–	6.5	–	6.5	–	6.5	–	6.5	ns	
Data-out Low-Z window from CK/CK#		^tLZ	1.0	–	1.0	–	1.0	–	1.0	–	ns	19
Address and control input hold time (fast slew rate)		^tIH_F	0.9	–	1.0	–	1.1	–	1.3	–	ns	15, 21
Address and control input hold time (slow slew rate)		^tIH_S	1.1	–	1.2	–	1.3	–	1.5	–	ns	
Address and control input setup time (fast slew rate)		^tIS_F	0.9	–	1.0	–	1.1	–	1.3	–	ns	15, 21
Address and control input setup time (slow slew rate)		^tIS_S	1.1	–	1.2	–	1.3	–	1.5	–	ns	
Address and control input pulse width		^tIPW	2.3	–	2.5	–	2.6	–	^tIS + ^tIH	–	ns	16
LOAD MODE REGISTER command cycle time		^tMRD	2	–	2	–	2	–	2	–	^tCK	
DQ–DQS hold, DQS to first DQ to go nonvalid, per access		^tQH	^tHP - ^tQHS	–	^tHP - ^tQHS	–	^tHP - ^tQHS	–	^tHP - ^tQHS	–	ns	13, 17
Data hold skew factor		^tQHS	–	0.5	–	0.5	–	0.65	–	0.75	ns	
ACTIVE-to-PRECHARGE command		^tRAS	40	70,000	42	70,000	42	70,000	45	70,000	ns	22
ACTIVE to ACTIVE/ACTIVE to AUTO REFRESH command period		^tRC	55	–	58.2	–	60	–	67.5	–	ns	23
Active to read or write delay		^tRCD	15	–	16.2	–	18	–	22.5	–	ns	
Refresh period		^tREF	–	64	–	64	–	64	–	64	ms	24
Average periodic refresh interval: 64Mb, 128Mb, and 256Mb (x32)		^tREFI	–	15.6	–	15.6	–	15.6	–	15.6	µs	24
Average periodic refresh interval: 256Mb, 512Mb, 1Gb, 2Gb		^tREFI	–	7.8	–	7.8	–	7.8	–	7.8	µs	24

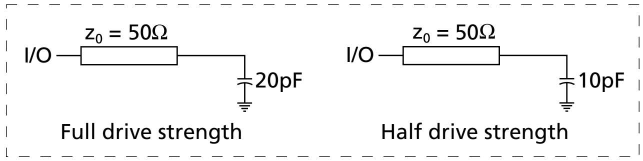
Table 24: Electrical Characteristics and Recommended AC Operating Conditions (Continued)

Notes 1–9 apply to all the parameters in this table; V_{DD}/V_{DDQ} = 1.70–1.95V

Parameter		Symbol	-5		-54		-6		-75		Unit	Notes
			Min	Max	Min	Max	Min	Max	Min	Max		
AUTO REFRESH command period		^tRFC	72	–	72	–	72	–	72	–	ns	
PRECHARGE command period		^tRP	15	–	16.2	–	18	–	22.5	–	ns	
DQS read preamble	CL = 3	^tRPRE	0.9	1.1	0.9	1.1	0.9	1.1	0.9	1.1	^tCK	
	CL = 2	^tRPRE	0.5	1.1	0.5	1.1	0.5	1.1	0.5	1.1	^tCK	
DQS read postamble		^tRPST	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	^tCK	
Active bank *a* to active bank *b* command		^tRRD	10	–	10.8	–	12	–	15	–	ns	
Read of SRR to next valid command		^tSRC	CL + 1	–	CL + 1	–	CL + 1	–	CL + 1	–	^tCK	
SRR to read		^tSRR	2	–	2	–	2	–	2	–	^tCK	
DQS write preamble		^tWPRE	0.25	–	0.25	–	0.25	–	0.25	–	^tCK	
DQS write preamble setup time		^tWPRES	0	–	0	–	0	–	0	–	ns	25, 26
DQS write postamble		^tWPST	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	^tCK	27
Write recovery time		^tWR	15	–	15	–	15	–	15	–	ns	28
Internal WRITE-to-READ command delay		^tWTR	2	–	2	–	1	–	1	–	^tCK	
Exit power-down mode to first valid command		^tXP	2	–	2	–	1	–	1	–	^tCK	
Exit self refresh to first valid command		^tXSR	112.5	–	112.5	–	112.5	–	112.5	–	ns	29

Notes:
1. All voltages referenced to V_{SS}.
2. All parameters assume proper device initialization.
3. Tests for AC timing and electrical AC and DC characteristics may be conducted at nominal supply voltage levels, but the related specifications and device operation are guaranteed for the full voltage ranges specified.
4. The circuit shown below represents the timing reference load used in defining the relevant timing parameters of the device. It is not intended to be either a precise representation of the typical system environment or a depiction of the actual load presented by a production tester. System designers will use IBIS or other simulation tools to correlate the timing reference load to system environment. Specifications are correlated to production test conditions (generally a coaxial transmission line terminated at the tester electronics). For the half-strength driver with a nominal 10pF load, parameters ^tAC and ^tQH are expected to be in the same range. However, these parameters are not subject to production test but are estimated by design/characterization. Use of IBIS or other simu-

lation tools for system design validation is suggested.



5. The CK/CK# input reference voltage level (for timing referenced to CK/CK#) is the point at which CK and CK# cross; the input reference voltage level for signals other than CK/CK# is $V_{DDQ/2}$.
6. A CK and CK# input slew rate ≥1 V/ns (2 V/ns if measured differentially) is assumed for all parameters.
7. All AC timings assume an input slew rate of 1 V/ns.
8. CAS latency definition: with CL = 2, the first data element is valid at (^{t}CK + ^{t}AC) after the clock at which the READ command was registered; for CL = 3, the first data element is valid at (2 × ^{t}CK + ^{t}AC) after the first clock at which the READ command was registered.
9. Timing tests may use a V_{IL}-to-V_{IH} swing of up to 1.5V in the test environment, but input timing is still referenced to $V_{DDQ/2}$ or to the crossing point for CK/CK#. The output timing reference voltage level is $V_{DDQ/2}$.
10. Clock frequency change is only permitted during clock stop, power-down, or self refresh mode.
11. In cases where the device is in self refresh mode for ^{t}CKE, ^{t}CKE starts at the rising edge of the clock and ends when CKE transitions HIGH.
12. ^{t}DAL = (^{t}WR/^{t}CK) + (^{t}RP/^{t}CK): for each term, if not already an integer, round up to the next highest integer.
13. Referenced to each output group: for x16, LDQS with DQ[7:0]; and UDQS with DQ[15:8]. For x32, DQS0 with DQ[7:0]; DQS1 with DQ[15:8]; DQS2 with DQ[23:16]; and DQS3 with DQ[31:24].
14. DQ and DM input slew rates must not deviate from DQS by more than 10%. If the DQ/DM/DQS slew rate is less than 1.0 V/ns, timing must be derated: 50ps must be added to ^{t}DS and ^{t}DH for each 100 mV/ns reduction in slew rate. If the slew rate exceeds 4 V/ns, functionality is uncertain.
15. The transition time for input signals (CAS#, CKE, CS#, DM, DQ, DQS, RAS#, WE#, and addresses) are measured between $V_{IL(DC)}$ to $V_{IH(AC)}$ for rising input signals and $V_{IH(DC)}$ to $V_{IL(AC)}$ for falling input signals.
16. These parameters guarantee device timing but are not tested on each device.
17. The valid data window is derived by achieving other specifications: ^{t}HP (^{t}CK/2), ^{t}DQSQ, and ^{t}QH (^{t}HP - ^{t}QHS). The data valid window derates directly proportional with the clock duty cycle and a practical data valid window can be derived. The clock is provided a maximum duty cycle variation of 45/55. Functionality is uncertain when operating beyond a 45/55 ratio.
18. ^{t}HP (MIN) is the lesser of ^{t}CL (MIN) and ^{t}CH (MIN) actually applied to the device CK and CK# inputs, collectively.
19. ^{t}HZ and ^{t}LZ transitions occur in the same access time windows as valid data transitions. These parameters are not referenced to a specific voltage level, but specify when the device output is no longer driving (^{t}HZ) or begins driving (^{t}LZ).
20. ^{t}HZ (MAX) will prevail over ^{t}DQSCK (MAX) + ^{t}RPST (MAX) condition.
21. Fast command/address input slew rate ≥1 V/ns. Slow command/address input slew rate ≥0.5 V/ns. If the slew rate is less than 0.5 V/ns, timing must be derated: ^{t}IS has an additional 50ps per each 100 mV/ns reduction in slew rate from the 0.5 V/ns. ^{t}IH has 0ps added, therefore, it remains constant. If the slew rate exceeds 4.5 V/ns, functionality is uncertain.
22. READs and WRITEs with auto precharge must not be issued until ^{t}RAS (MIN) can be satisfied prior to the internal PRECHARGE command being issued.

23. DRAM devices should be evenly addressed when being accessed. Disproportionate accesses to a particular row address may result in reduction of the product lifetime.
24. For the Automotive Temperature parts, ^{t}REF = ^{t}REF /2 and ^{t}REF I = ^{t}REF I/2 .
25. This is not a device limit. The device will operate with a negative value, but system performance could be degraded due to bus turnaround.
26. It is recommended that DQS be valid (HIGH or LOW) on or before the WRITE command. The case shown (DQS going from High-Z to logic low) applies when no WRITEs were previously in progress on the bus. If a previous WRITE was in progress, DQS could be HIGH during this time, depending on ^{t}DQSS.
27. The maximum limit for this parameter is not a device limit. The device will operate with a greater value for this parameter, but system performance (bus turnaround) will degrade accordingly.
28. At least 1 clock cycle is required during ^{t}WR time when in auto precharge mode.
29. Clock must be toggled a minimum of two times during the ^{t}XSR period.

Output Drive Characteristics

Table 25: Target Output Drive Characteristics (Full Strength)

Notes 1–2 apply to all values; characteristics are specified under best and worst process variations/conditions

Voltage (V)	Pull-Down Current (mA)		Pull-Up Current (mA)	
	Min	Max	Min	Max
0.00	0.00	0.00	0.00	0.00
0.10	2.80	18.53	–2.80	–18.53
0.20	5.60	26.80	–5.60	–26.80
0.30	8.40	32.80	–8.40	–32.80
0.40	11.20	37.05	–11.20	–37.05
0.50	14.00	40.00	–14.00	–40.00
0.60	16.80	42.50	–16.80	–42.50
0.70	19.60	44.57	–19.60	–44.57
0.80	22.40	46.50	–22.40	–46.50
0.85	23.80	47.48	–23.80	–47.48
0.90	23.80	48.50	–23.80	–48.50
0.95	23.80	49.40	–23.80	–49.40
1.00	23.80	50.05	–23.80	–50.05
1.10	23.80	51.35	–23.80	–51.35
1.20	23.80	52.65	–23.80	–52.65
1.30	23.80	53.95	–23.80	–53.95
1.40	23.80	55.25	–23.80	–55.25
1.50	23.80	56.55	–23.80	–56.55
1.60	23.80	57.85	–23.80	–57.85
1.70	23.80	59.15	–23.80	–59.15
1.80	–	60.45	–	–60.45
1.90	–	61.75	–	–61.75

Notes:
1. Based on nominal impedance of 25Ω (full strength) at $V_{DDQ}/2$.
2. The full variation in driver current from minimum to maximum, due to process, voltage, and temperature, will lie within the outer bounding lines of the I-V curves.

Table 26: Target Output Drive Characteristics (Three-Quarter Strength)

Notes 1–3 apply to all values; characteristics are specified under best and worst process variations/conditions

Voltage (V)	Pull-Down Current (mA)		Pull-Up Current (mA)	
	Min	Max	Min	Max
0.00	0.00	0.00	0.00	0.00
0.10	1.96	12.97	–1.96	–12.97
0.20	3.92	18.76	–3.92	–18.76
0.30	5.88	22.96	–5.88	–22.96
0.40	7.84	25.94	–7.84	–25.94
0.50	9.80	28.00	–9.80	–28.00
0.60	11.76	29.75	–11.76	–29.75
0.70	13.72	31.20	–13.72	–31.20
0.80	15.68	32.55	–15.68	–32.55
0.85	16.66	33.24	–16.66	–33.24
0.90	16.66	33.95	–16.66	–33.95
0.95	16.66	34.58	–16.66	–34.58
1.00	16.66	35.04	–16.66	–35.04
1.10	16.66	35.95	–16.66	–35.95
1.20	16.66	36.86	–16.66	–36.86
1.30	16.66	37.77	–16.66	–37.77
1.40	16.66	38.68	–16.66	–38.68
1.50	16.66	39.59	–16.66	–39.59
1.60	16.66	40.50	–16.66	–40.50
1.70	16.66	41.41	–16.66	–41.41
1.80	–	42.32	–	–42.32
1.90	–	43.23	–	–43.23

Notes:
1. Based on nominal impedance of 37Ω (three-quarter drive strength) at $V_{DDQ}/2$.
2. The full variation in driver current from minimum to maximum, due to process, voltage, and temperature, will lie within the outer bounding lines of the I-V curves.
3. Contact factory for availability of three-quarter drive strength.

Table 27: Target Output Drive Characteristics (One-Half Strength)

Notes 1–3 apply to all values; characteristics are specified under best and worst process variations/conditions

Voltage (V)	Pull-Down Current (mA)		Pull-Up Current (mA)	
	Min	Max	Min	Max
0.00	0.00	0.00	0.00	0.00
0.10	1.27	8.42	–1.27	–8.42
0.20	2.55	12.30	–2.55	–12.30
0.30	3.82	14.95	–3.82	–14.95
0.40	5.09	16.84	–5.09	–16.84
0.50	6.36	18.20	–6.36	–18.20
0.60	7.64	19.30	–7.64	–19.30
0.70	8.91	20.30	–8.91	–20.30
0.80	10.16	21.20	–10.16	–21.20
0.85	10.80	21.60	–10.80	–21.60
0.90	10.80	22.00	–10.80	–22.00
0.95	10.80	22.45	–10.80	–22.45
1.00	10.80	22.73	–10.80	–22.73
1.10	10.80	23.21	–10.80	–23.21
1.20	10.80	23.67	–10.80	–23.67
1.30	10.80	24.14	–10.80	–24.14
1.40	10.80	24.61	–10.80	–24.61
1.50	10.80	25.08	–10.80	–25.08
1.60	10.80	25.54	–10.80	–25.54
1.70	10.80	26.01	–10.80	–26.01
1.80	–	26.48	–	–26.48
1.90	–	26.95	–	–26.95

Notes:
1. Based on nominal impedance of 55Ω (one-half drive strength) at $V_{DDQ}/2$.
2. The full variation in driver current from minimum to maximum, due to process, voltage, and temperature, will lie within the outer bounding lines of the I-V curves.
3. The I-V curve for one-quarter drive strength is approximately 50% of one-half drive strength.

Functional Description

The Mobile LPDDR SDRAM uses a double data rate architecture to achieve high-speed operation. The double data rate architecture is essentially a $2n$-prefetch architecture, with an interface designed to transfer two data words per clock cycle at the I/O. Single read or write access for the device consists of a single $2n$-bit-wide, one-clock-cycle data transfer at the internal DRAM core and two corresponding n-bit-wide, one-half-clock-cycle data transfers at the I/O.

A bidirectional data strobe (DQS) is transmitted externally, along with data, for use in data capture at the receiver. DQS is a strobe transmitted by the device during READs and by the memory controller during WRITEs. DQS is edge-aligned with data for READs and center-aligned with data for WRITEs. The x16 device has two data strobes, one for the lower byte and one for the upper byte; the x32 device has four data strobes, one per byte.

The LPDDR device operates from a differential clock (CK and CK#); the crossing of CK going HIGH and CK# going LOW will be referred to as the positive edge of CK. Commands (address and control signals) are registered at every positive edge of CK. Input data is registered on both edges of DQS, and output data is referenced to both edges of DQS, as well as to both edges of CK.

Read and write accesses to the device are burst-oriented; accesses start at a selected location and continue for a programmed number of locations in a programmed sequence. Accesses begin with the registration of an ACTIVE command, followed by a READ or WRITE command. The address bits registered coincident with the ACTIVE command are used to select the bank and row to be accessed. The address bits registered coincident with the READ or WRITE command are used to select the starting column location for the burst access.

The device provides for programmable READ or WRITE burst lengths of 2, 4, 8, or 16. An auto precharge function can be enabled to provide a self-timed row precharge that is initiated at the end of the burst access.

As with standard DDR SDRAM, the pipelined, multibank architecture of LPDDR supports concurrent operation, thereby providing high effective bandwidth by hiding row precharge and activation time.

An auto refresh mode is provided, along with a power-saving power-down mode. Deep power-down mode is offered to achieve maximum power reduction by eliminating the power of the memory array. Data will not be retained after the device enters deep power-down mode.

Two self refresh features, temperature-compensated self refresh (TCSR) and partial-array self refresh (PASR), offer additional power savings. TCSR is controlled by the automatic on-chip temperature sensor. PASR can be customized using the extended mode register settings. The two features can be combined to achieve even greater power savings.

The DLL that is typically used on standard DDR devices is not necessary on LPDDR devices. It has been omitted to save power.

Commands

A quick reference for available commands is provided in Table 28 and Table 29 (page 57), followed by a written description of each command. Three additional truth tables (Table 30 (page 63), Table 31 (page 65), and Table 32 (page 67)) provide CKE commands and current/next state information.

Table 28: Truth Table – Commands

CKE is HIGH for all commands shown except SELF REFRESH and DEEP POWER-DOWN; all states and sequences not shown are reserved and/or illegal

Name (Function)	CS#	RAS#	CAS#	WE#	Address	Notes
DESELECT (NOP)	H	X	X	X	X	1
NO OPERATION (NOP)	L	H	H	H	X	1
ACTIVE (select bank and activate row)	L	L	H	H	Bank/row	2
READ (select bank and column, and start READ burst)	L	H	L	H	Bank/column	3
WRITE (select bank and column, and start WRITE burst)	L	H	L	L	Bank/column	3
BURST TERMINATE or DEEP POWER-DOWN (enter deep power-down mode)	L	H	H	L	X	4, 5
PRECHARGE (deactivate row in bank or banks)	L	L	H	L	Code	6
AUTO REFRESH (refresh all or single bank) or SELF REFRESH (enter self refresh mode)	L	L	L	H	X	7, 8
LOAD MODE REGISTER	L	L	L	L	Op-code	9

Notes:
1. DESELECT and NOP are functionally interchangeable.
2. BA0–BA1 provide bank address and A[0:*I*] provide row address (where *I* = the most significant address bit for each configuration).
3. BA0–BA1 provide bank address; A[0:*I*] provide column address (where *I* = the most significant address bit for each configuration); A10 HIGH enables the auto precharge feature (nonpersistent); A10 LOW disables the auto precharge feature.
4. Applies only to READ bursts with auto precharge disabled; this command is undefined and should not be used for READ bursts with auto precharge enabled and for WRITE bursts.
5. This command is a BURST TERMINATE if CKE is HIGH and DEEP POWER-DOWN if CKE is LOW.
6. A10 LOW: BA0–BA1 determine which bank is precharged.
   A10 HIGH: all banks are precharged and BA0–BA1 are "Don't Care."
7. This command is AUTO REFRESH if CKE is HIGH, SELF REFRESH if CKE is LOW.
8. Internal refresh counter controls row addressing; in self refresh mode all inputs and I/Os are "Don't Care" except for CKE.
9. BA0–BA1 select the standard mode register, extended mode register, or status register.

Table 29: DM Operation Truth Table

Name (Function)	DM	DQ	Notes
Write enable	L	Valid	1, 2
Write inhibit	H	X	1, 2

Notes: 1. Used to mask write data; provided coincident with the corresponding data.
2. All states and sequences not shown are reserved and/or illegal.

DESELECT

The DESELECT function (CS# HIGH) prevents new commands from being executed by the device. Operations already in progress are not affected.

NO OPERATION

The NO OPERATION (NOP) command is used to instruct the selected device to perform a NOP. This prevents unwanted commands from being registered during idle or wait states. Operations already in progress are not affected.

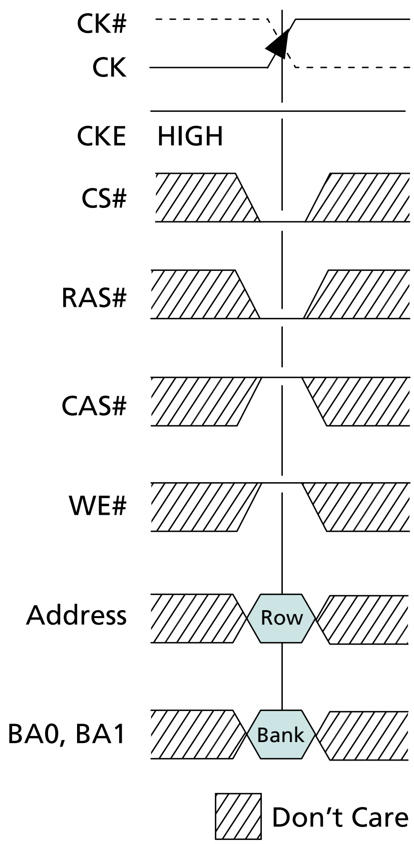
LOAD MODE REGISTER

The mode registers are loaded via inputs A[0:*n*]. See mode register descriptions in Standard Mode Register and Extended Mode Register. The LOAD MODE REGISTER command can only be issued when all banks are idle, and a subsequent executable command cannot be issued until ^{t}MRD is met.

ACTIVE

The ACTIVE command is used to activate a row in a particular bank for a subsequent access. The values on the BA0 and BA1 inputs select the bank, and the address provided on inputs A[0:*n*] selects the row. This row remains active for accesses until a PRECHARGE command is issued to that bank. A PRECHARGE command must be issued before opening a different row in the same bank.

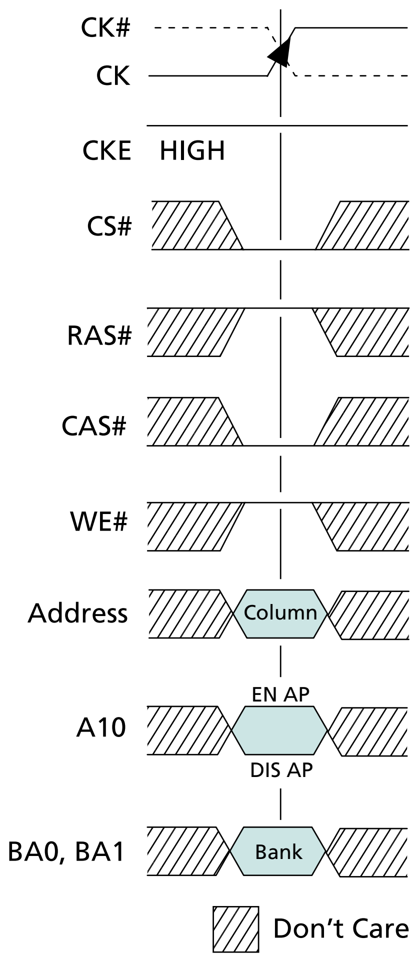
Figure 16: ACTIVE Command



READ

The READ command is used to initiate a burst read access to an active row. The values on the BA0 and BA1 inputs select the bank; the address provided on inputs A[*I*:0] (where *I* = the most significant column address bit for each configuration) selects the starting column location. The value on input A10 determines whether auto precharge is used. If auto precharge is selected, the row being accessed will be precharged at the end of the READ burst; if auto precharge is not selected, the row will remain open for subsequent accesses.

Figure 17: READ Command



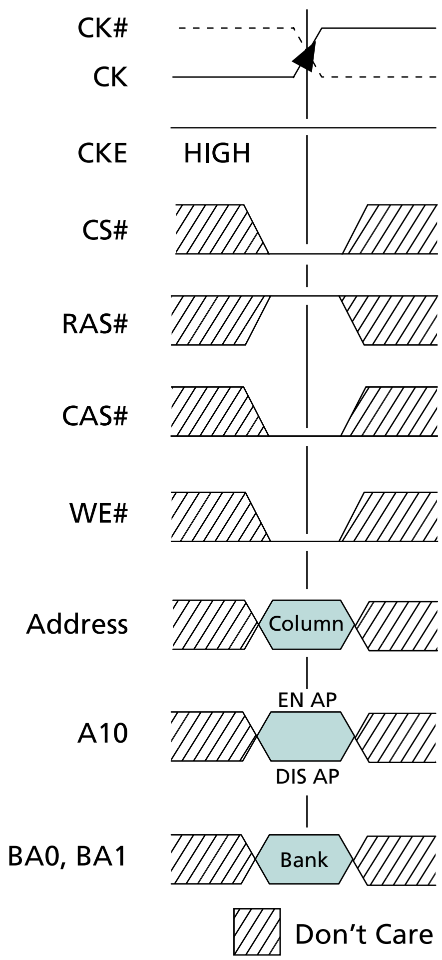
Note: 1. EN AP = enable auto precharge; DIS AP = disable auto precharge.

WRITE

The WRITE command is used to initiate a burst write access to an active row. The values on the BA0 and BA1 inputs select the bank; the address provided on inputs A[*I*:0] (where *I* = the most significant column address bit for each configuration) selects the starting column location. The value on input A10 determines whether auto precharge is used. If auto precharge is selected, the row being accessed will be precharged at the end of the WRITE burst; if auto precharge is not selected, the row will remain open for subsequent accesses. Input data appearing on the DQ is written to the memory array, subject to the DM input logic level appearing coincident with the data. If a given DM signal is registered LOW, the corresponding data will be written to memory; if the DM signal is registered HIGH, the corresponding data inputs will be ignored, and a WRITE will not be executed to that byte/column location.

If a WRITE or a READ is in progress, the entire data burst must be complete prior to stopping the clock (see Clock Change Frequency (page 116)). A burst completion for WRITEs is defined when the write postamble and ^{t}WR or ^{t}WTR are satisfied.

Figure 18: WRITE Command

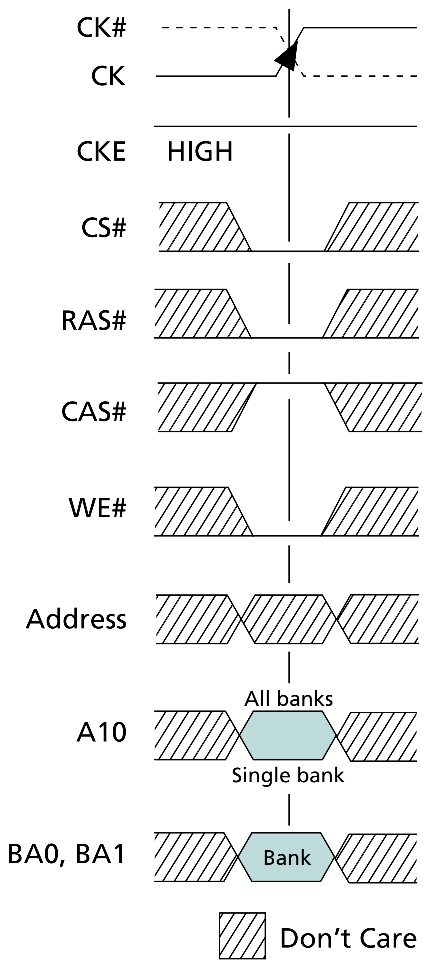


Note: 1. EN AP = enable auto precharge; DIS AP = disable auto precharge.

PRECHARGE

The PRECHARGE command is used to deactivate the open row in a particular bank or the open row in all banks. The bank(s) will be available for a subsequent row access a specified time (^{t}RP) after the PRECHARGE command is issued. Input A10 determines whether one or all banks will be precharged, and in the case where only one bank is precharged, inputs BA0 and BA1 select the bank. Otherwise, BA0 and BA1 are treated as "Don't Care." After a bank has been precharged, it is in the idle state and must be activated prior to any READ or WRITE commands being issued to that bank.

Figure 19: PRECHARGE Command



Note: 1. If A10 is HIGH, bank address becomes "Don't Care."

BURST TERMINATE

The BURST TERMINATE command is used to truncate READ bursts with auto precharge disabled. The most recently registered READ command prior to the BURST TERMINATE command will be truncated, as described in READ Operation. The open page from which the READ was terminated remains open.

AUTO REFRESH

AUTO REFRESH is used during normal operation of the device and is analogous to CAS#-BEFORE-RAS# (CBR) REFRESH in FPM/EDO DRAM. The AUTO REFRESH command is nonpersistent and must be issued each time a refresh is required.

Addressing is generated by the internal refresh controller. This makes the address bits a "Don't Care" during an AUTO REFRESH command.

For improved efficiency in scheduling and switching between tasks, some flexibility in the absolute refresh interval is provided. The auto refresh period begins when the AUTO REFRESH command is registered and ends ^{t}RFC later.

SELF REFRESH

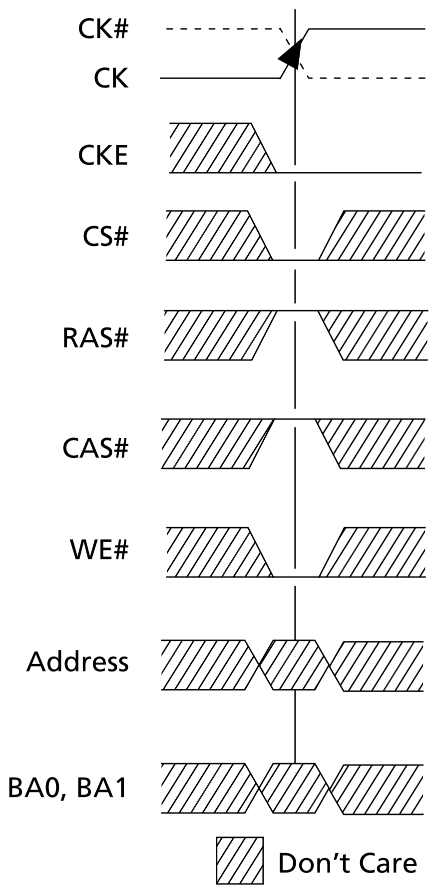
The SELF REFRESH command is used to place the device in self refresh mode; self refresh mode is used to retain data in the memory device while the rest of the system is powered down. When in self refresh mode, the device retains data without external clocking. The SELF REFRESH command is initiated like an AUTO REFRESH command, except that CKE is disabled (LOW). After the SELF REFRESH command is registered, all inputs to the device become “Don’t Care” with the exception of CKE, which must remain LOW.

Micron recommends that, prior to self refresh entry and immediately upon self refresh exit, the user perform a burst auto refresh cycle for the number of refresh rows. Alternatively, if a distributed refresh pattern is used, this pattern should be immediately resumed upon self refresh exit.

DEEP POWER-DOWN

The DEEP POWER-DOWN (DPD) command is used to enter DPD mode, which achieves maximum power reduction by eliminating the power to the memory array. Data will not be retained when the device enters DPD mode. The DPD command is the same as a BURST TERMINATE command with CKE LOW.

Figure 20: DEEP POWER-DOWN Command



Truth Tables

Table 30: Truth Table – Current State Bank *n* – Command to Bank *n*

Notes 1–6 apply to all parameters in this table

Current State	CS#	RAS#	CAS#	WE#	Command/Action	Notes
Any	H	X	X	X	DESELECT (NOP/continue previous operation)	
	L	H	H	H	NO OPERATION (NOP/continue previous operation)	
Idle	L	L	H	H	ACTIVE (select and activate row)	
	L	L	L	H	AUTO REFRESH	7
	L	L	L	L	LOAD MODE REGISTER	7
Row active	L	H	L	H	READ (select column and start READ burst)	10
	L	H	L	L	WRITE (select column and start WRITE burst)	10
	L	L	H	L	PRECHARGE (deactivate row in bank or banks)	8
Read (auto pre-charge disabled)	L	H	L	H	READ (select column and start new READ burst)	10
	L	H	L	L	WRITE (select column and start WRITE burst)	10, 12
	L	L	H	L	PRECHARGE (truncate READ burst, start PRECHARGE)	8
	L	H	H	L	BURST TERMINATE	9
Write (auto pre-charge disabled)	L	H	L	H	READ (select column and start READ burst)	10, 11
	L	H	L	L	WRITE (select column and start new WRITE burst)	10
	L	L	H	L	PRECHARGE (truncate WRITE burst, start PRECHARGE)	8, 11

Notes:
1. This table applies when CKE_{n-1} was HIGH, CKE_n is HIGH and after ^tXSR has been met (if the previous state was self refresh), after ^tXP has been met (if the previous state was power-down), or after a full initialization (if the previous state was deep power-down).
2. This table is bank-specific, except where noted (for example, the current state is for a specific bank and the commands shown are supported for that bank when in that state). Exceptions are covered in the notes below.
3. Current state definitions:

   Idle: The bank has been precharged, and ^tRP has been met.

   Row active: A row in the bank has been activated, and ^tRCD has been met. No data bursts/accesses and no register accesses are in progress.

   Read: A READ burst has been initiated with auto precharge disabled and has not yet terminated or been terminated.

   Write: A WRITE burst has been initiated with auto precharge disabled and has not yet terminated or been terminated.
4. The states listed below must not be interrupted by a command issued to the same bank. COMMAND INHIBIT or NOP commands, or supported commands to the other bank, must be issued on any clock edge occurring during these states. Supported commands to any other bank are determined by that bank's current state.

   Precharging: Starts with registration of a PRECHARGE command and ends when ^tRP is met. After ^tRP is met, the bank will be in the idle state.

   Row activating: Starts with registration of an ACTIVE command and ends when ^tRCD is met. After ^tRCD is met, the bank will be in the row active state.

Read with auto-precharge enabled: Starts with registration of a READ command with auto precharge enabled and ends when ^{t}RP has been met. After ^{t}RP is met, the bank will be in the idle state.

Write with auto-precharge enabled: Starts with registration of a WRITE command with auto precharge enabled and ends when ^{t}RP has been met. After ^{t}RP is met, the bank will be in the idle state.

5. The states listed below must not be interrupted by any executable command; DESELECT or NOP commands must be applied on each positive clock edge during these states.

   Refreshing: Starts with registration of an AUTO REFRESH command and ends when ^{t}RFC is met. After ^{t}RFC is met, the device will be in the all banks idle state.

   Accessing mode register: Starts with registration of a LOAD MODE REGISTER command and ends when ^{t}MRD has been met. After ^{t}MRD is met, the device will be in the all banks idle state.

   Precharging all: Starts with registration of a PRECHARGE ALL command and ends when ^{t}RP is met. After ^{t}RP is met, all banks will be in the idle state.
6. All states and sequences not shown are illegal or reserved.
7. Not bank-specific; requires that all banks are idle, and bursts are not in progress.
8. May or may not be bank-specific; if multiple banks need to be precharged, each must be in a valid state for precharging.
9. Not bank-specific; BURST TERMINATE affects the most recent READ burst, regardless of bank.
10. READs or WRITEs listed in the Command/Action column include READs or WRITEs with auto precharge enabled and READs or WRITEs with auto precharge disabled.
11. Requires appropriate DM masking.
12. A WRITE command can be applied after the completion of the READ burst; otherwise, a BURST TERMINATE must be used to end the READ burst prior to asserting a WRITE command.

Table 31: Truth Table – Current State Bank *n* – Command to Bank *m*

Notes 1–6 apply to all parameters in this table

Current State	CS#	RAS#	CAS#	WE#	Command/Action	Notes
Any	H	X	X	X	DESELECT (NOP/continue previous operation)	
	L	H	H	H	NO OPERATION (NOP/continue previous operation)	
Idle	X	X	X	X	Any command supported to bank *m*	
Row activating, active, or pre-charging	L	L	H	H	ACTIVE (select and activate row)	
	L	H	L	H	READ (select column and start READ burst)	
	L	H	L	L	WRITE (select column and start WRITE burst)	
	L	L	H	L	PRECHARGE	
Read (auto pre-charge disabled)	L	L	H	H	ACTIVE (select and activate row)	
	L	H	L	H	READ (select column and start new READ burst)	
	L	H	L	L	WRITE (select column and start WRITE burst)	7
	L	L	H	L	PRECHARGE	
Write (auto pre-charge disabled)	L	L	H	H	ACTIVE (select and activate row)	
	L	H	L	H	READ (select column and start READ burst)	
	L	H	L	L	WRITE (select column and start new WRITE burst)	
	L	L	H	L	PRECHARGE	
Read (with auto precharge)	L	L	H	H	ACTIVE (select and activate row)	
	L	H	L	H	READ (select column and start new READ burst)	
	L	H	L	L	WRITE (select column and start WRITE burst)	7
	L	L	H	L	PRECHARGE	
Write (with auto precharge)	L	L	H	H	ACTIVE (select and activate row)	
	L	H	L	H	READ (select column and start READ burst)	
	L	H	L	L	WRITE (select column and start new WRITE burst)	
	L	L	H	L	PRECHARGE	

Notes:

1. This table applies when CKE_{n-1} was HIGH, CKE_n is HIGH and after ^tXSR has been met (if the previous state was self refresh), after ^tXP has been met (if the previous state was power-down) or after a full initialization (if the previous state was deep power-down).
2. This table describes alternate bank operation, except where noted (for example, the current state is for bank *n* and the commands shown are those supported for issue to bank *m*, assuming that bank *m* is in such a state that the given command is supported). Exceptions are covered in the notes below.
3. Current state definitions:

   Idle: The bank has been precharged, and ^tRP has been met.

   Row active: A row in the bank has been activated, and ^tRCD has been met. No data bursts/accesses and no register accesses are in progress.

   Read: A READ burst has been initiated and has not yet terminated or been terminated.

   Write: A WRITE burst has been initiated and has not yet terminated or been terminated.

   3a. Both the read with auto precharge enabled state or the write with auto precharge enabled state can be broken into two parts: the access period and the precharge period. For read with auto precharge, the precharge period is defined as if the same burst was executed with auto precharge disabled and then followed with the earliest possible PRECHARGE command that still accesses all of the data in the burst. For write with auto precharge, the precharge period begins when ^tWR ends, with ^tWR measured as if auto precharge was disabled. The access period starts with registration of the command and ends when the precharge period (or ^tRP) begins. This device supports concurrent auto precharge such that when a read with auto precharge is enabled or a write with auto precharge is enabled, any command to other banks is supported, as long as that command does not interrupt the read or write data transfer already in process. In either case, all other related limitations apply (i.e., contention between read data and write data must be avoided).

3b. The minimum delay from a READ or WRITE command (with auto precharge enabled) to a command to a different bank is summarized below.

From Command	To Command	Minimum Delay (with Concurrent Auto Precharge)
WRITE with Auto Precharge	READ or READ with auto precharge WRITE or WRITE with auto precharge PRECHARGE ACTIVE	[1 + (BL/2)] ^tCK + ^tWTR (BL/2) ^tCK 1 ^tCK 1 ^tCK
READ with Auto Precharge	READ or READ with auto precharge WRITE or WRITE with auto precharge PRECHARGE ACTIVE	(BL/2) × ^tCK [CL + (BL/2)] ^tCK 1 ^tCK 1 ^tCK

4. AUTO REFRESH and LOAD MODE REGISTER commands can only be issued when all banks are idle.
5. All states and sequences not shown are illegal or reserved.
6. Requires appropriate DM masking.
7. A WRITE command can be applied after the completion of the READ burst; otherwise, a BURST TERMINATE must be used to end the READ burst prior to asserting a WRITE command.

Table 32: Truth Table – CKE

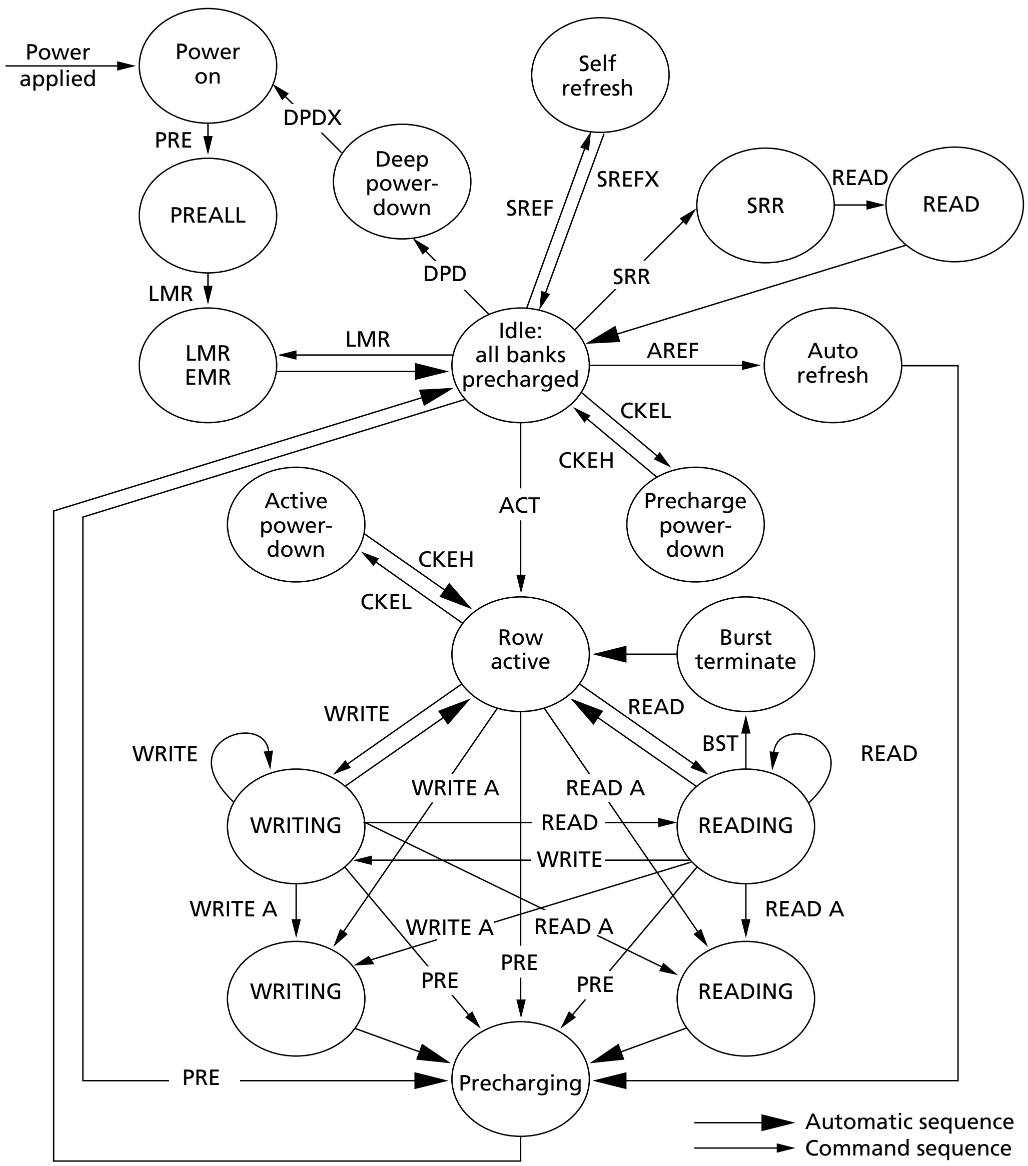
Notes 1–4 apply to all parameters in this table

Current State	CKE_{n-1}	CKE_n	$COMMAND_n$	$ACTION_n$	Notes
Active power-down	L	L	X	Maintain active power-down	
Deep power-down	L	L	X	Maintain deep power-down	
Precharge power-down	L	L	X	Maintain precharge power-down	
Self refresh	L	L	X	Maintain self refresh	
Active power-down	L	H	DESELECT or NOP	Exit active power-down	5
Deep power-down	L	H	DESELECT or NOP	Exit deep power-down	6
Precharge power-down	L	H	DESELECT or NOP	Exit precharge power-down	
Self refresh	L	H	DESELECT or NOP	Exit self refresh	5, 7
Bank(s) active	H	L	DESELECT or NOP	Active power-down entry	
All banks idle	H	L	BURST TERMINATE	Deep power-down entry	
All banks idle	H	L	DESELECT or NOP	Precharge power-down entry	
All banks idle	H	L	AUTO REFRESH	Self refresh entry	
	H	H	See Table 31 (page 65)		
	H	H	See Table 31 (page 65)		

Notes:
1. CKE_n is the logic state of CKE at clock edge *n*; CKE_{n-1} was the state of CKE at the previous clock edge.
2. Current state is the state of the DDR SDRAM immediately prior to clock edge *n*.
3. $COMMAND_n$ is the command registered at clock edge *n*, and $ACTION_n$ is a result of $COMMAND_n$.
4. All states and sequences not shown are illegal or reserved.
5. DESELECT or NOP commands should be issued on each clock edge occurring during the ^tXP or ^tXSR period.
6. After exiting deep power-down mode, a full DRAM initialization sequence is required.
7. The clock must toggle at least two times during the ^tXSR period.

State Diagram

Figure 21: Simplified State Diagram



ACT = ACTIVE	DPDX = Exit deep power-down	READ A = READ w/ auto precharge
AREF = AUTO REFRESH	EMR = LOAD EXTENDED MODE REGISTER	SREF = Enter self refresh
BST = BURST TERMINATE	LMR = LOAD MODE REGISTER	SREFX = Exit self refresh
CKEH = Exit power-down	PRE = PRECHARGE	SRR = STATUS REGISTER READ
CKEL = Enter power-down	PREALL = PRECHARGE all banks	WRITE = WRITE w/o auto precharge
DPD = Enter deep power-down	READ = READ w/o auto precharge	WRITE A = WRITE w/ auto precharge

Initialization

Prior to normal operation, the device must be powered up and initialized in a predefined manner. Using initialization procedures other than those specified will result in undefined operation.

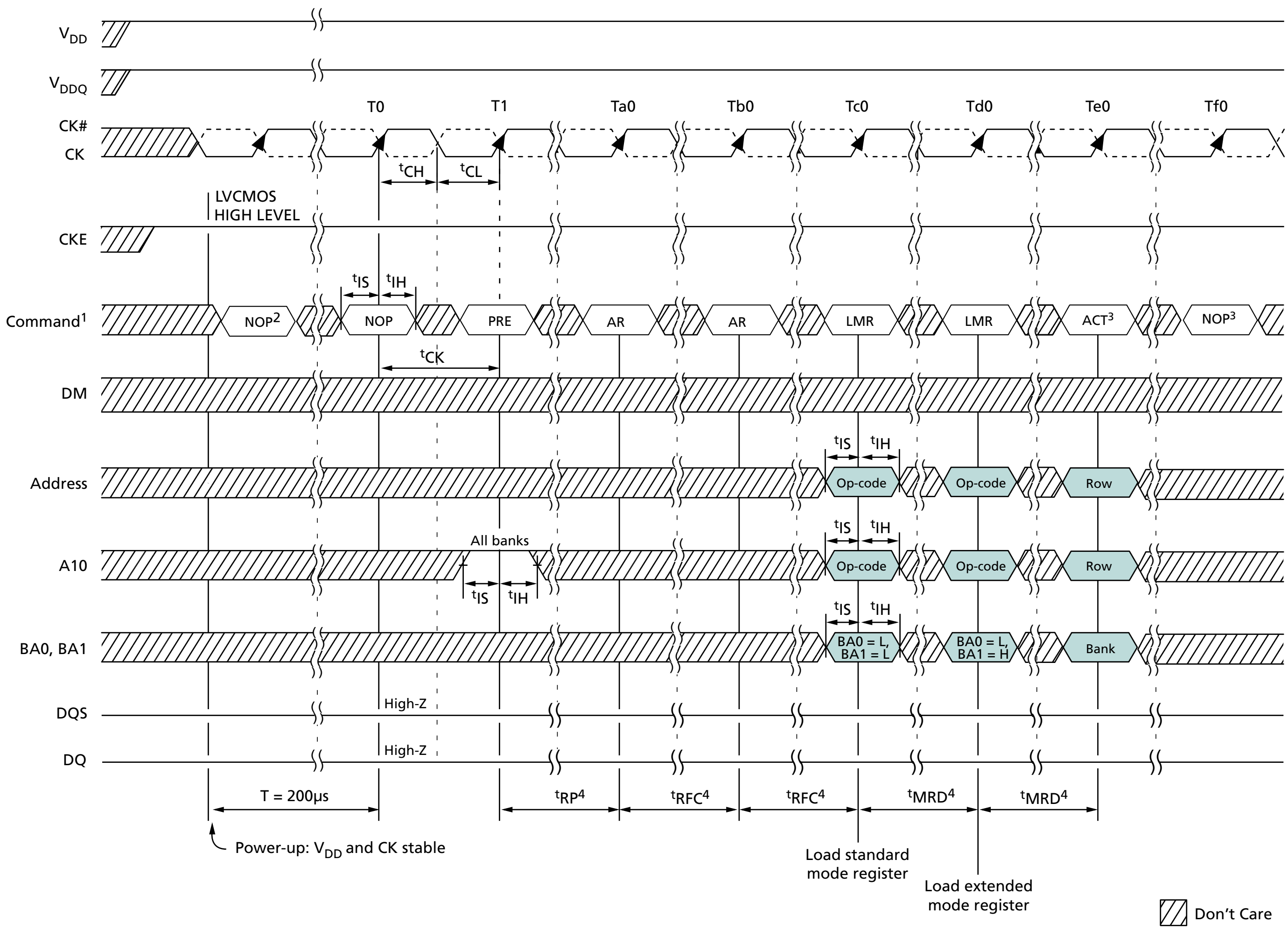
If there is an interruption to the device power, the device must be re-initialized using the initialization sequence described below to ensure proper functionality of the device.

To properly initialize the device, this sequence must be followed:

1. The core power (V_{DD}) and I/O power (V_{DDQ}) must be brought up simultaneously. It is recommended that V_{DD} and V_{DDQ} be from the same power source, or V_{DDQ} must never exceed V_{DD}. Standard initialization requires that CKE be asserted HIGH (see Figure 22 (page 70)). Alternatively, initialization can be completed with CKE LOW provided that CKE transitions HIGH ^{t}IS prior to T0 (see Figure 23 (page 71)).
2. When power supply voltages are stable and the CKE has been driven HIGH, it is safe to apply the clock.
3. When the clock is stable, a 200µs minimum delay is required by the Mobile LPDDR prior to applying an executable command. During this time, NOP or DESELECT commands must be issued on the command bus.
4. Issue a PRECHARGE ALL command.
5. Issue NOP or DESELECT commands for at least ^{t}RP time.
6. Issue an AUTO REFRESH command followed by NOP or DESELECT commands for at least ^{t}RFC time. Issue a second AUTO REFRESH command followed by NOP or DESELECT commands for at least ^{t}RFC time. Two AUTO REFRESH commands must be issued. Typically, both of these commands are issued at this stage as described above.
7. Using the LOAD MODE REGISTER command, load the standard mode register as desired.
8. Issue NOP or DESELECT commands for at least ^{t}MRD time.
9. Using the LOAD MODE REGISTER command, load the extended mode register to the desired operating modes. Note that the sequence in which the standard and extended mode registers are programmed is not critical.
10. Issue NOP or DESELECT commands for at least ^{t}MRD time.

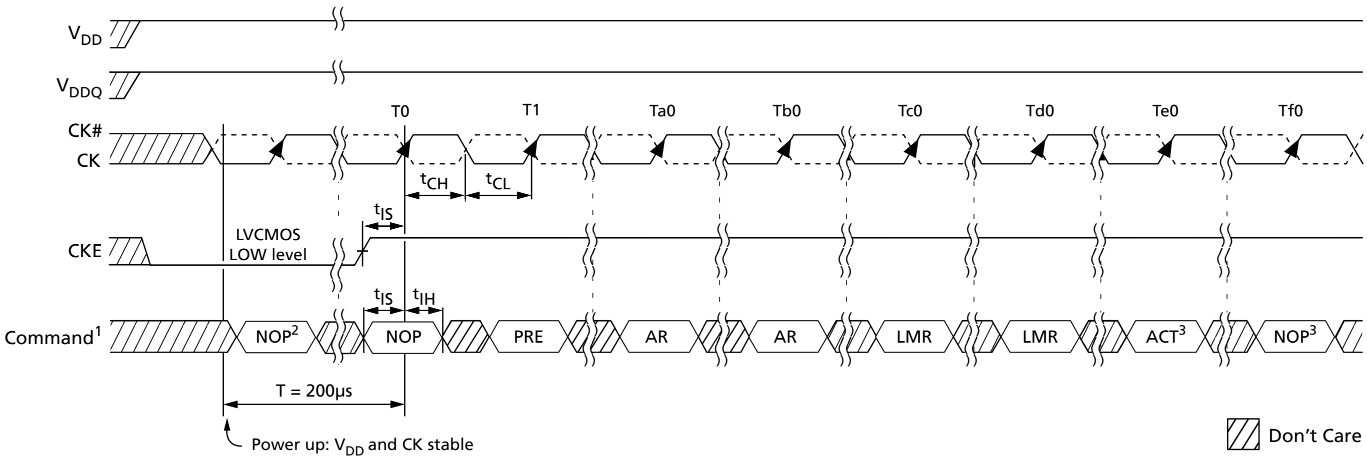
After steps 1–10 are completed, the device has been properly initialized and is ready to receive any valid command.

Figure 22: Initialize and Load Mode Registers



Notes:
1. PRE = PRECHARGE command; LMR = LOAD MODE REGISTER command; AR = AUTO REFRESH command; ACT = ACTIVE command.
2. NOP or DESELECT commands are required for at least 200µs.
3. Other valid commands are possible.
4. NOPs or DESELECTs are required during this time.

Figure 23: Alternate Initialization with CKE LOW



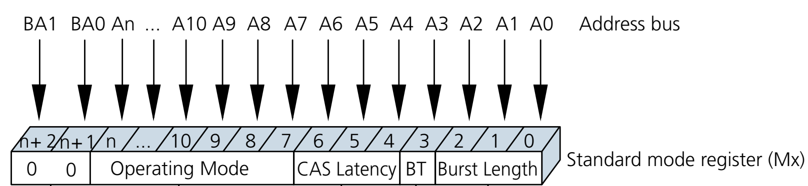
Notes:
1. PRE = PRECHARGE command; LMR = LOAD MODE REGISTER command; AR = AUTO REFRESH command; ACT = ACTIVE command.
2. NOP or DESELECT commands are required for at least 200µs.
3. Other valid commands are possible.

Standard Mode Register

The standard mode register bit definition enables the selection of burst length, burst type, CAS latency (CL), and operating mode, as shown in Figure 24. Reserved states should not be used as this may result in setting the device into an unknown state or cause incompatibility with future versions of LPDDR devices. The standard mode register is programmed via the LOAD MODE REGISTER command (with BA0 = 0 and BA1 = 0) and will retain the stored information until it is programmed again, until the device goes into deep power-down mode, or until the device loses power.

Reprogramming the mode register will not alter the contents of the memory, provided it is performed correctly. The mode register must be loaded when all banks are idle and no bursts are in progress, and the controller must wait ^{t}MRD before initiating the subsequent operation. Violating any of these requirements will result in unspecified operation.

Figure 24: Standard Mode Register Definition



Mn + 2	Mn + 1	Mode Register Definition
0	0	Standard mode register
0	1	Status register
1	0	Extended mode register
1	1	Reserved

Mn	...	M10	M9	M8	M7	Operating Mode
0		0	0	0	0	Normal operation
–		–	–	–	–	All other states reserved

			Burst Length	
M2	M1	M0	M3 = 0	M3 = 1
0	0	0	Reserved	Reserved
0	0	1	2	2
0	1	0	4	4
0	1	1	8	8
1	0	0	16	16
1	0	1	Reserved	Reserved
1	1	0	Reserved	Reserved
1	1	1	Reserved	Reserved

M6	M5	M4	CAS Latency
0	0	0	Reserved
0	0	1	Reserved
0	1	0	2
0	1	1	3
1	0	0	Reserved
1	0	1	Reserved
1	1	0	Reserved
1	1	1	Reserved

M3	Burst Type
0	Sequential
1	Interleaved

Note: 1. The integer *n* is equal to the most significant address bit.

Burst Length

Read and write accesses to the device are burst-oriented, and the burst length (BL) is programmable. The burst length determines the maximum number of column locations that can be accessed for a given READ or WRITE command. Burst lengths of 2, 4, 8, or 16 locations are available for both sequential and interleaved burst types.

When a READ or WRITE command is issued, a block of columns equal to the burst length is effectively selected. All accesses for that burst take place within this block, meaning that the burst will wrap when a boundary is reached. The block is uniquely selected by A[*i*:1] when BL = 2, by A[*i*:2] when BL = 4, by A[*i*:3] when BL = 8, and by A[*i*:4] when BL = 16, where A*i* is the most significant column address bit for a given configuration. The remaining (least significant) address bits are used to specify the starting location within the block. The programmed burst length applies to both READ and WRITE bursts.

Burst Type

Accesses within a given burst can be programmed to be either sequential or interleaved via the standard mode register.

The ordering of accesses within a burst is determined by the burst length, the burst type, and the starting column address.

Table 33: Burst Definition Table

Burst Length	Starting Column Address				Order of Accesses Within a Burst	
					Type = Sequential	Type = Interleaved
2				**A0**		
				0	0-1	0-1
				1	1-0	1-0
4			**A1**	**A0**		
			0	0	0-1-2-3	0-1-2-3
			0	1	1-2-3-0	1-0-3-2
			1	0	2-3-0-1	2-3-0-1
			1	1	3-0-1-2	3-2-1-0
8		**A2**	**A1**	**A0**		
		0	0	0	0-1-2-3-4-5-6-7	0-1-2-3-4-5-6-7
		0	0	1	1-2-3-4-5-6-7-0	1-0-3-2-5-4-7-6
		0	1	0	2-3-4-5-6-7-0-1	2-3-0-1-6-7-4-5
		0	1	1	3-4-5-6-7-0-1-2	3-2-1-0-7-6-5-4
		1	0	0	4-5-6-7-0-1-2-3	4-5-6-7-0-1-2-3
		1	0	1	5-6-7-0-1-2-3-4	5-4-7-6-1-0-3-2
		1	1	0	6-7-0-1-2-3-4-5	6-7-4-5-2-3-0-1
		1	1	1	7-0-1-2-3-4-5-6	7-6-5-4-3-2-1-0
16	**A3**	**A2**	**A1**	**A0**		

Table 33: Burst Definition Table (Continued)

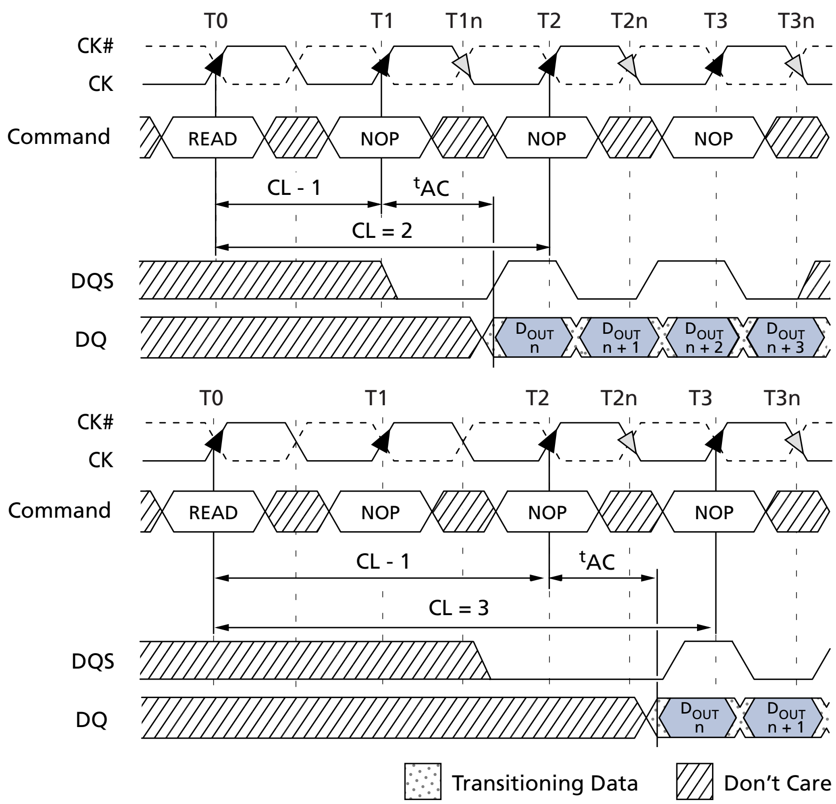
Burst Length	Starting Column Address				Order of Accesses Within a Burst	
					Type = Sequential	Type = Interleaved
	0	0	0	0	0-1-2-3-4-5-6-7-8-9-A-B-C-D-E-F	0-1-2-3-4-5-6-7-8-9-A-B-C-D-E-F
	0	0	0	1	1-2-3-4-5-6-7-8-9-A-B-C-D-E-F-0	1-0-3-2-5-4-7-6-9-8-B-A-D-C-F-E
	0	0	1	0	2-3-4-5-6-7-8-9-A-B-C-D-E-F-0-1	2-3-0-1-6-7-4-5-A-B-8-9-E-F-C-D
	0	0	1	1	3-4-5-6-7-8-9-A-B-C-D-E-F-0-1-2	3-2-1-0-7-6-5-4-B-A-9-8-F-E-D-C
	0	1	0	0	4-5-6-7-8-9-A-B-C-D-E-F-0-1-2-3	4-5-6-7-0-1-2-3-C-D-E-F-8-9-A-B
	0	1	0	1	5-6-7-8-9-A-B-C-D-E-F-0-1-2-3-4	5-4-7-6-1-0-3-2-D-C-F-E-9-8-B-A
	0	1	1	0	6-7-8-9-A-B-C-D-E-F-0-1-2-3-4-5	6-7-4-5-2-3-0-1-E-F-C-D-A-B-8-9
	0	1	1	1	7-8-9-A-B-C-D-E-F-0-1-2-3-4-5-6	7-6-5-4-3-2-1-0-F-E-D-C-B-A-9-8
	1	0	0	0	8-9-A-B-C-D-E-F-0-1-2-3-4-5-6-7	8-9-A-B-C-D-E-F-0-1-2-3-4-5-6-7
	1	0	0	1	9-A-B-C-D-E-F-0-1-2-3-4-5-6-7-8	9-8-B-A-D-C-F-E-1-0-3-2-5-4-7-6
	1	0	1	0	A-B-C-D-E-F-0-1-2-3-4-5-6-7-8-9	A-B-8-9-E-F-C-D-2-3-0-1-6-7-4-5
	1	0	1	1	B-C-D-E-F-0-1-2-3-4-5-6-7-8-9-A	B-A-9-8-F-E-D-C-3-2-1-0-7-6-5-4
	1	1	0	0	C-D-E-F-0-1-2-3-4-5-6-7-8-9-A-B	C-D-E-F-8-9-A-B-4-5-6-7-0-1-2-3
	1	1	0	1	D-E-F-0-1-2-3-4-5-6-7-8-9-A-B-C	D-C-F-E-9-8-B-A-5-4-7-6-1-0-3-2
	1	1	1	0	E-F-0-1-2-3-4-5-6-7-8-9-A-B-C-D	E-F-C-D-A-B-8-9-6-7-4-5-2-3-0-1
	1	1	1	1	F-0-1-2-3-4-5-6-7-8-9-A-B-C-D-E	F-E-D-C-B-A-9-8-7-6-5-4-3-2-1-0

CAS Latency

The CAS latency (CL) is the delay, in clock cycles, between the registration of a READ command and the availability of the first output data. The latency can be set to 2 or 3 clocks, as shown in Figure 25 (page 75).

For CL = 3, if the READ command is registered at clock edge n, then the data will be nominally available at (n + 2 clocks + ^{t}AC). For CL = 2, if the READ command is registered at clock edge n, then the data will be nominally available at (n + 1 clock + ^{t}AC).

Figure 25: CAS Latency



Operating Mode

The normal operating mode is selected by issuing a LOAD MODE REGISTER command with bits A[*n*:7] each set to zero, and bits A[6:0] set to the desired values.

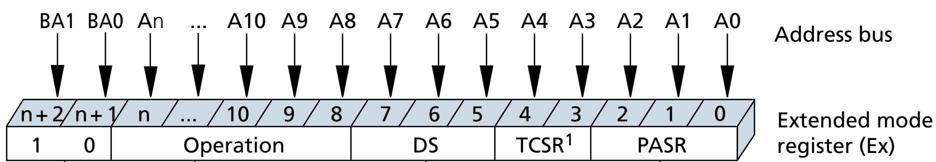
All other combinations of values for A[*n*:7] are reserved for future use. Reserved states should not be used because unknown operation or incompatibility with future versions may result.

Extended Mode Register

The EMR controls additional functions beyond those set by the mode registers. These additional functions include drive strength, TCSR, and PASR.

The EMR is programmed via the LOAD MODE REGISTER command with BA0 = 0 and BA1 = 1. Information in the EMR will be retained until it is programmed again, the device goes into deep power-down mode, or the device loses power.

Figure 26: Extended Mode Register



En + 2	En + 1	Mode Register Definition
0	0	Standard mode register
0	1	Status register
1	0	Extended mode register
1	1	Reserved

E7	E6	E5	Drive Strength
0	0	0	Full strength
0	0	1	1/2 strength
0	1	0	1/4 strength
0	1	1	3/4 strength
1	0	0	3/4 strength
1	0	1	Reserved
1	1	0	Reserved
1	1	1	Reserved

En	...	E10	E9	E8	E7–E0	
0	0	0	0	0	Valid	Normal AR operation
–	–	–	–	–	–	All other states reserved

E2	E1	E0	Partial-Array Self Refresh Coverage
0	0	0	Full array
0	0	1	1/2 array
0	1	0	1/4 array
0	1	1	Reserved
1	0	0	Reserved
1	0	1	1/8 array
1	1	0	1/16 array
1	1	1	Reserved

Notes:
1. On-die temperature sensor is used in place of TCSR. Setting these bits will have no effect.
2. The integer *n* is equal to the most significant address bit.

Temperature-Compensated Self Refresh

This device includes a temperature sensor that is implemented for automatic control of the self refresh oscillator. Programming the temperature-compensated self refresh (TCSR) bits will have no effect on the device. The self refresh oscillator will continue to refresh at the optimal factory-programmed rate for the device temperature.

Partial-Array Self Refresh

For further power savings during self refresh, the partial-array self refresh (PASR) feature enables the controller to select the amount of memory to be refreshed during self refresh. The refresh options include:

- Full array: banks 0, 1, 2, and 3
- One-half array: banks 0 and 1
- One-quarter array: bank 0
- One-eighth array: bank 0 with row address most significant bit (MSB) = 0
- One-sixteenth array: bank 0 with row address MSB = 0 and row address MSB - 1 = 0

READ and WRITE commands can still be issued to the full array during standard operation, but only the selected regions of the array will be refreshed during self refresh. Data in regions that are not selected will be lost.

Output Drive Strength

Because the device is designed for use in smaller systems that are typically point-to-point connections, an option to control the drive strength of the output buffers is provided. Drive strength should be selected based on the expected loading of the memory bus. The output driver settings are 25Ω, 37Ω, and 55Ω internal impedance for full, three-quarter, and one-half drive strengths, respectively.

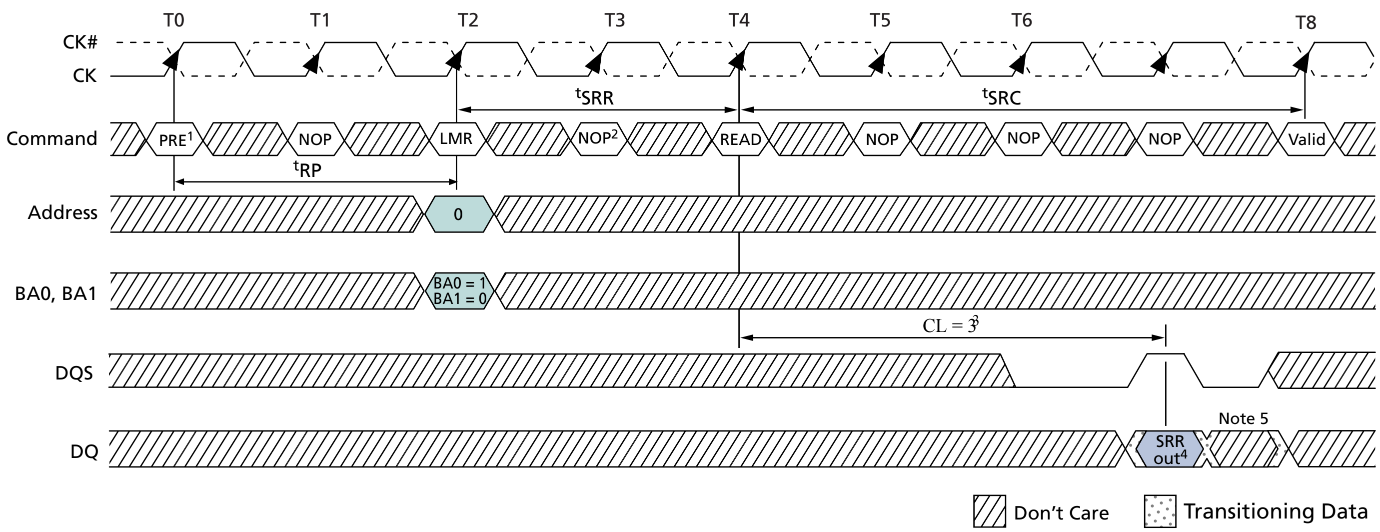
Status Read Register

The status read register (SRR) is used to read the manufacturer ID, revision ID, refresh multiplier, width type, and density of the device, as shown in Figure 28 (page 79). The SRR is read via the LOAD MODE REGISTER command with BA0 = 1 and BA1 = 0. The sequence to perform an SRR command is as follows:

1. The device must be properly initialized and in the idle or all banks precharged state.
2. Issue a LOAD MODE REGISTER command with BA[1:0] = 01 and all address pins set to 0.
3. Wait ^{t}SRR; only NOP or DESELECT commands are supported during the ^{t}SRR time.
4. Issue a READ command.
5. Subsequent commands to the device must be issued ^{t}SRC after the SRR READ command is issued; only NOP or DESELECT commands are supported during ^{t}SRC.

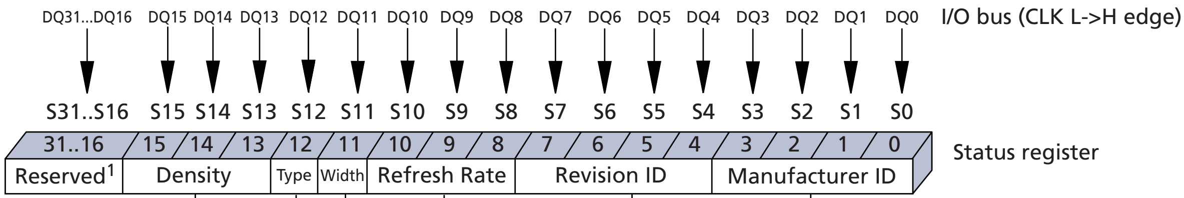
SRR output is read with a burst length of 2. SRR data is driven to the outputs on the first bit of the burst, with the output being "Don't Care" on the second bit of the burst.

Figure 27: Status Read Register Timing



Notes:
1. All banks must be idle prior to status register read.
2. NOP or DESELECT commands are required between the LMR and READ commands (^{t}SRR), and between the READ and the next VALID command (^{t}SRC).
3. CAS latency is predetermined by the programming of the mode register. CL = 3 is shown as an example only.
4. Burst length is fixed to 2 for SRR regardless of the value programmed by the mode register.
5. The second bit of the data-out burst is a "Don't Care."

Figure 28: Status Register Definition



S15	S14	S13	Density
0	0	0	128Mb
0	0	1	256Mb
0	1	0	512Mb
0	1	1	1Gb
1	0	0	2Gb
1	0	1	Reserved
1	1	0	Reserved
1	1	1	Reserved

S12	Device Type
0	LPDDR
1	LPDDR2

S11	Device Width
0	16 bits
1	32 bits

S10	S9	S8	Refresh Multiplier[2]
0	0	0	Reserved
0	0	1	Reserved
0	1	0	Reserved
0	1	1	2X
1	0	0	1X
1	0	1	Reserved
1	1	0	0.25X
1	1	1	Reserved

S3	S2	S1	S0	Manufacturer ID
0	0	0	0	Reserved
0	0	0	1	Samsung
0	0	1	0	Infineon
0	0	1	1	Elpida
0	1	0	0	Reserved
0	1	0	1	Reserved
0	1	1	0	Reserved
0	1	1	1	Reserved
1	0	0	0	Winbond
1	0	0	1	ESMT
1	0	1	0	NVM
1	0	1	1	Reserved
1	1	0	0	Reserved
1	1	0	1	Reserved
1	1	1	0	Reserved
1	1	1	1	Micron

S7	S6	S5	S4	Revision ID
0	0	0	0	The manufacturer's revision number starts at '0000' and increments by '0001' each time a change in the specification (AC timings or feature set), IBIS (pull-up or pull-down characteristics), or process occurs.
...	...	...	...	
X	X	X	X	

Notes: 1. Reserved bits should be set to 0 for future compatibility.

2. Refresh multiplier is based on the memory device on-board temperature sensor. Required average periodic refresh interval = $^{t}REFI$ × multiplier.

Bank/Row Activation

Before any READ or WRITE commands can be issued to a bank within the device, a row in that bank must be opened. This is accomplished via the ACTIVE command, which selects both the bank and the row to be activated (see the ACTIVE Command figure). After a row is opened with the ACTIVE command, a READ or WRITE command can be issued to that row, subject to the ^{t}RCD specification.

A subsequent ACTIVE command to a different row in the same bank can only be issued after the previous active row has been precharged. The minimum time interval between successive ACTIVE commands to the same bank is defined by ^{t}RC.

A subsequent ACTIVE command to another bank can be issued while the first bank is being accessed, which results in a reduction of total row access overhead. The minimum time interval between successive ACTIVE commands to different banks is defined by ^{t}RRD.

READ Operation

READ burst operations are initiated with a READ command, as shown in Figure 17 (page 59). The starting column and bank addresses are provided with the READ command, and auto precharge is either enabled or disabled for that burst access. If auto precharge is enabled, the row being accessed is precharged at the completion of the burst. For the READ commands used in the following illustrations, auto precharge is disabled.

During READ bursts, the valid data-out element from the starting column address will be available following the CL after the READ command. Each subsequent data-out element will be valid nominally at the next positive or negative clock edge. Figure 29 (page 82) shows general timing for each possible CL setting.

DQS is driven by the device along with output data. The initial LOW state on DQS is known as the read preamble; the LOW state coincident with the last data-out element is known as the read postamble. The READ burst is considered complete when the read postamble is satisfied.

Upon completion of a burst, assuming no other commands have been initiated, the DQ will go to High-Z. A detailed explanation of ^{t}DQSQ (valid data-out skew), ^{t}QH (data-out window hold), and the valid data window is depicted in Figure 36 (page 89) and Figure 37 (page 90). A detailed explanation of ^{t}DQSCK (DQS transition skew to CK) and ^{t}AC (data-out transition skew to CK) is depicted in Figure 38 (page 91).

Data from any READ burst can be truncated by a READ or WRITE command to the same or alternate bank, by a BURST TERMINATE command, or by a PRECHARGE command to the same bank, provided that the auto precharge mode was not activated.

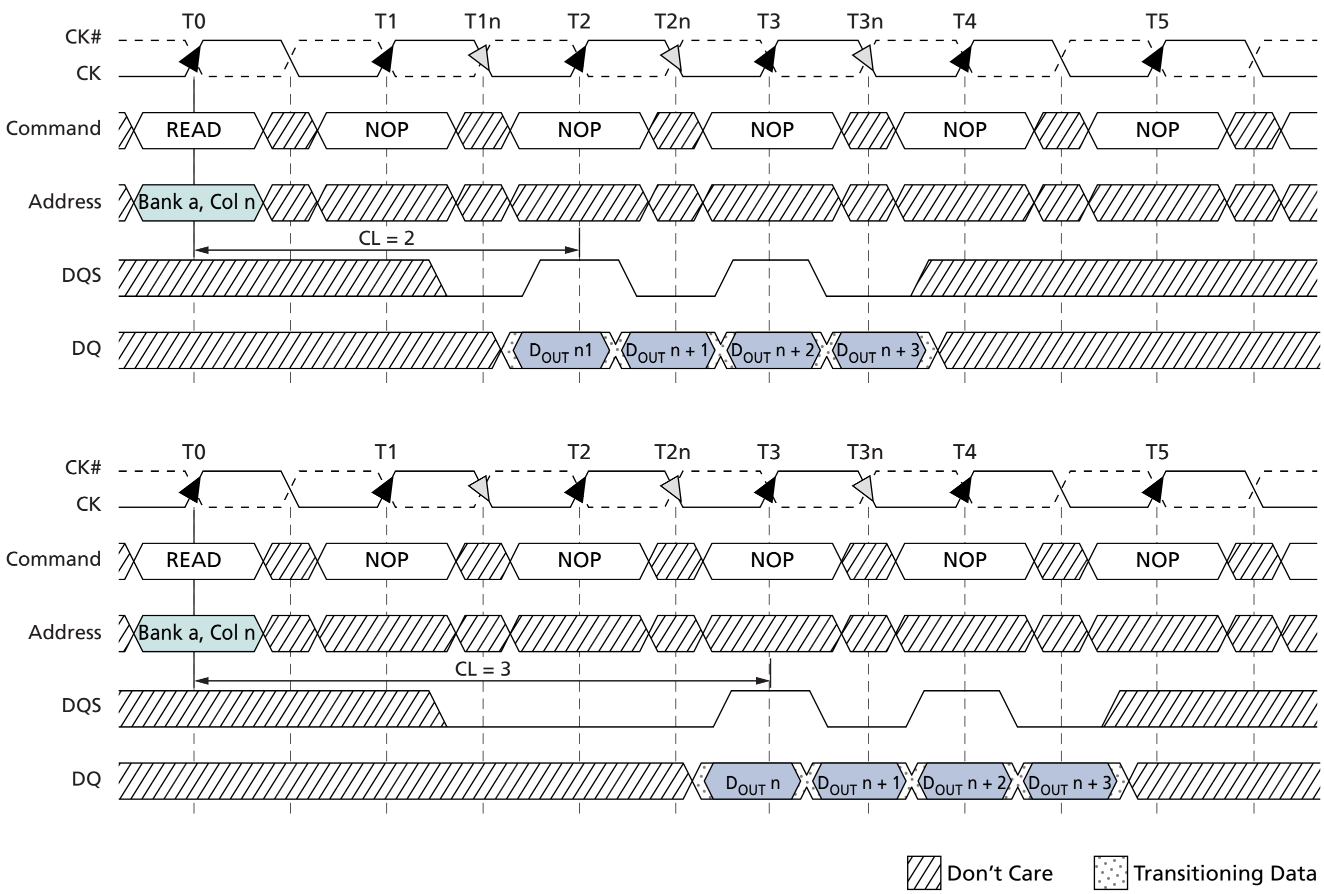
Data from any READ burst can be concatenated with or truncated with data from a subsequent READ command. In either case, a continuous flow of data can be maintained. The first data element from the new burst either follows the last element of a completed burst or the last desired data element of a longer burst that is being truncated. The new READ command should be issued x cycles after the first READ command, where x equals the number of desired data element pairs (pairs are required by the $2n$-prefetch architecture). This is shown in Figure 30 (page 83).

A READ command can be initiated on any clock cycle following a previous READ command. Nonconsecutive read data is shown in Figure 31 (page 84). Full-speed random read accesses within a page (or pages) can be performed as shown in Figure 32 (page 85).

Data from any READ burst can be truncated with a BURST TERMINATE command, as shown in Figure 33 (page 86). The BURST TERMINATE latency is equal to the READ (CAS) latency; for example, the BURST TERMINATE command should be issued x cycles after the READ command, where x equals the number of desired data element pairs (pairs are required by the $2n$-prefetch architecture).

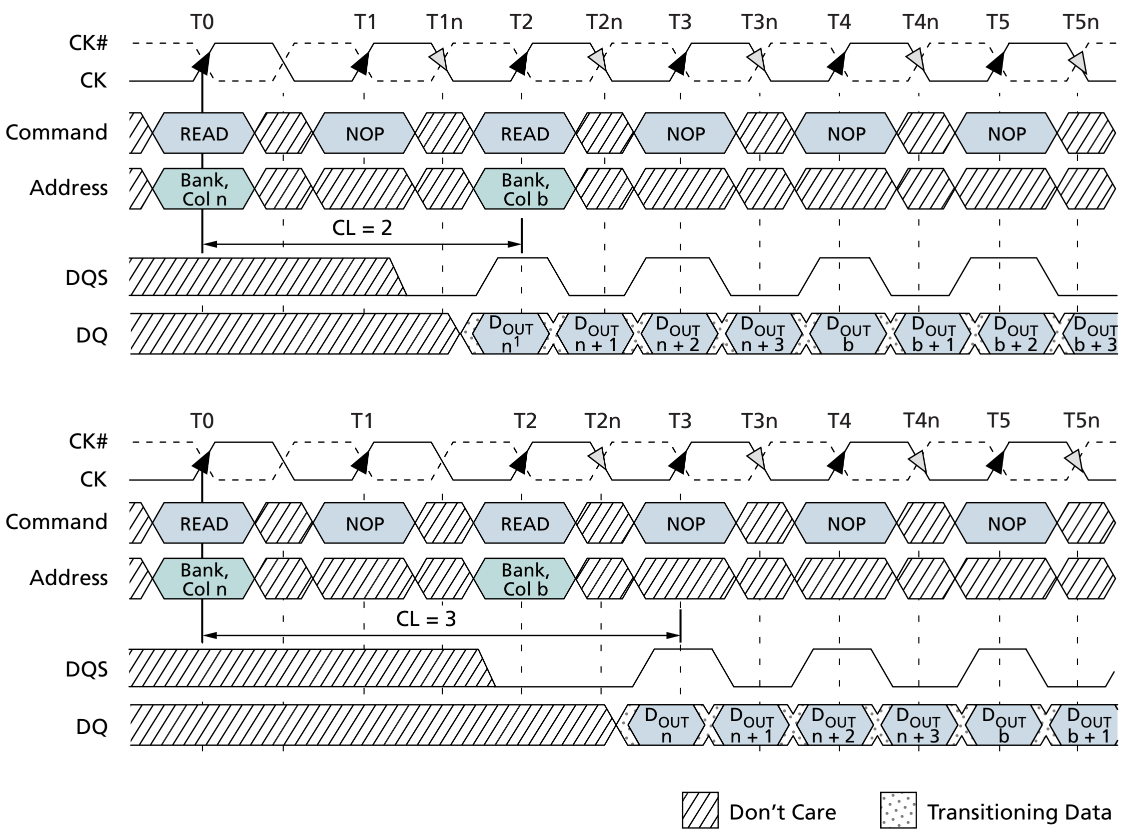
Data from any READ burst must be completed or truncated before a subsequent WRITE command can be issued. If truncation is necessary, the BURST TERMINATE command must be used, as shown in Figure 34 (page 87). A READ burst can be followed by, or truncated with, a PRECHARGE command to the same bank, provided that auto precharge was not activated. The PRECHARGE command should be issued x cycles after the READ command, where x equals the number of desired data element pairs. This is shown in Figure 35 (page 88). Following the PRECHARGE command, a subsequent command to the same bank cannot be issued until ^tRP is met. Part of the row precharge time is hidden during the access of the last data elements.

Figure 29: READ Burst



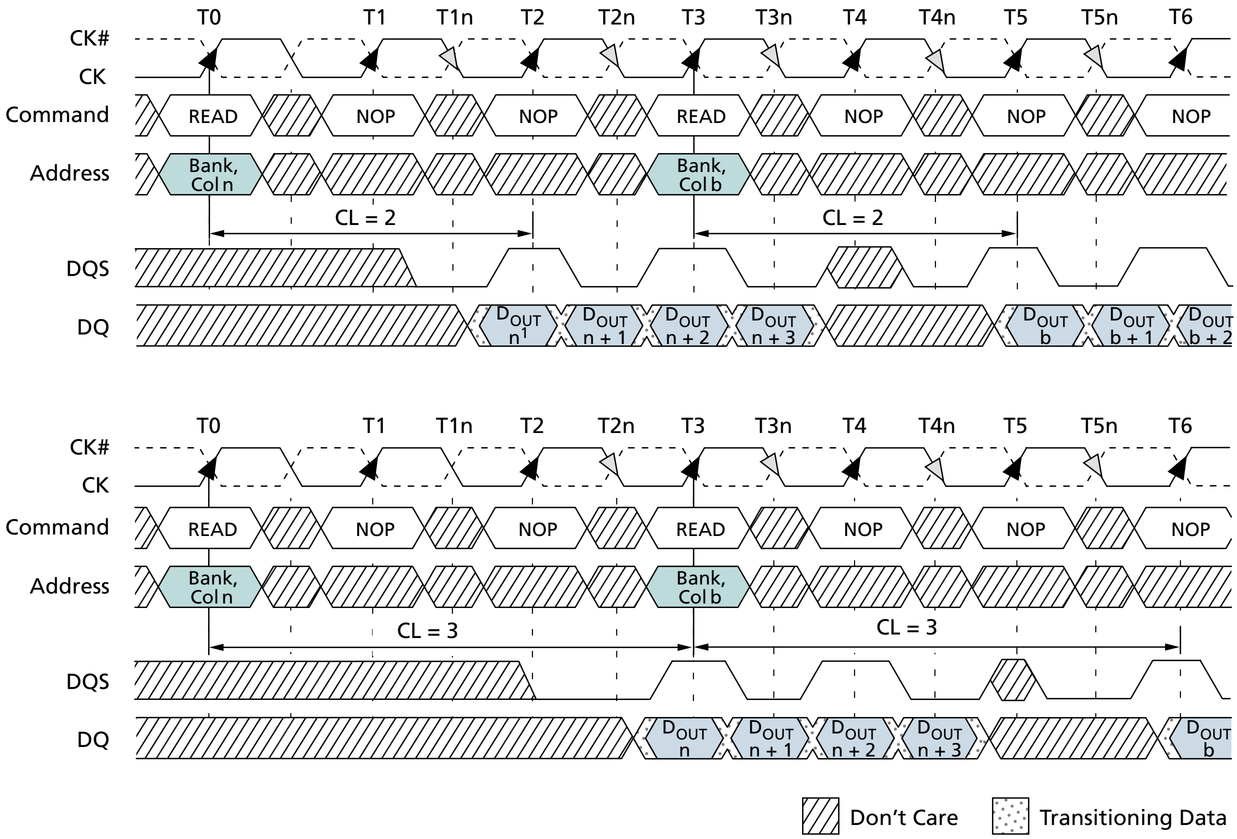
Notes:
1. D_{OUT} *n* = data-out from column *n*.
2. BL = 4.
3. Shown with nominal ^tAC, ^tDQSCK, and ^tDQSQ.

Figure 30: Consecutive READ Bursts



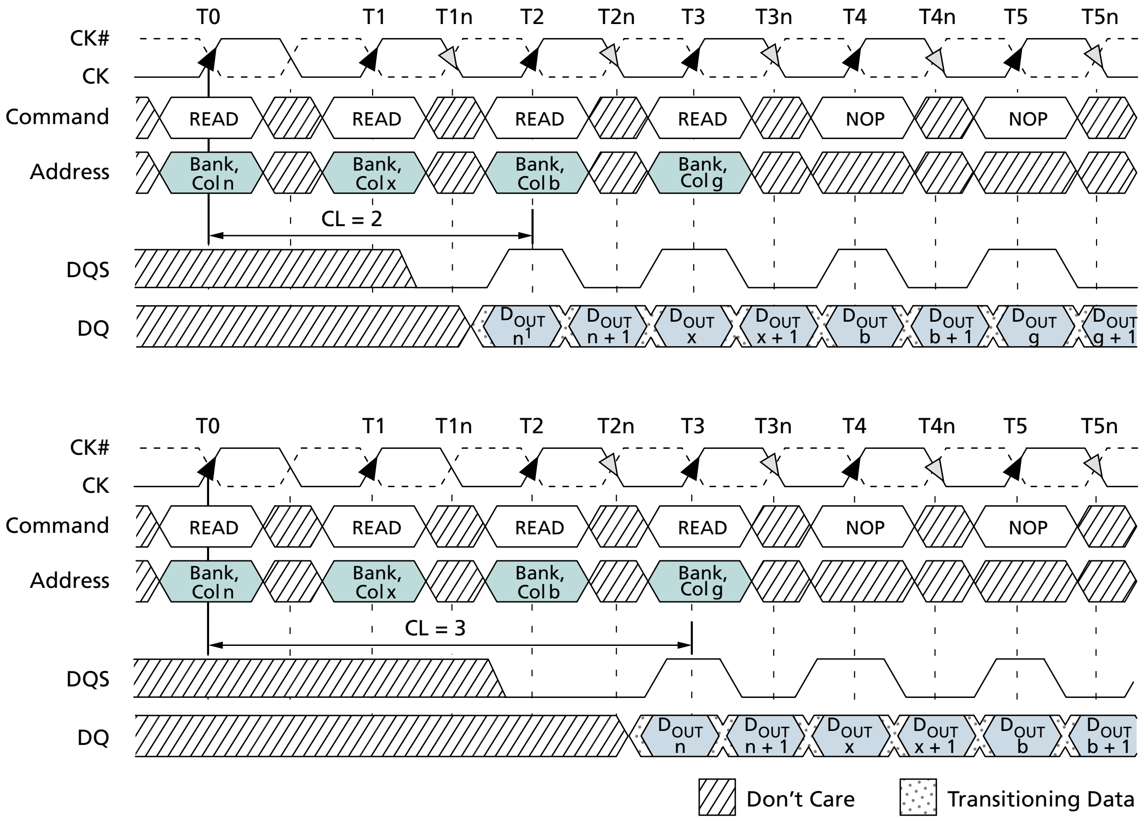
Notes:
1. D_{OUT}*n* (or *b*) = data-out from column *n* (or column *b*).
2. BL = 4, 8, or 16 (if 4, the bursts are concatenated; if 8 or 16, the second burst interrupts the first).
3. Shown with nominal ^tAC, ^tDQSCK, and ^tDQSQ.
4. Example applies only when READ commands are issued to same device.

Figure 31: Nonconsecutive READ Bursts



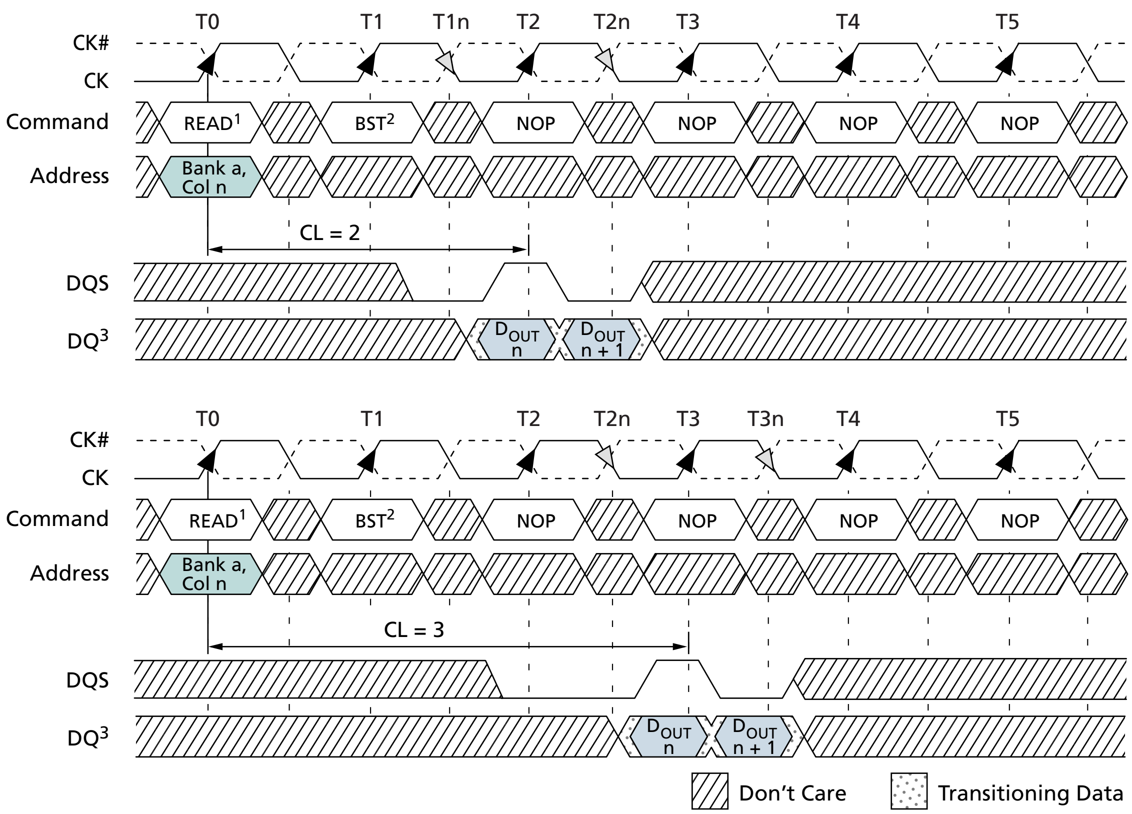
Notes:
1. $D_{OUT}n$ (or b) = data-out from column n (or column b).
2. BL = 4, 8, or 16 (if burst is 8 or 16, the second burst interrupts the first).
3. Shown with nominal ^tAC, ^tDQSCK, and ^tDQSQ.
4. Example applies when READ commands are issued to different devices or nonconsecutive READs.

Figure 32: Random Read Accesses



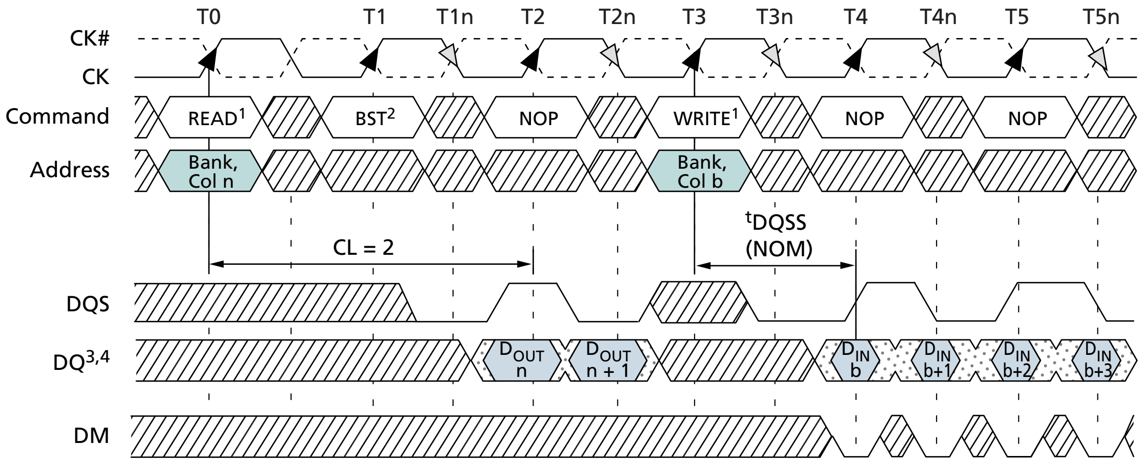
Notes:
1. D_{OUT}*n* (or *x*, *b*, *g*) = data-out from column *n* (or column *x*, column *b*, column *g*).
2. BL = 2, 4, 8, or 16 (if 4, 8, or 16, the following burst interrupts the previous).
3. READs are to an active row in any bank.
4. Shown with nominal ^{t}AC, ^{t}DQSCK, and ^{t}DQSQ.

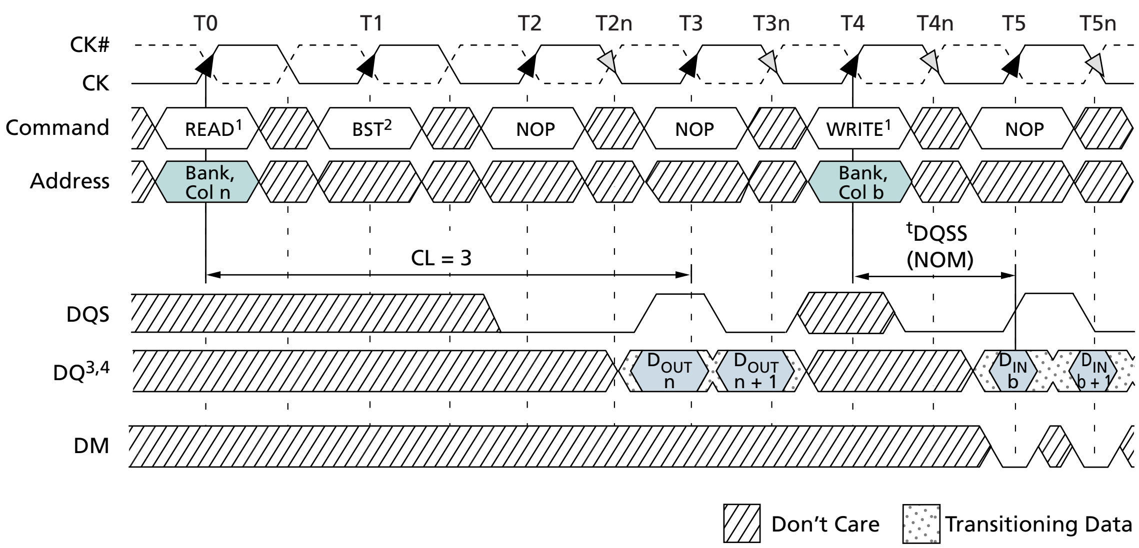
Figure 33: Terminating a READ Burst



Notes:
1. BL = 4, 8, or 16.
2. BST = BURST TERMINATE command; page remains open.
3. $D_{OUT}n$ = data-out from column *n*.
4. Shown with nominal ^{t}AC, $^{t}DQSCK$, and $^{t}DQSQ$.
5. CKE = HIGH.

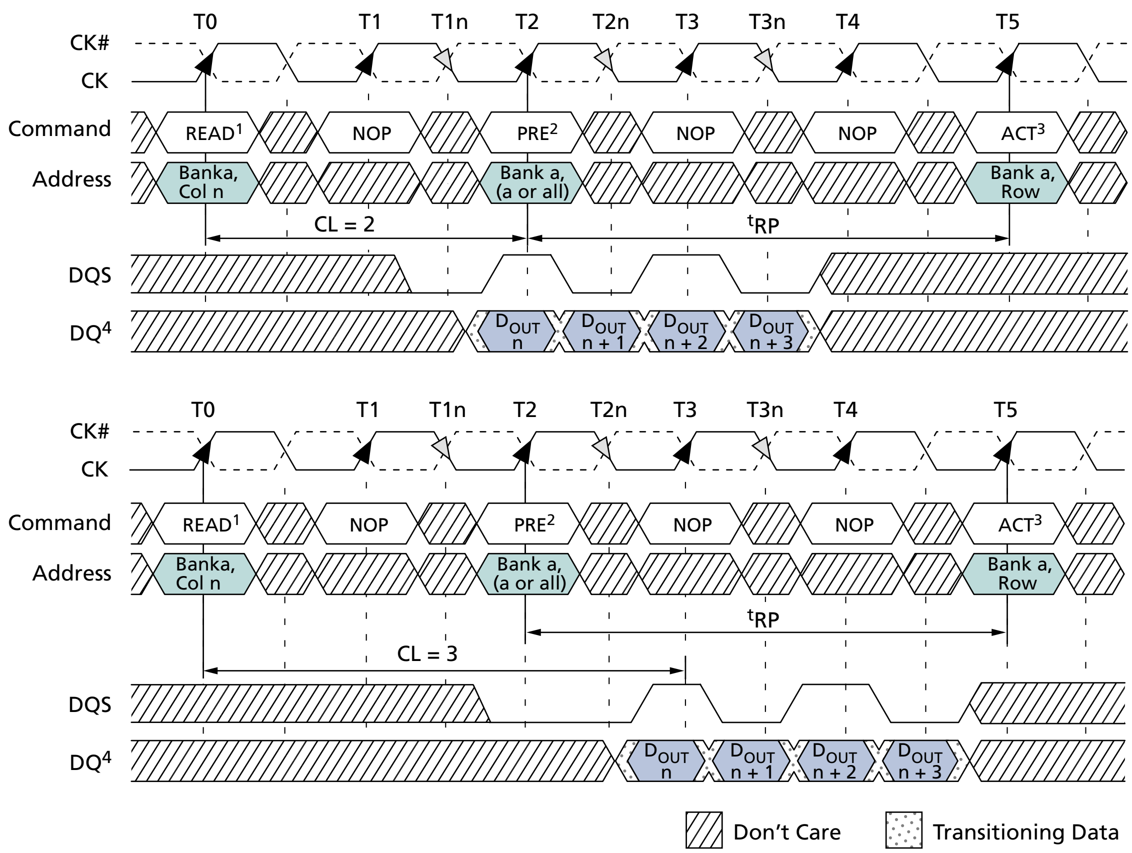
Figure 34: READ-to-WRITE





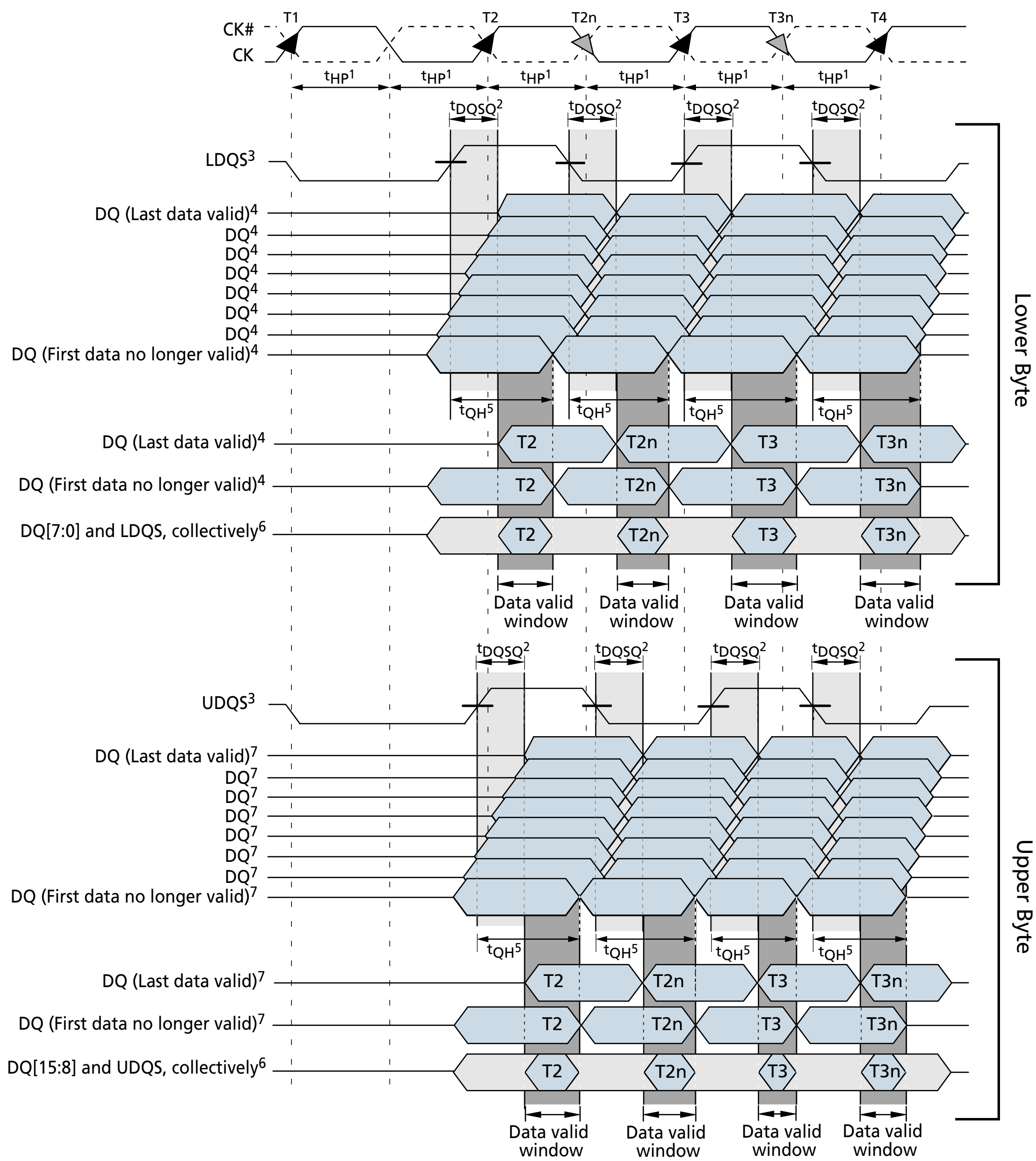
Notes:
1. BL = 4 in the cases shown (applies for bursts of 8 and 16 as well; if BL = 2, the BST command shown can be NOP).
2. BST = BURST TERMINATE command; page remains open.
3. $D_{OUT}n$ = data-out from column *n*.
4. $D_{IN}b$ = data-in from column *b*.
5. Shown with nominal ^tAC, ^tDQSCK, and ^tDQSQ.
6. CKE = HIGH.

Figure 35: READ-to-PRECHARGE



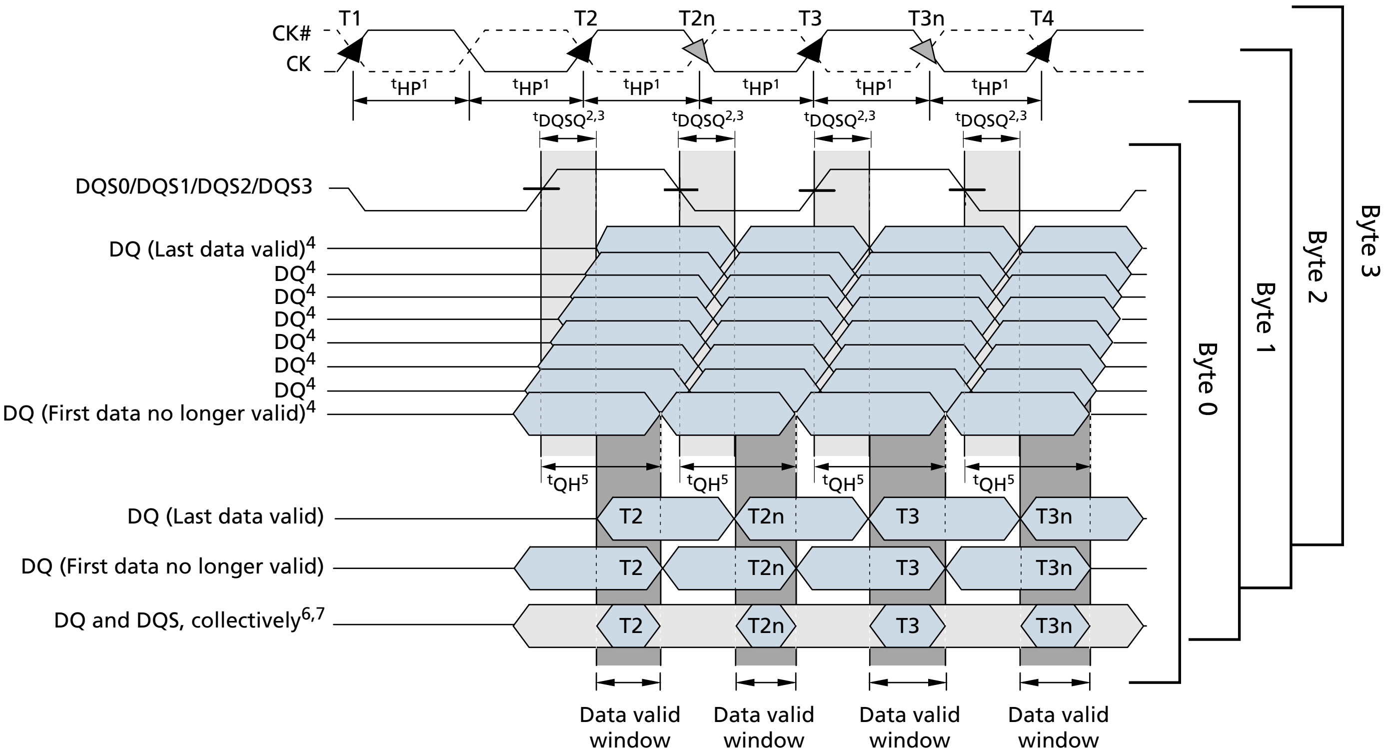
Notes:
1. BL = 4, or an interrupted burst of 8 or 16.
2. PRE = PRECHARGE command.
3. ACT = ACTIVE command.
4. $D_{OUT}n$ = data-out from column *n*.
5. Shown with nominal ^{t}AC, ^{t}DQSCK, and ^{t}DQSQ.
6. READ-to-PRECHARGE equals 2 clocks, which enables 2 data pairs of data-out.
7. A READ command with auto precharge enabled, provided ^{t}RAS (MIN) is met, would cause a precharge to be performed at *x* number of clock cycles after the READ command, where *x* = BL/2.

Figure 36: Data Output Timing – ^tDQSQ, ^tQH, and Data Valid Window (x16)



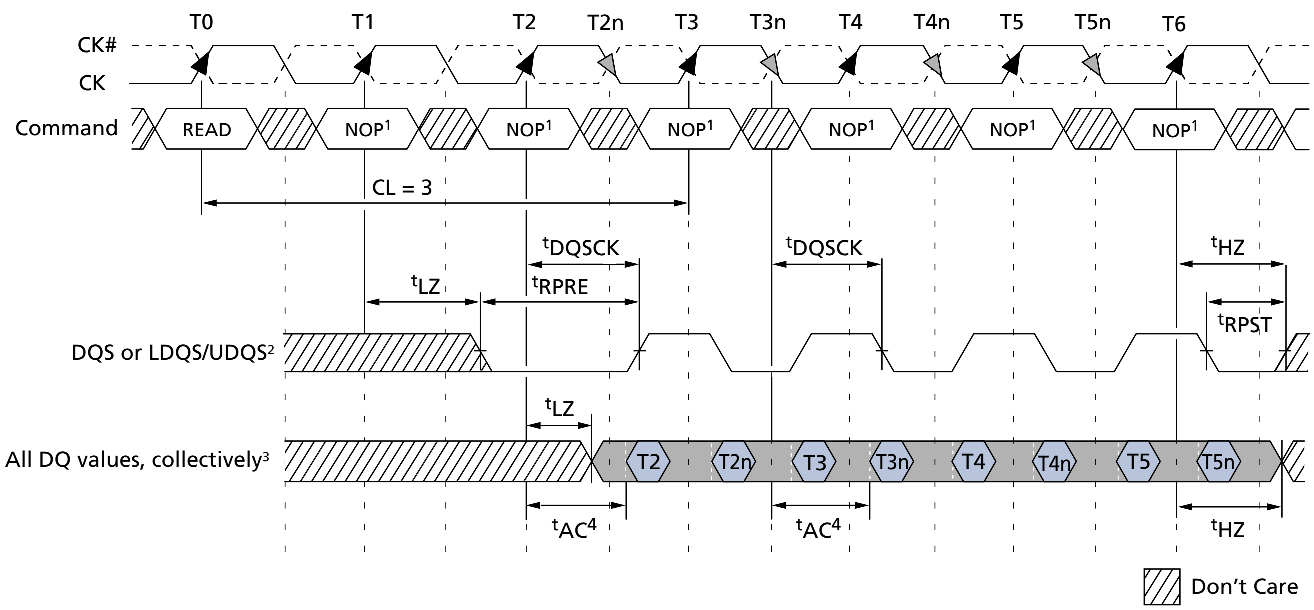
Notes:
1. ^tHP is the lesser of ^tCL or ^tCH clock transition collectively when a bank is active.
2. ^tDQSQ is derived at each DQS clock edge and is not cumulative over time and begins with DQS transition and ends with the last valid DQ transition.
3. DQ transitioning after DQS transitions define the ^tDQSQ window. LDQS defines the lower byte and UDQS defines the upper byte.
4. DQ0, DQ1, DQ2, DQ3, DQ4, DQ5, DQ6, or DQ7.
5. ^tQH is derived from ^tHP: $^tQH = {}^tHP - {}^tQHS$.
6. The data valid window is derived for each DQS transitions and is defined as $^tQH - {}^tDQSQ$.
7. DQ8, DQ9, DQ10, DQ11, DQ12, DQ13, DQ14, or DQ15.

Figure 37: Data Output Timing – ^{t}DQSQ, ^{t}QH, and Data Valid Window (x32)



Notes:
1. ^{t}HP is the lesser of ^{t}CL or ^{t}CH clock transition collectively when a bank is active.
2. DQ transitioning after DQS transitions define the ^{t}DQSQ window.
3. ^{t}DQSQ is derived at each DQS clock edge and is not cumulative over time; it begins with DQS transition and ends with the last valid DQ transition.
4. Byte 0 is DQ[7:0], byte 1 is DQ[15:8], byte 2 is DQ[23:16], byte 3 is DQ[31:24].
5. ^{t}QH is derived from ^{t}HP: $^{t}QH = {}^{t}HP - {}^{t}QHS$.
6. The data valid window is derived for each DQS transition and is ^{t}QH - ^{t}DQSQ.
7. DQ[7:0] and DQS0 for byte 0; DQ[15:8] and DQS1 for byte 1; DQ[23:16] and DQS2 for byte 2; DQ[31:23] and DQS3 for byte 3.

Figure 38: Data Output Timing – ^tAC and ^tDQSCK



Notes:
1. Commands other than NOP can be valid during this cycle.
2. DQ transitioning after DQS transitions define ^tDQSQ window.
3. All DQ must transition by ^tDQSQ after DQS transitions, regardless of ^tAC.
4. ^tAC is the DQ output window relative to CK and is the long-term component of DQ skew.

WRITE Operation

WRITE bursts are initiated with a WRITE command, as shown in Figure 18 (page 60). The starting column and bank addresses are provided with the WRITE command, and auto precharge is either enabled or disabled for that access. If auto precharge is enabled, the row being accessed is precharged at the completion of the burst. For the WRITE commands used in the following illustrations, auto precharge is disabled. Basic data input timing is shown in Figure 39 (page 93) (this timing applies to all WRITE operations).

Input data appearing on the data bus is written to the memory array subject to the state of data mask (DM) inputs coincident with the data. If DM is registered LOW, the corresponding data will be written; if DM is registered HIGH, the corresponding data will be ignored, and the write will not be executed to that byte/column location. DM operation is illustrated in Figure 40 (page 94).

During WRITE bursts, the first valid data-in element will be registered on the first rising edge of DQS following the WRITE command, and subsequent data elements will be registered on successive edges of DQS. The LOW state of DQS between the WRITE command and the first rising edge is known as the write preamble; the LOW state of DQS following the last data-in element is known as the write postamble. The WRITE burst is complete when the write postamble and ^tWR or ^tWTR are satisfied.

The time between the WRITE command and the first corresponding rising edge of DQS (^tDQSS) is specified with a relatively wide range (75%–125% of one clock cycle). All WRITE diagrams show the nominal case. Where the two extreme cases (that is, ^tDQSS [MIN] and ^tDQSS [MAX]) might not be obvious, they have also been included. Figure 41 (page 95) shows the nominal case and the extremes of ^tDQSS for a burst of 4. Upon completion of a burst, assuming no other commands have been initiated, the DQ will remain High-Z and any additional input data will be ignored.

Data for any WRITE burst can be concatenated with or truncated by a subsequent WRITE command. In either case, a continuous flow of input data can be maintained. The new WRITE command can be issued on any positive edge of clock following the previous WRITE command. The first data element from the new burst is applied after either the last element of a completed burst or the last desired data element of a longer burst that is being truncated. The new WRITE command should be issued x cycles after the first WRITE command, where x equals the number of desired data element pairs (pairs are required by the $2n$-prefetch architecture).

Figure 42 (page 96) shows concatenated bursts of 4. An example of nonconsecutive WRITEs is shown in Figure 43 (page 96). Full-speed random write accesses within a page or pages can be performed, as shown in Figure 44 (page 97).

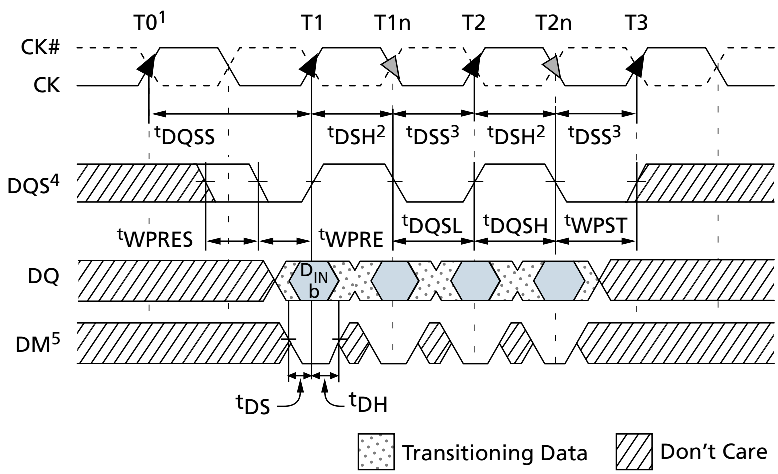
Data for any WRITE burst can be followed by a subsequent READ command. To follow a WRITE without truncating the WRITE burst, ^tWTR should be met, as shown in Figure 45 (page 98).

Data for any WRITE burst can be truncated by a subsequent READ command, as shown in Figure 46 (page 99). Note that only the data-in pairs that are registered prior to the ^tWTR period are written to the internal array, and any subsequent data-in should be masked with DM, as shown in Figure 47 (page 100).

Data for any WRITE burst can be followed by a subsequent PRECHARGE command. To follow a WRITE without truncating the WRITE burst, ^tWR should be met, as shown in Figure 48 (page 101).

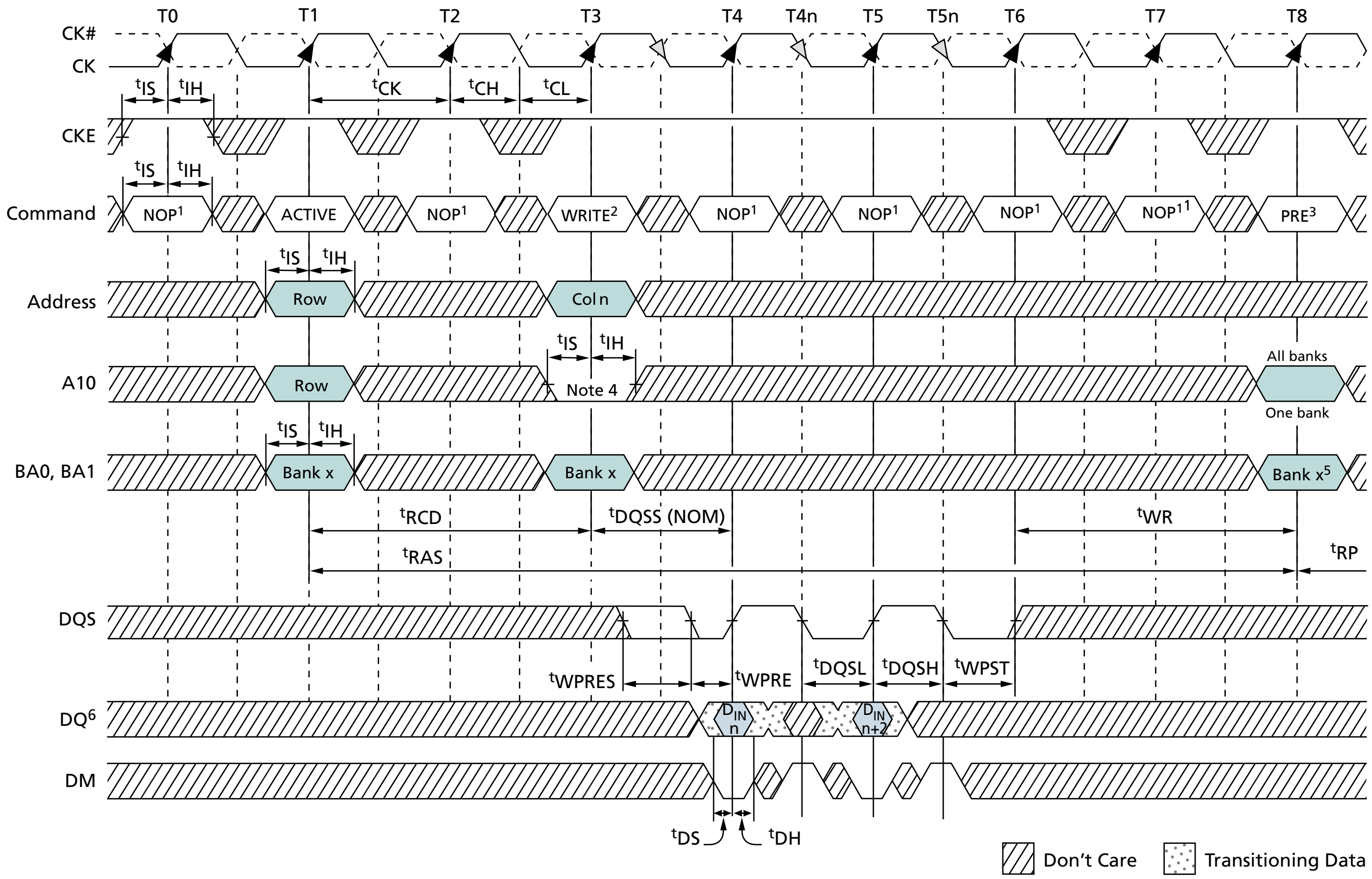
Data for any WRITE burst can be truncated by a subsequent PRECHARGE command, as shown in Figure 49 (page 102) and Figure 50 (page 103). Note that only the data-in pairs that are registered prior to the ^{t}WR period are written to the internal array, and any subsequent data-in should be masked with DM, as shown in Figure 49 (page 102) and Figure 50 (page 103). After the PRECHARGE command, a subsequent command to the same bank cannot be issued until ^{t}RP is met.

Figure 39: Data Input Timing



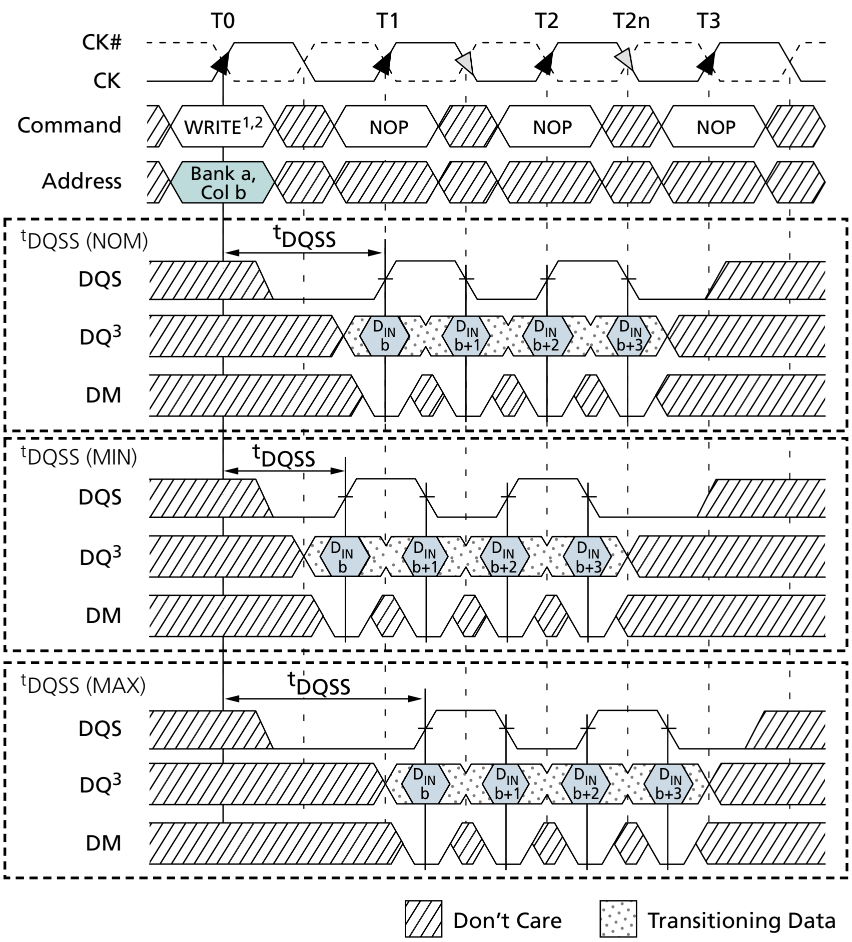
Notes:
1. WRITE command issued at T0.
2. ^{t}DSH (MIN) generally occurs during ^{t}DQSS (MIN).
3. ^{t}DSS (MIN) generally occurs during ^{t}DQSS (MAX).
4. For x16, LDQS controls the lower byte; UDQS controls the upper byte. For x32, DQS0 controls DQ[7:0], DQS1 controls DQ[15:8], DQS2 controls DQ[23:16], and DQS3 controls DQ[31:24].
5. For x16, LDM controls the lower byte; UDM controls the upper byte. For x32, DM0 controls DQ[7:0], DM1 controls DQ[15:8], DM2 controls DQ[23:16], and DM3 controls DQ[31:24].

Figure 40: Write – DM Operation



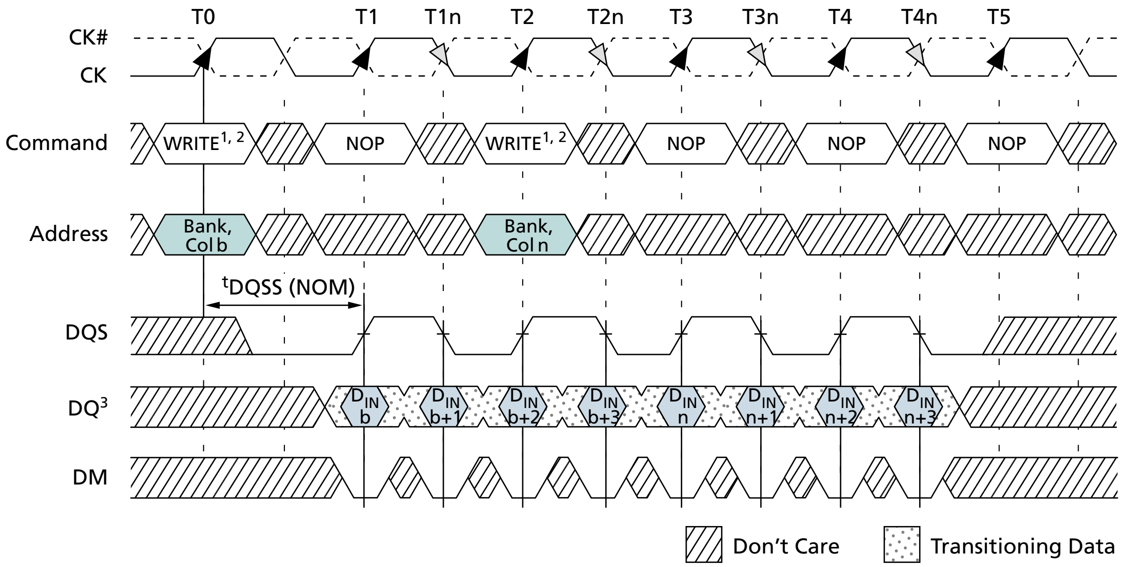
Notes:
1. NOP commands are shown for ease of illustration; other commands may be valid at these times.
2. BL = 4 in the case shown.
3. PRE = PRECHARGE.
4. Disable auto precharge.
5. Bank *x* at T8 is "Don't Care" if A10 is HIGH at T8.
6. $D_{IN}n$ = data-in from column *n*.

Figure 41: WRITE Burst



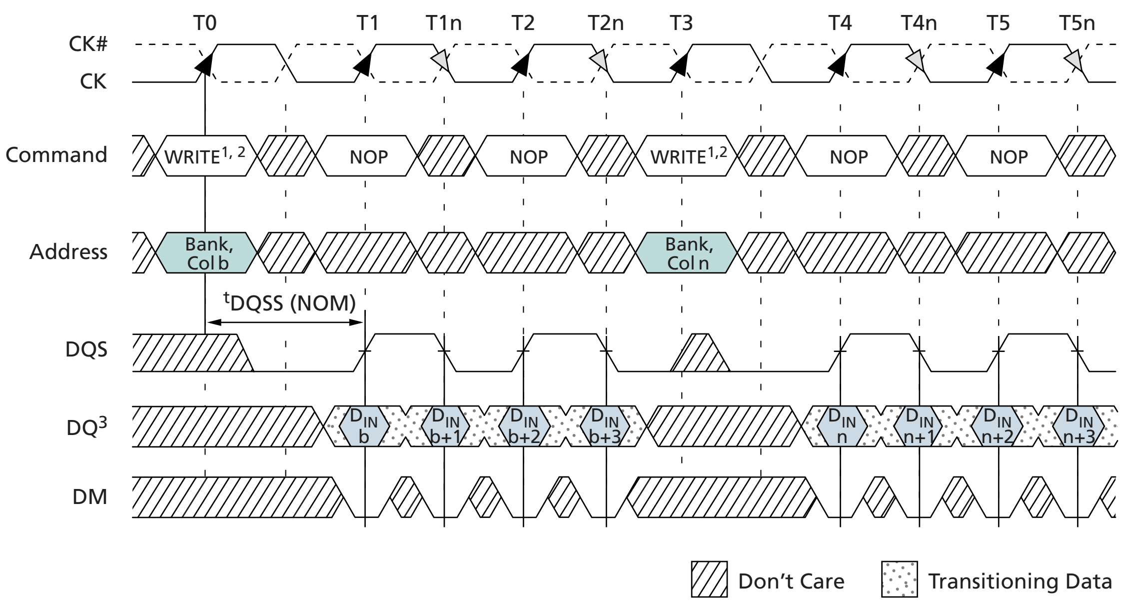
Notes:
1. An uninterrupted burst of 4 is shown.
2. A10 is LOW with the WRITE command (auto precharge is disabled).
3. $D_{IN}b$ = data-in for column *b*.

Figure 42: Consecutive WRITE-to-WRITE



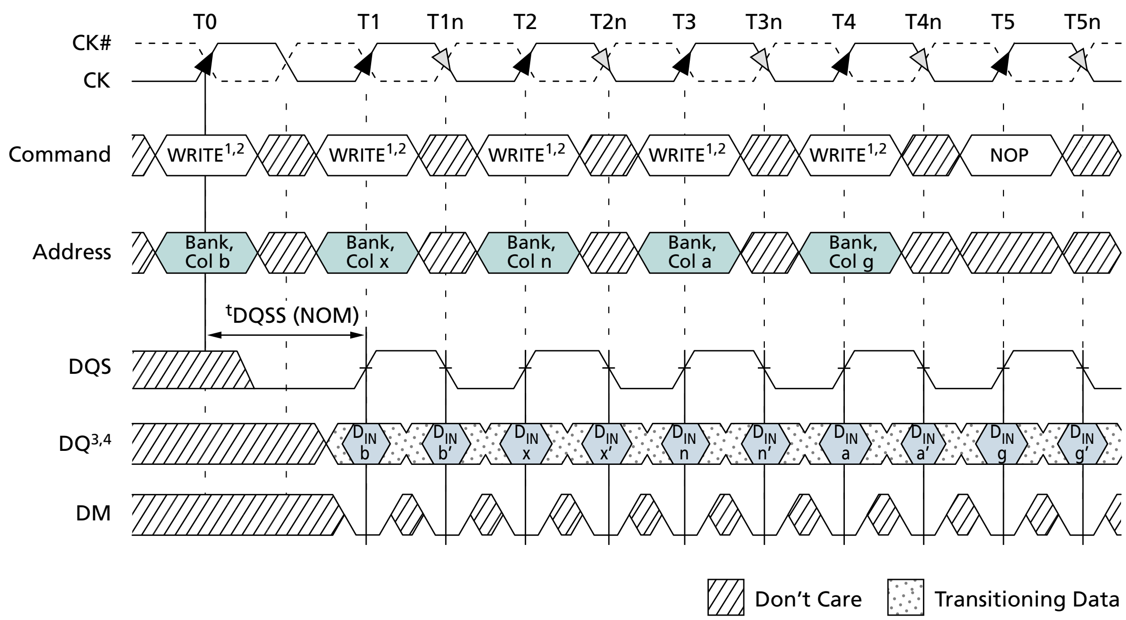
Notes:
1. Each WRITE command can be to any bank.
2. An uninterrupted burst of 4 is shown.
3. $D_{IN}b$ (*n*) = data-in for column *b* (*n*).

Figure 43: Nonconsecutive WRITE-to-WRITE



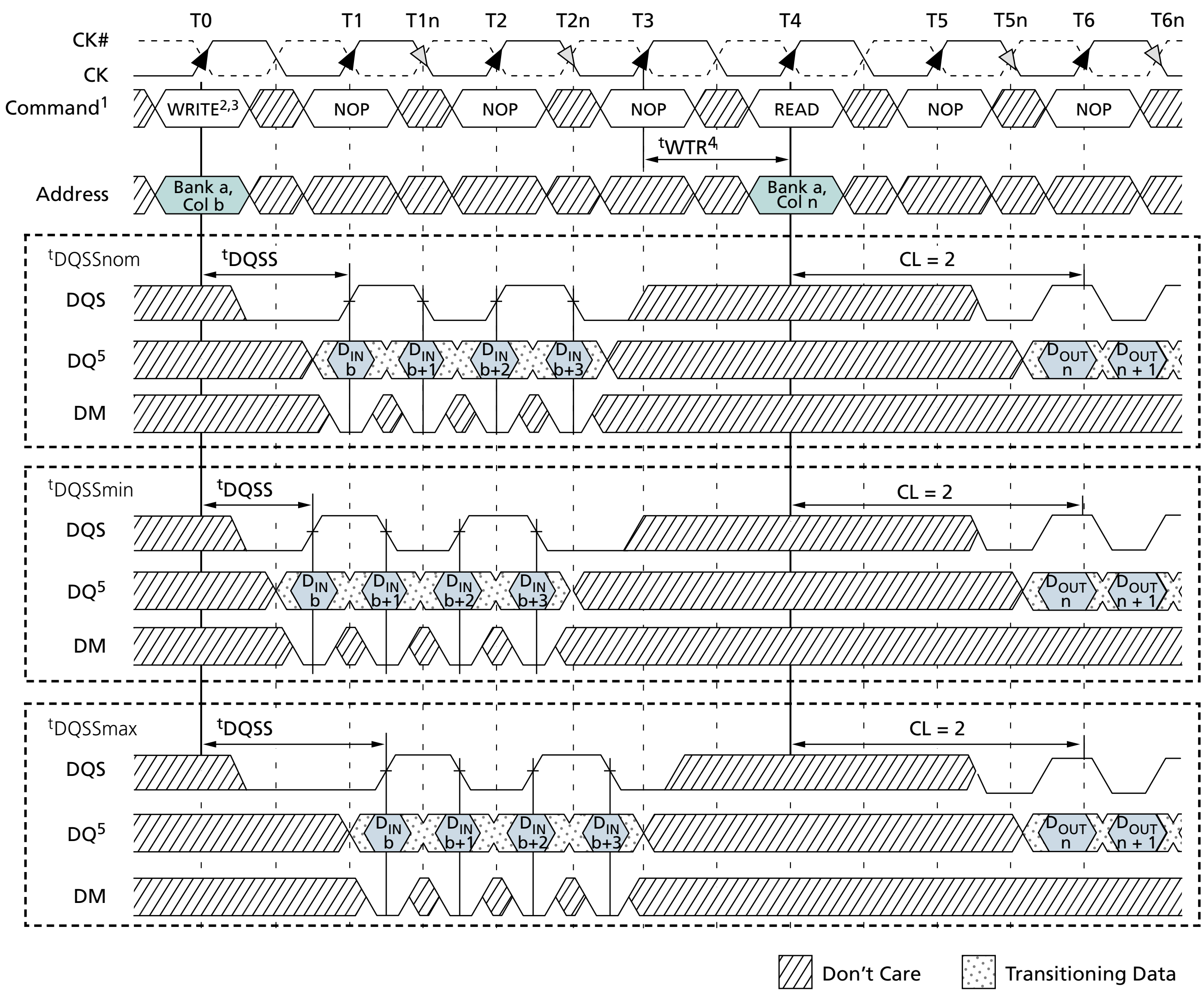
Notes:
1. Each WRITE command can be to any bank.
2. An uninterrupted burst of 4 is shown.
3. $D_{IN}b$ (*n*) = data-in for column *b* (*n*).

Figure 44: Random WRITE Cycles



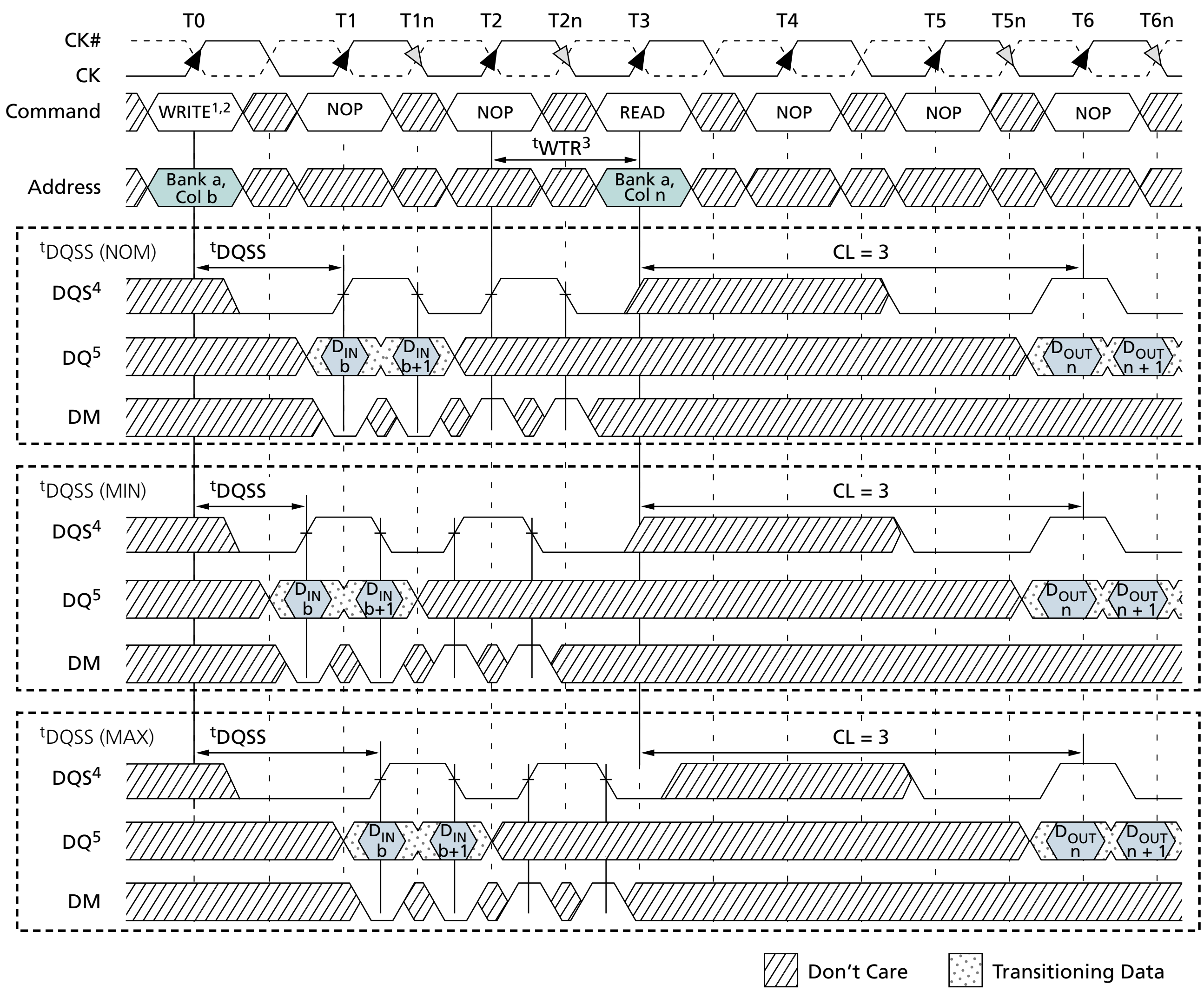
Notes:
1. Each WRITE command can be to any bank.
2. Programmed BL = 2, 4, 8, or 16 in cases shown.
3. $D_{IN}b$ (*or x*, *n*, *a*, *g*) = data-in for column *b* (or *x, n, a, g*).
4. b' (or *x, n, a, g*) = the next data-in following $D_{IN}b$ (*x, n, a, g*) according to the programmed burst order.

Figure 45: WRITE-to-READ – Uninterrupting



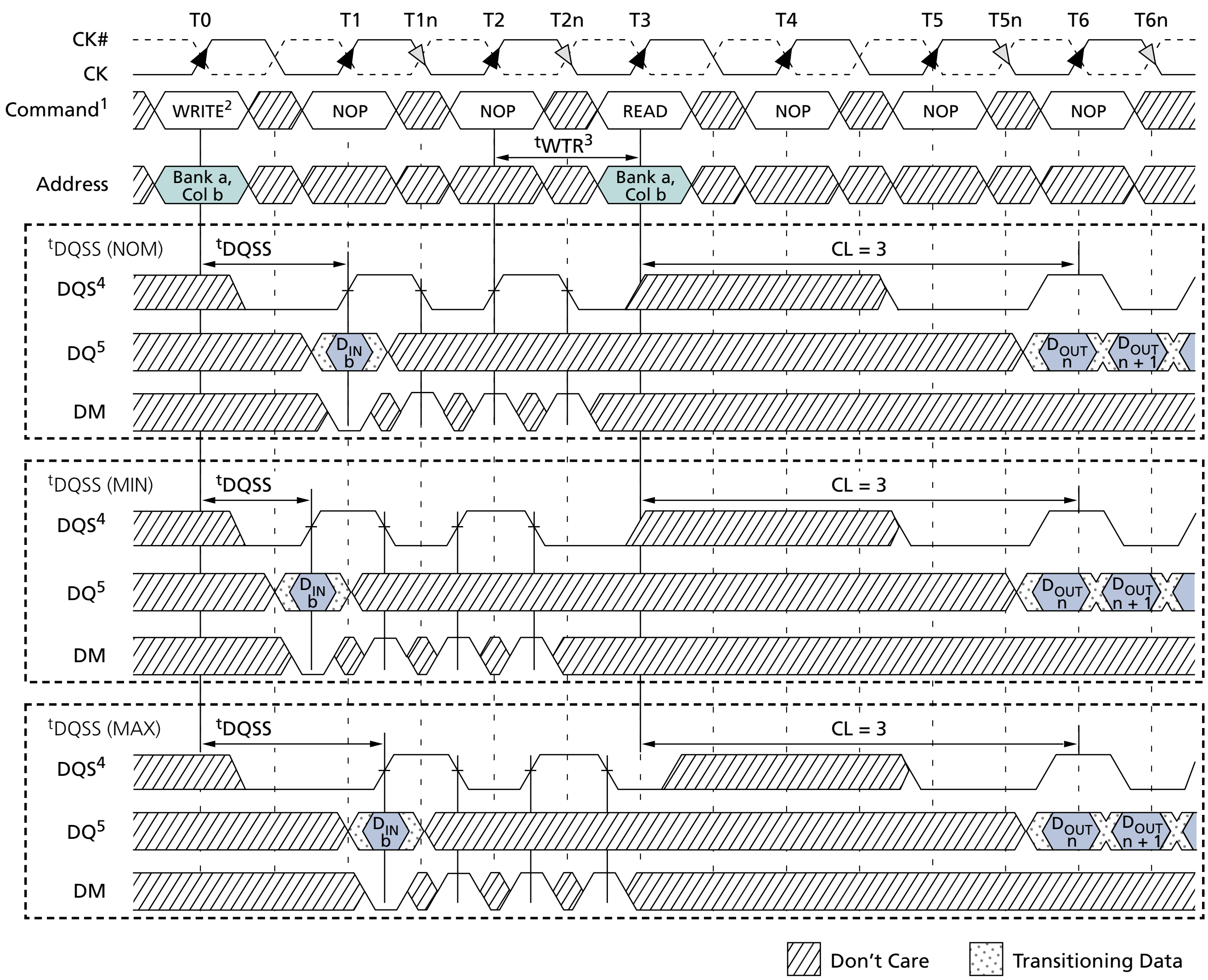
Notes:
1. The READ and WRITE commands are to the same device. However, the READ and WRITE commands may be to different devices, in which case ᵗWRT is not required and the READ command could be applied earlier.
2. A10 is LOW with the WRITE command (auto precharge is disabled).
3. An uninterrupted burst of 4 is shown.
4. ᵗWTR is referenced from the first positive CK edge after the last data-in pair.
5. D_{IN}*b* = data-in for column *b*; D_{OUT}*n* = data-out for column *n*.

Figure 46: WRITE-to-READ – Interrupting



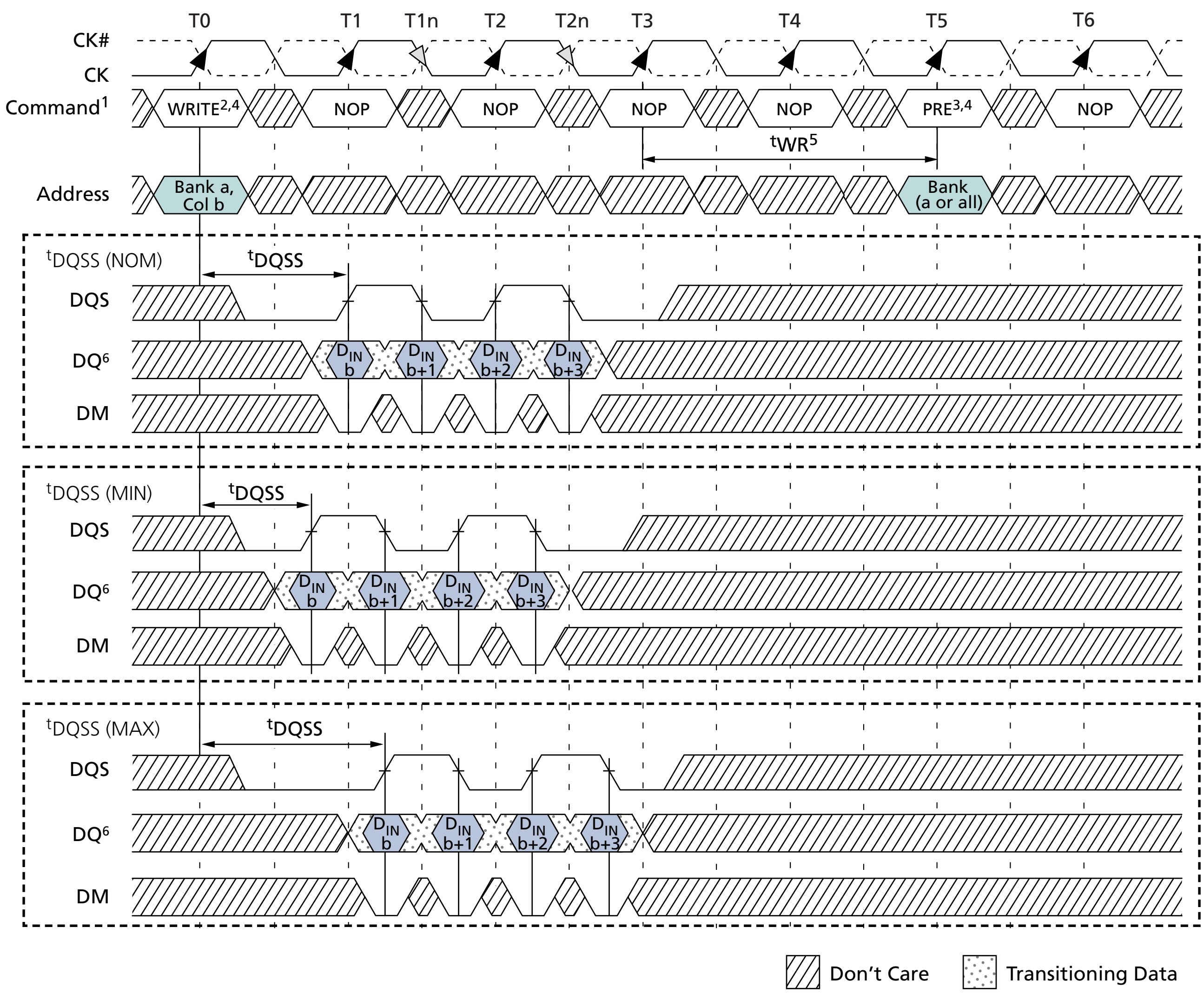
Notes:
1. An interrupted burst of 4 is shown; 2 data elements are written.
2. A10 is LOW with the WRITE command (auto precharge is disabled).
3. ${}^tWTR$ is referenced from the first positive CK edge after the last data-in pair.
4. DQS is required at T2 and T2n (nominal case) to register DM.
5. $D_{IN}b$ = data-in for column *b*; $D_{OUT}n$ = data-out for column *n*.

Figure 47: WRITE-to-READ – Odd Number of Data, Interrupting



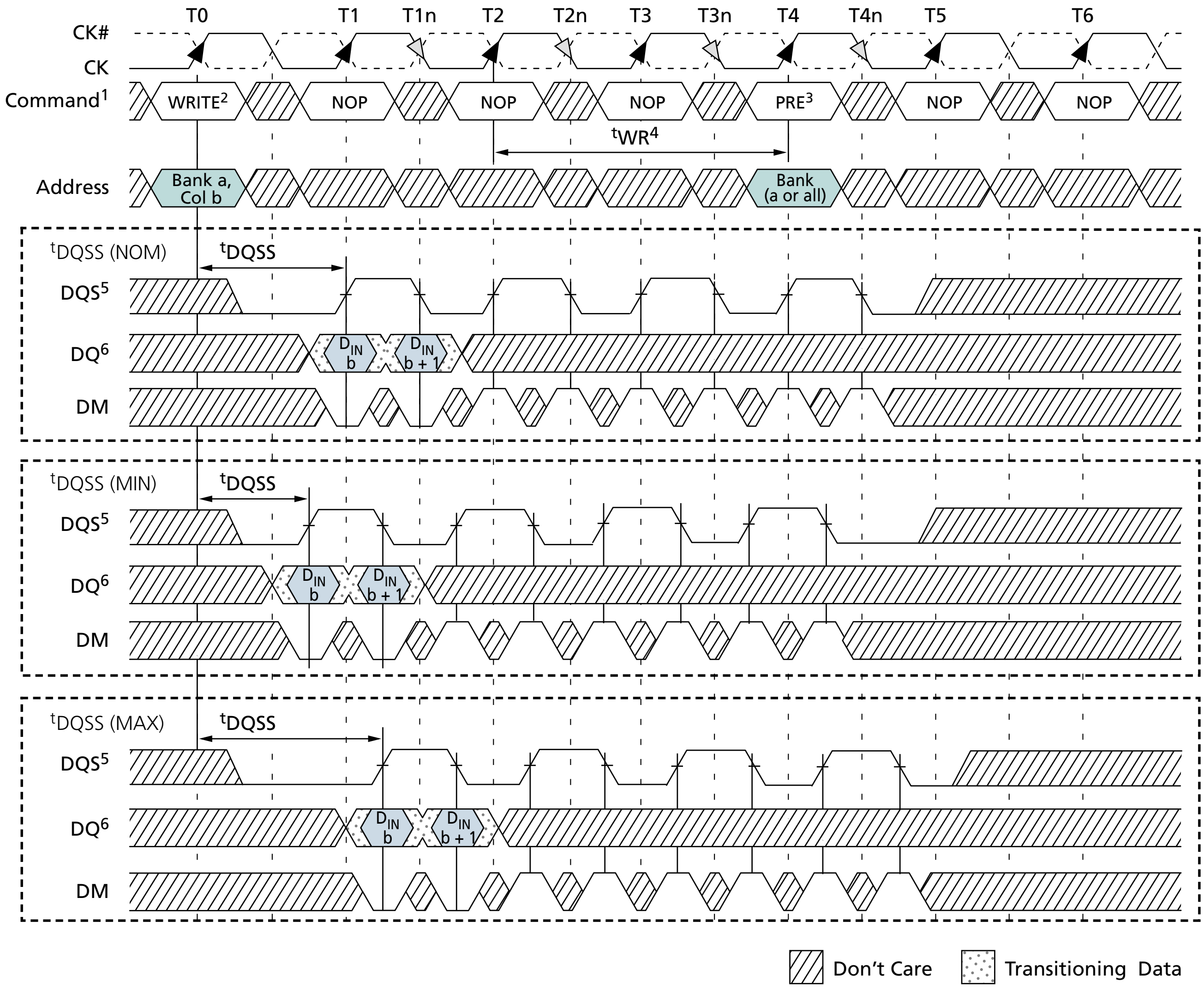
Notes:
1. An interrupted burst of 4 is shown; 1 data element is written, 3 are masked.
2. A10 is LOW with the WRITE command (auto precharge is disabled).
3. tWTR is referenced from the first positive CK edge after the last data-in pair.
4. DQS is required at T2 and T2n (nominal case) to register DM.
5. D_{IN}*b* = data-in for column *b*; D_{OUT}*n* = data-out for column *n*.

Figure 48: WRITE-to-PRECHARGE – Uninterrupting



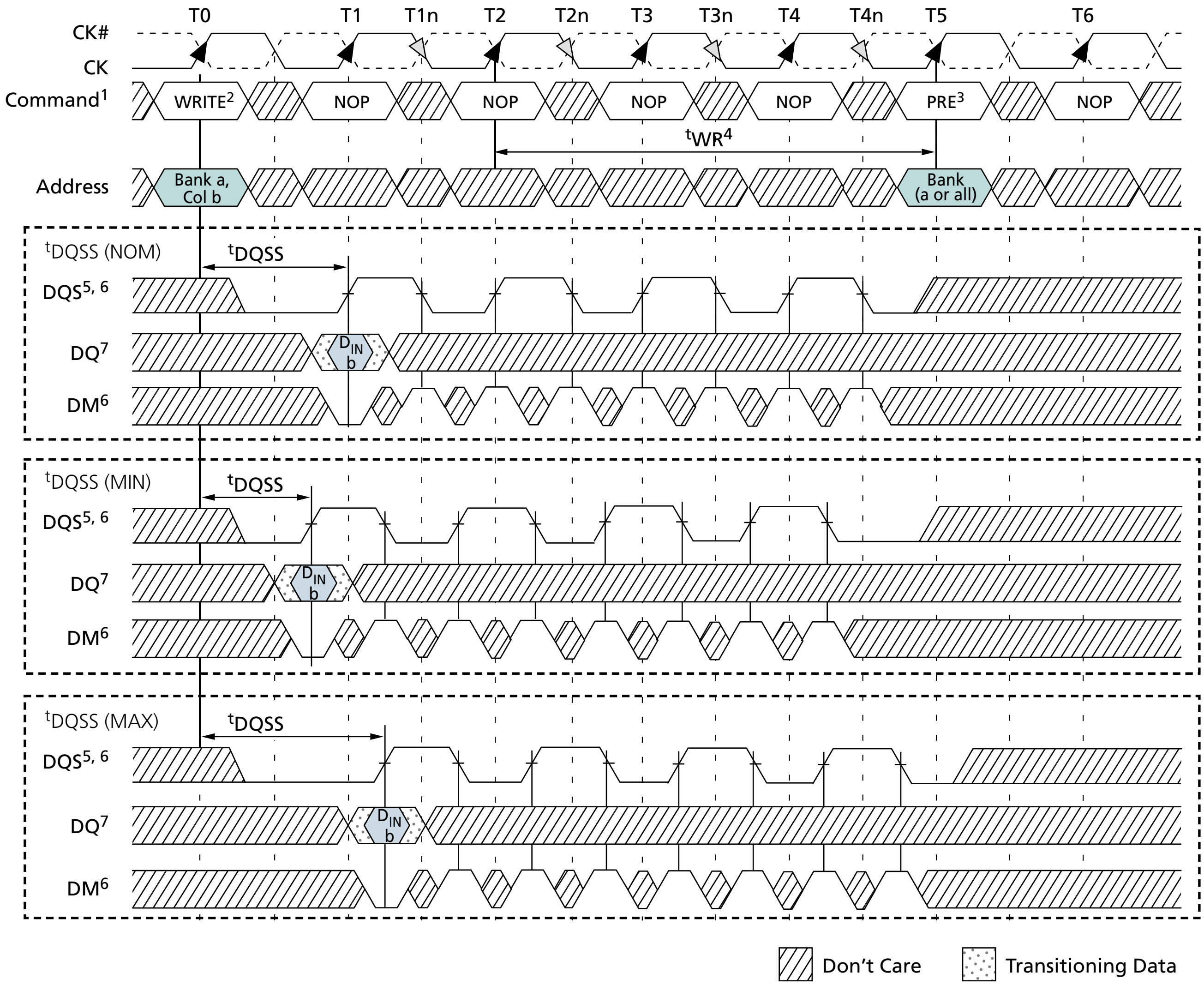
Notes:
1. An uninterrupted burst 4 of is shown.
2. A10 is LOW with the WRITE command (auto precharge is disabled).
3. PRE = PRECHARGE.
4. The PRECHARGE and WRITE commands are to the same device. However, the PRECHARGE and WRITE commands can be to different devices; in this case, ^{t}WR is not required and the PRECHARGE command can be applied earlier.
5. ^{t}WR is referenced from the first positive CK edge after the last data-in pair.
6. $D_{IN}b$ = data-in for column *b*.

Figure 49: WRITE-to-PRECHARGE – Interrupting



Notes:
1. An interrupted burst of 8 is shown; two data elements are written.
2. A10 is LOW with the WRITE command (auto precharge is disabled).
3. PRE = PRECHARGE.
4. ^{t}WR is referenced from the first positive CK edge after the last data-in pair.
5. DQS is required at T4 and T4n to register DM.
6. $D_{IN}b$ = data-in for column *b*.

Figure 50: WRITE-to-PRECHARGE – Odd Number of Data, Interrupting



Notes:
1. An interrupted burst of 8 is shown; one data element is written.
2. A10 is LOW with the WRITE command (auto precharge is disabled).
3. PRE = PRECHARGE.
4. ^{t}WR is referenced from the first positive CK edge after the last data-in pair.
5. DQS is required at T4 and T4n to register DM.
6. If a burst of 4 is used, DQS and DM are not required at T3, T3n, T4, and T4n.
7. $D_{IN}b$ = data-in for column *b*.

PRECHARGE Operation

The PRECHARGE command is used to deactivate the open row in a particular bank or the open row in all banks. The bank(s) will be available for a subsequent row access some specified time (^tRP) after the PRECHARGE command is issued. Input A10 determines whether one or all banks will be precharged, and in the case where only one bank is precharged (A10 = LOW), inputs BA0 and BA1 select the bank. When all banks are precharged (A10 = HIGH), inputs BA0 and BA1 are treated as "Don't Care." After a bank has been precharged, it is in the idle state and must be activated prior to any READ or WRITE commands being issued to that bank. A PRECHARGE command will be treated as a NOP if there is no open row in that bank (idle state), or if the previously open row is already in the process of precharging.

Auto Precharge

Auto precharge is a feature that performs the same individual bank PRECHARGE function described previously, without requiring an explicit command. This is accomplished by using A10 to enable auto precharge in conjunction with a specific READ or WRITE command. A precharge of the bank/row that is addressed with the READ or WRITE command is automatically performed upon completion of the READ or WRITE burst. Auto precharge is nonpersistent; it is either enabled or disabled for each individual READ or WRITE command.

Auto precharge ensures that the precharge is initiated at the earliest valid stage within a burst. This earliest valid stage is determined as if an explicit PRECHARGE command was issued at the earliest possible time without violating ^tRAS (MIN), as described for each burst type in Table 31 (page 65). The READ with auto precharge enabled state or the WRITE with auto precharge enabled state can each be broken into two parts: the access period and the precharge period. The access period starts with registration of the command and ends where ^tRP (the precharge period) begins. For READ with auto precharge, the precharge period is defined as if the same burst was executed with auto precharge disabled, followed by the earliest possible PRECHARGE command that still accesses all the data in the burst. For WRITE with auto precharge, the precharge period begins when ^tWR ends, with ^tWR measured as if auto precharge was disabled. In addition, during a WRITE with auto precharge, at least one clock is required during ^tWR time. During the precharge period, the user must not issue another command to the same bank until ^tRP is satisfied.

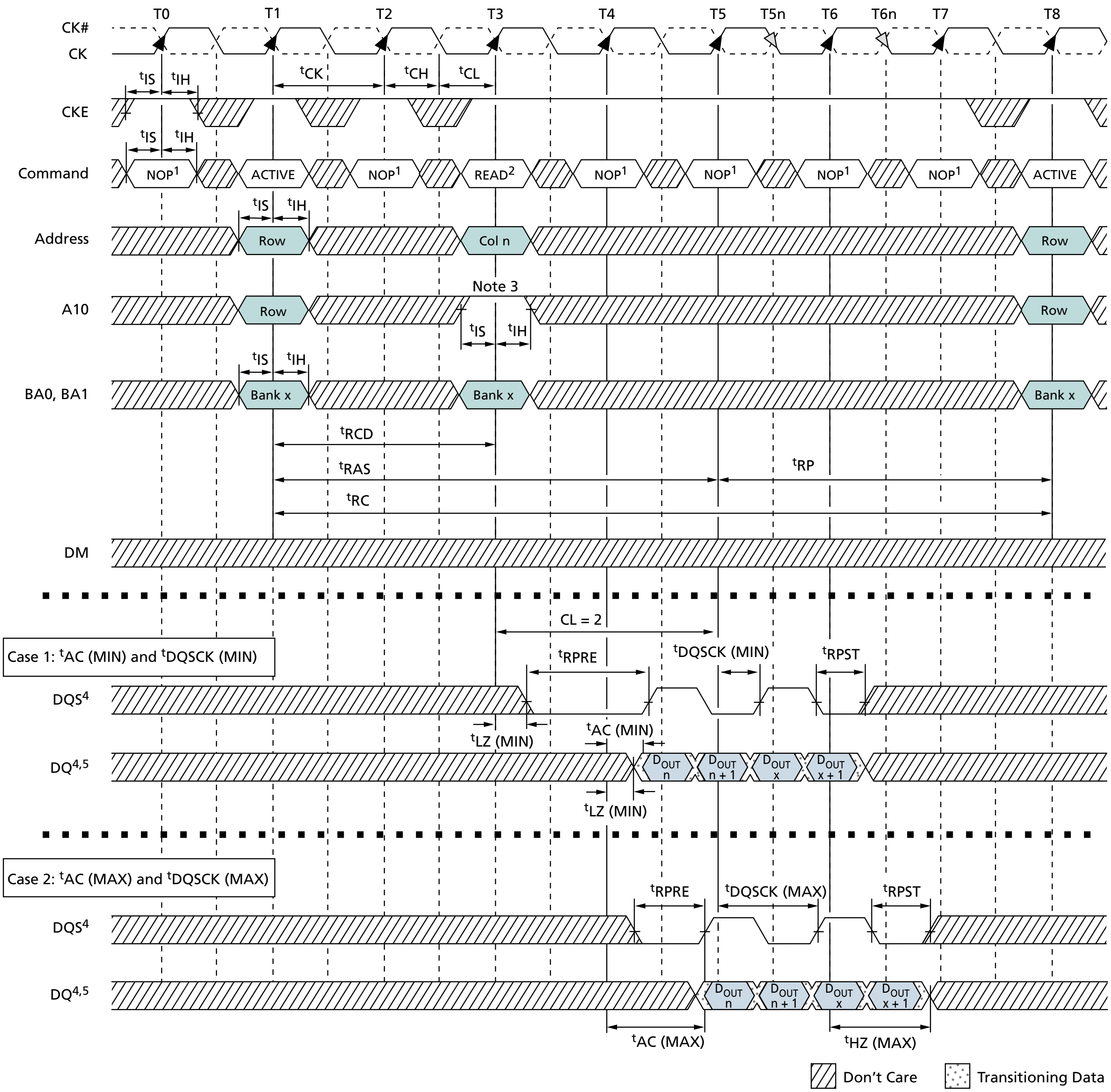
This device supports ^tRAS lock-out. In the case of a single READ with auto precharge or single WRITE with auto precharge issued at ^tRCD (MIN), the internal precharge will be delayed until ^tRAS (MIN) has been satisfied.

Bank READ operations with and without auto precharge are shown in Figure 51 (page 106) and Figure 52 (page 107). Bank WRITE operations with and without auto precharge are shown in Figure 53 (page 108) and Figure 54 (page 109).

Concurrent Auto Precharge

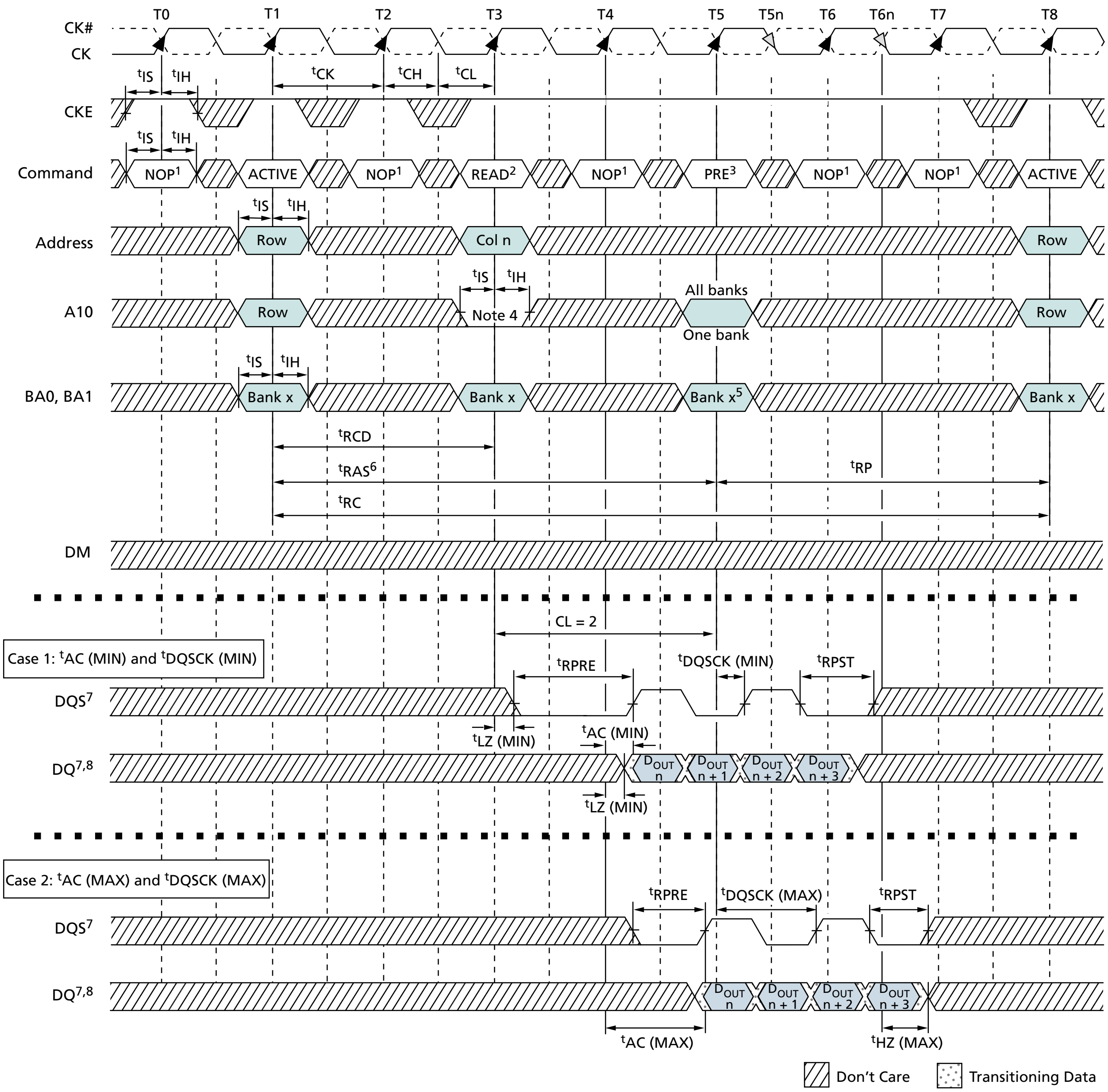
This device supports concurrent auto precharge such that when a READ with auto precharge is enabled or a WRITE with auto precharge is enabled, any command to another bank is supported, as long as that command does not interrupt the read or write data transfer already in process. This feature enables the precharge to complete in the bank in which the READ or WRITE with auto precharge was executed, without requiring an explicit PRECHARGE command, thus freeing the command bus for operations in other banks.

Figure 51: Bank Read – With Auto Precharge



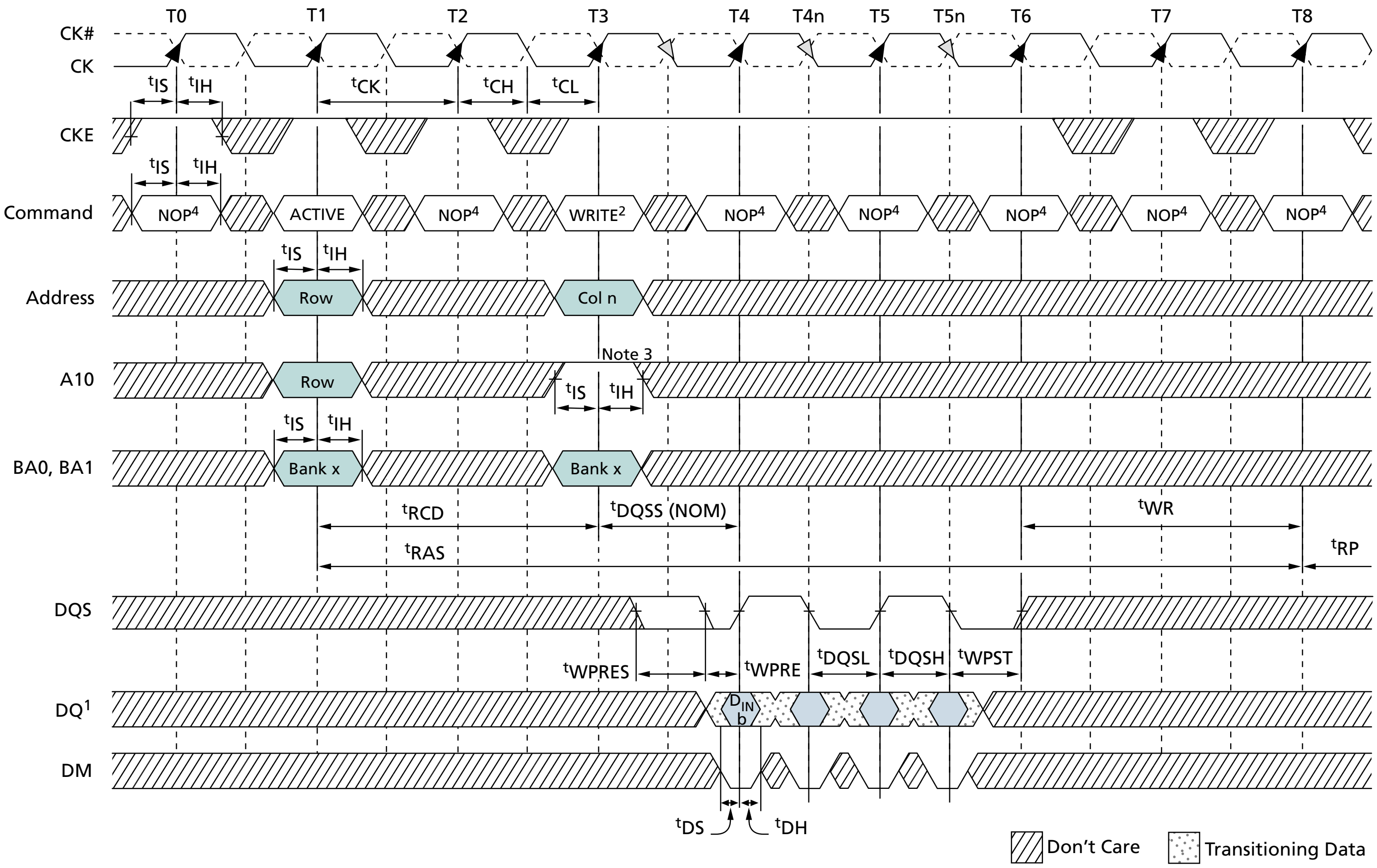
Notes:
1. NOP commands are shown for ease of illustration; other commands may be valid at these times.
2. BL = 4 in the case shown.
3. Enable auto precharge.
4. Refer to Figure 36 (page 89) and Figure 37 (page 90) for detailed DQS and DQ timing.
5. D_{OUT} *n* = data-out from column *n*.

Figure 52: Bank Read – Without Auto Precharge



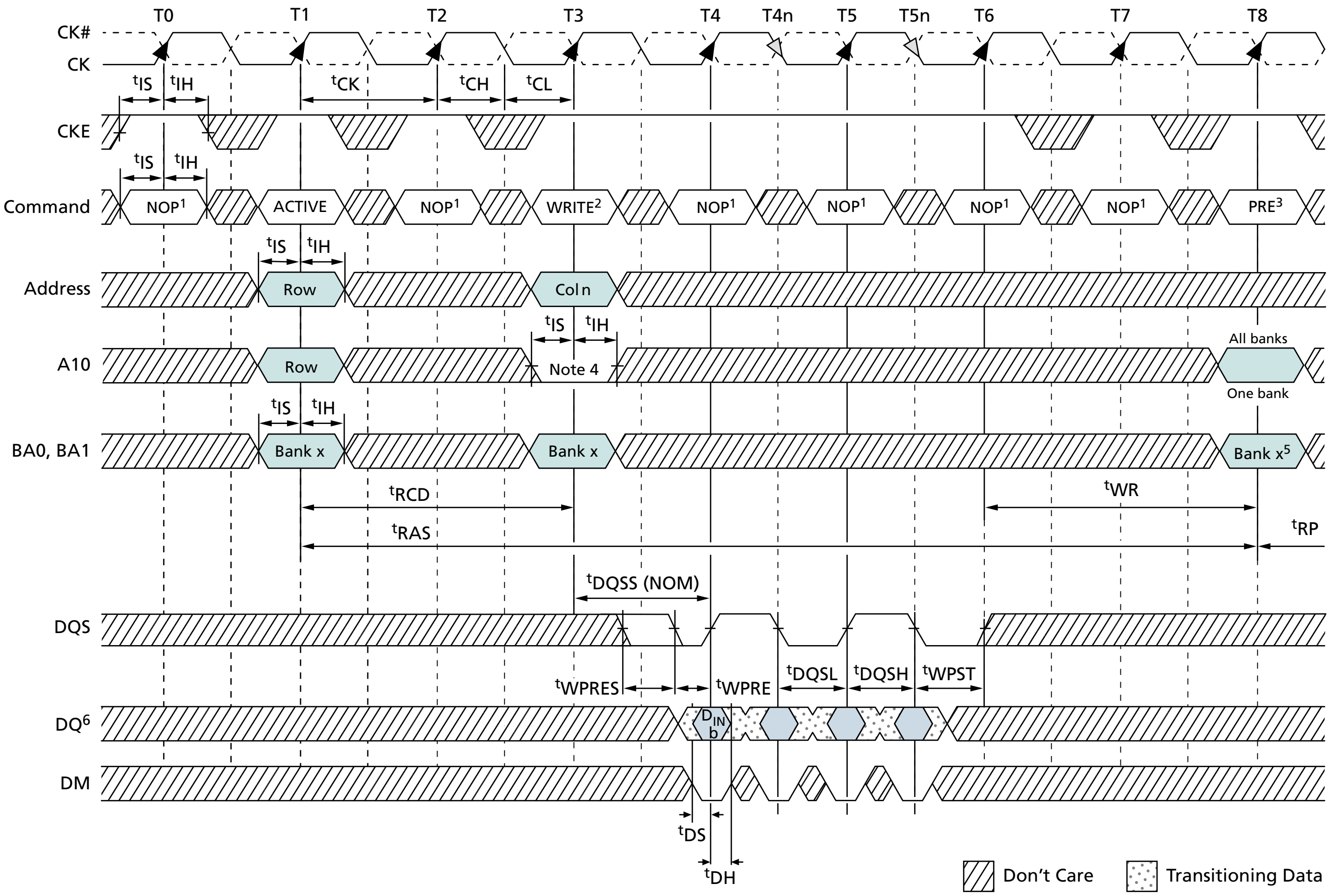
Notes:
1. NOP commands are shown for ease of illustration; other commands may be valid at these times.
2. BL = 4 in the case shown.
3. PRE = PRECHARGE.
4. Disable auto precharge.
5. Bank *x* at T5 is "Don't Care" if A10 is HIGH at T5.
6. The PRECHARGE command can only be applied at T5 if ^tRAS (MIN) is met.
7. Refer to Figure 36 (page 89) and Figure 37 (page 90) for DQS and DQ timing details.
8. $D_{OUT}n$ = data out from column *n*.

Figure 53: Bank Write – With Auto Precharge



Notes:
1. NOP commands are shown for ease of illustration; other commands may be valid at these times.
2. BL = 4 in the case shown.
3. Enable auto precharge.
4. $D_{IN}n$ = data-out from column *n*.

Figure 54: Bank Write – Without Auto Precharge



Notes:
1. NOP commands are shown for ease of illustration; other commands may be valid at these times.
2. BL = 4 in the case shown.
3. PRE = PRECHARGE.
4. Disable auto precharge.
5. Bank x at T8 is "Don't Care" if A10 is HIGH at T8.
6. $D_{OUT}n$ = data-out from column *n*.

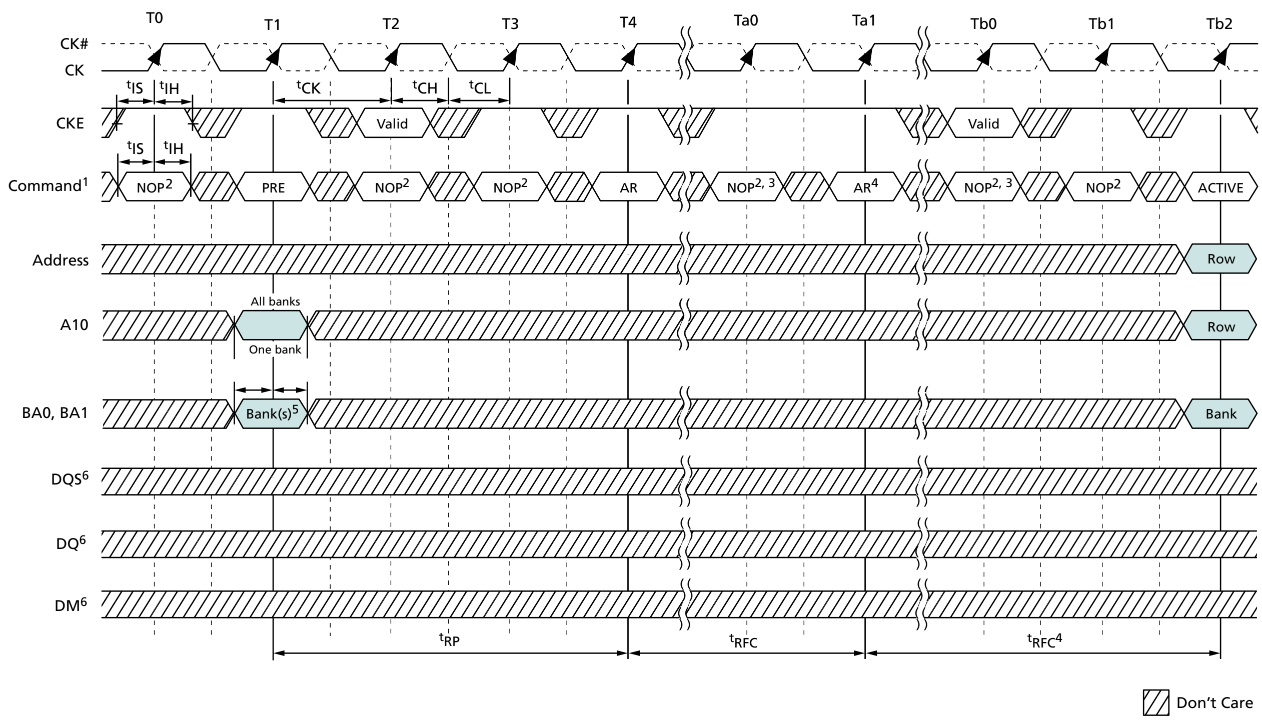
AUTO REFRESH Operation

Auto refresh mode is used during normal operation of the device and is analogous to CAS#-BEFORE-RAS# (CBR) REFRESH in FPM/EDO DRAM. The AUTO REFRESH command is nonpersistent and must be issued each time a refresh is required.

The addressing is generated by the internal refresh controller. This makes the address bits a "Don't Care" during an AUTO REFRESH command.

For improved efficiency in scheduling and switching between tasks, some flexibility in the absolute refresh interval is provided. The auto refresh period begins when the AUTO REFRESH command is registered and ends ^{t}RFC later.

Figure 55: Auto Refresh Mode



Notes:
1. PRE = PRECHARGE; AR = AUTO REFRESH.
2. NOP commands are shown for ease of illustration; other commands may be valid during this time. CKE must be active during clock positive transitions.
3. NOP or COMMAND INHIBIT are the only commands supported until after ^{t}RFC time; CKE must be active during clock positive transitions.
4. The second AUTO REFRESH is not required and is only shown as an example of two back-to-back AUTO REFRESH commands.
5. Bank *x* at T1 is "Don't Care" if A10 is HIGH at this point; A10 must be HIGH if more than one bank is active (for example, must precharge all active banks).
6. DM, DQ, and DQS signals are all "Don't Care"/High-Z for operations shown.

Although it is not a JEDEC requirement, CKE must be active (HIGH) during the auto refresh period to provide support for future functional features. The auto refresh period begins when the AUTO REFRESH command is registered and ends ^{t}RFC later.

SELF REFRESH Operation

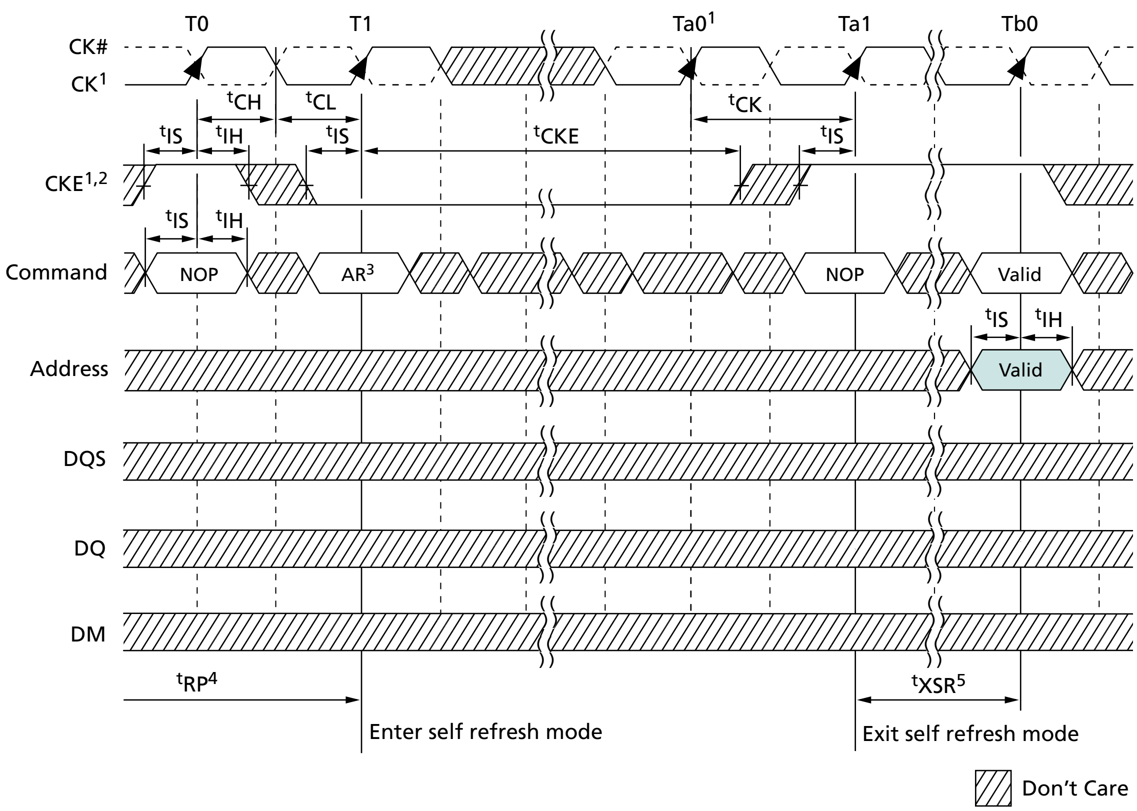
The SELF REFRESH command can be used to retain data in the device while the rest of the system is powered down. When in self refresh mode, the device retains data without external clocking. The SELF REFRESH command is initiated like an AUTO REFRESH command, except that CKE is disabled (LOW). All command and address input signals except CKE are "Don't Care" during self refresh.

During self refresh, the device is refreshed as defined in the extended mode register. (see Partial-Array Self Refresh (page 77).) An internal temperature sensor adjusts the refresh rate to optimize device power consumption while ensuring data integrity. (See Temperature-Compensated Self Refresh (page 76).)

The procedure for exiting self refresh requires a sequence of commands. First, CK must be stable prior to CKE going HIGH. When CKE is HIGH, the device must have NOP commands issued for ^{t}XSR to complete any internal refresh already in progress.

During SELF REFRESH operation, refresh intervals are scheduled internally and may vary. These refresh intervals may differ from the specified ^{t}REFI time. For this reason, the SELF REFRESH command must not be used as a substitute for the AUTO REFRESH command.

Figure 56: Self Refresh Mode



Notes:
1. Clock must be stable, cycling within specifications by Ta0, before exiting self refresh mode.
2. CKE must remain LOW to remain in self refresh.
3. AR = AUTO REFRESH.
4. Device must be in the all banks idle state prior to entering self refresh mode.
5. Either a NOP or DESELECT command is required for ^{t}XSR time with at least two clock pulses.

Power-Down

Power-down is entered when CKE is registered LOW. If power-down occurs when all banks are idle, this mode is referred to as precharge power-down; if power-down occurs when there is a row active in any bank, this mode is referred to as active power-down. Entering power-down deactivates all input and output buffers, including CK and CK# and excluding CKE. Exiting power-down requires the device to be at the same voltage as when it entered power-down and received a stable clock. Note that the power-down duration is limited by the refresh requirements of the device.

When in power-down, CKE LOW must be maintained at the inputs of the device, while all other input signals are "Don't Care." The power-down state is synchronously exited when CKE is registered HIGH (in conjunction with a NOP or DESELECT command). NOP or DESELECT commands must be maintained on the command bus until ^{t}XP is satisfied. See Figure 58 (page 114) for a detailed illustration of power-down mode.

Figure 57: Power-Down Entry (in Active or Precharge Mode)

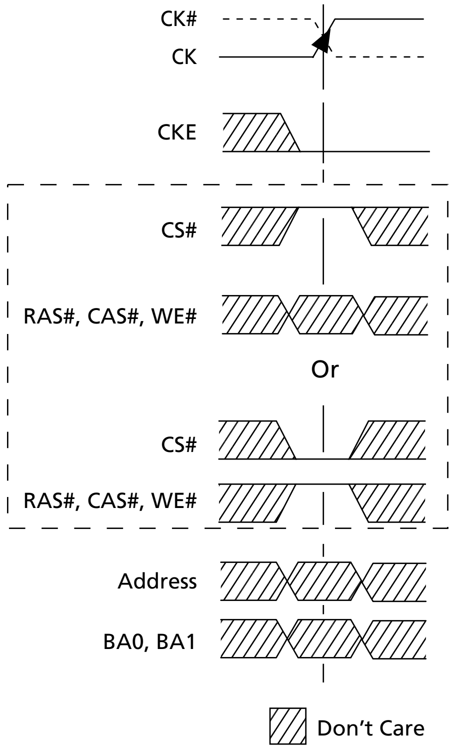
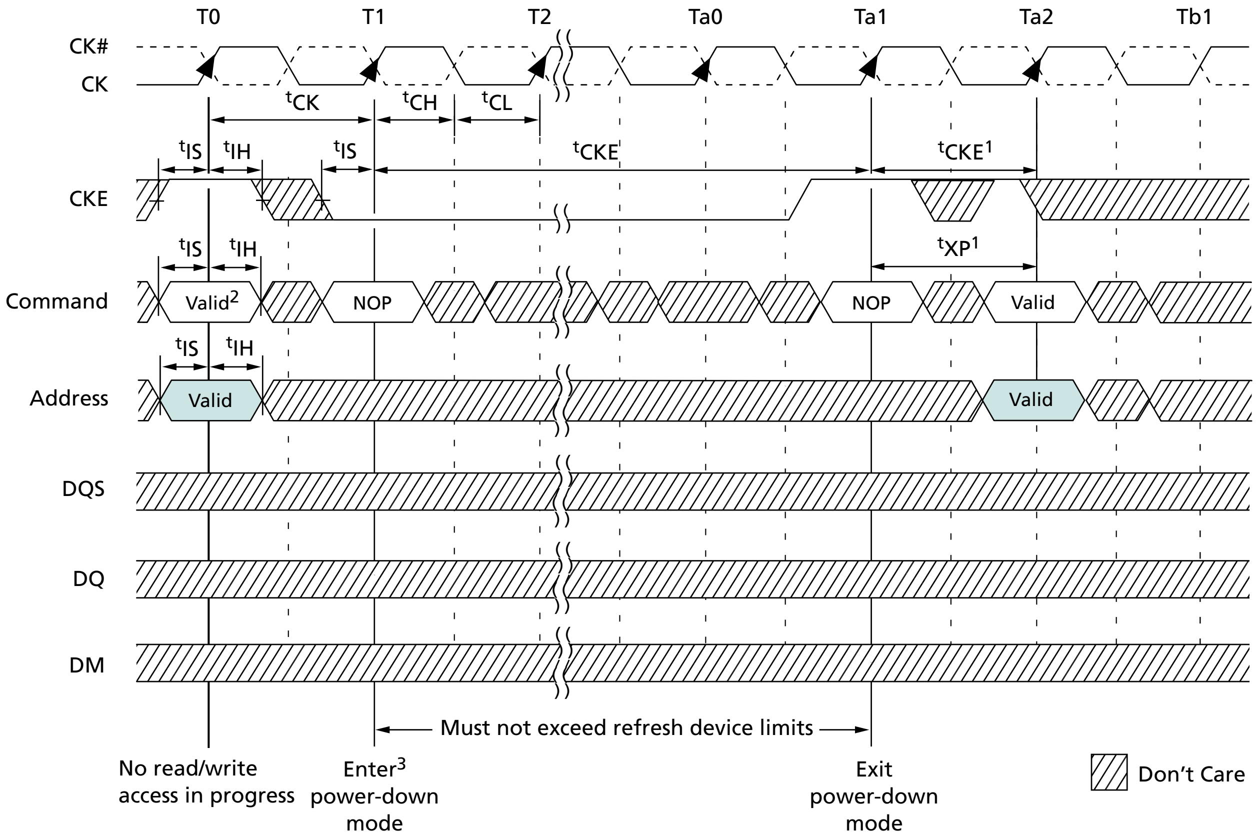


Figure 58: Power-Down Mode (Active or Precharge)



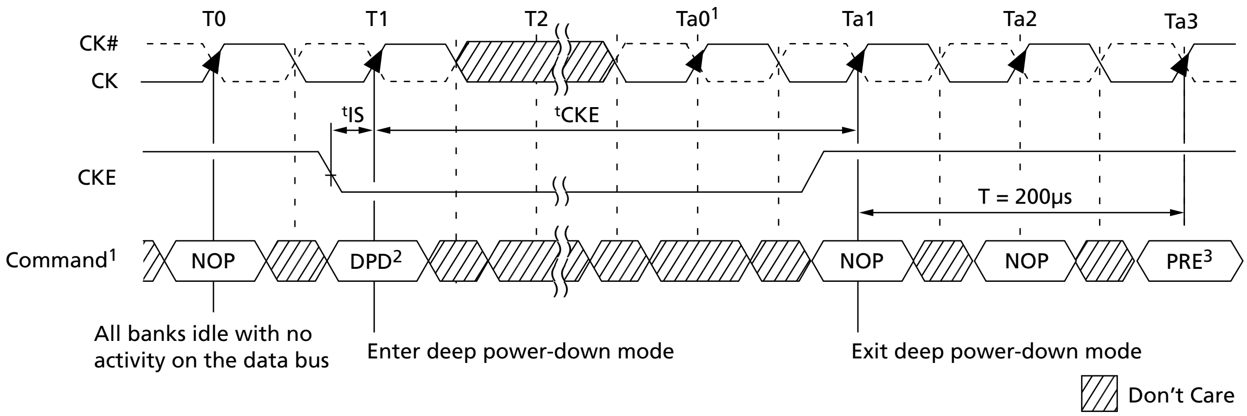
Notes:
1. tCKE applies if CKE goes LOW at Ta2 (entering power-down); tXP applies if CKE remains HIGH at Ta2 (exit power-down).
2. If this command is a PRECHARGE (or if the device is already in the idle state), then the power-down mode shown is precharge power-down. If this command is an ACTIVE (or if at least 1 row is already active), then the power-down mode shown is active power-down.
3. No column accesses can be in progress when power-down is entered.

Deep Power-Down

Deep power-down (DPD) is an operating mode used to achieve maximum power reduction by eliminating power to the memory array. Data will not be retained after the device enters DPD mode.

Before entering DPD mode the device must be in the all banks idle state with no activity on the data bus (tRP time must be met). DPD mode is entered by holding CS# and WE# LOW with RAS# and CAS# HIGH at the rising edge of the clock while CKE is LOW. CKE must be held LOW to maintain DPD mode. The clock must be stable prior to exiting DPD mode. To exit DPD mode, assert CKE HIGH with either a NOP or DESELECT command present on the command bus. After exiting DPD mode, a full DRAM initialization sequence is required.

Figure 59: Deep Power-Down Mode



Notes:
1. Clock must be stable prior to CKE going HIGH.
2. DPD = deep power-down.
3. Upon exit of deep power-down mode, a full DRAM initialization sequence is required.

Clock Change Frequency

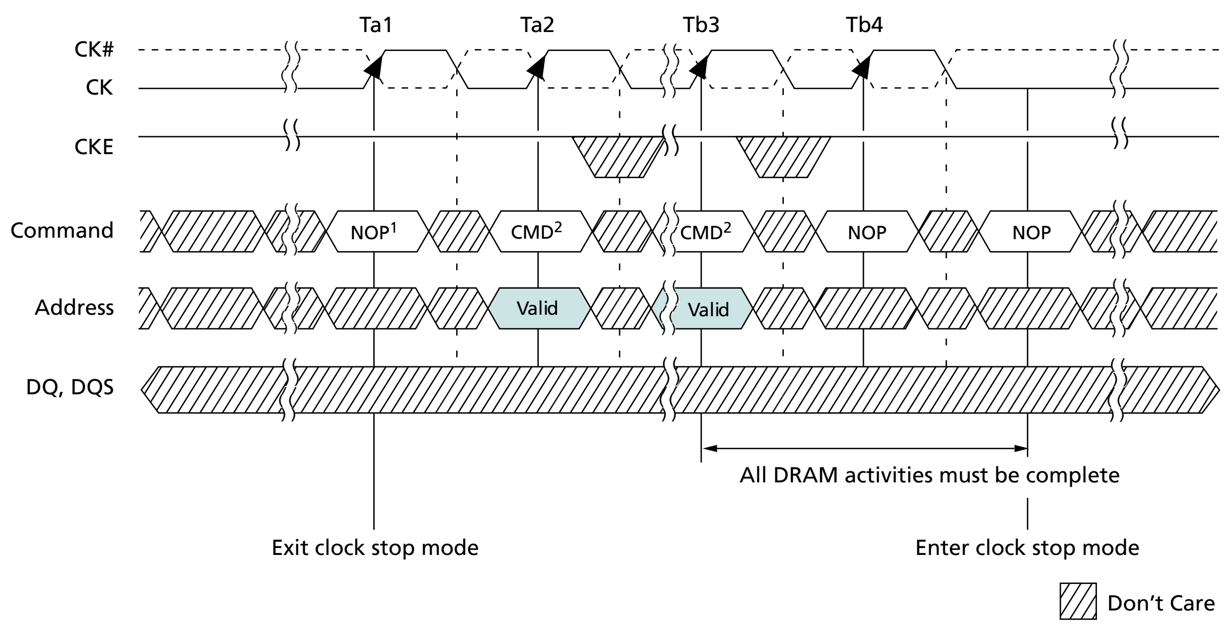
One method of controlling the power efficiency in applications is to throttle the clock that controls the device. The clock can be controlled by changing the clock frequency or stopping the clock.

The device enables the clock to change frequency during operation only if all timing parameters are met and all refresh requirements are satisfied.

The clock can be stopped altogether if there are no DRAM operations in progress that would be affected by this change. Any DRAM operation already in process must be completed before entering clock stop mode; this includes the following timings: ^{t}RCD, ^{t}RP, ^{t}RFC, ^{t}MRD, ^{t}WR, and ^{t}RPST. In addition, any READ or WRITE burst in progress must be complete. (See READ Operation and WRITE Operation.)

CKE must be held HIGH with CK = LOW and CK# = HIGH for the full duration of the clock stop mode. One clock cycle and at least one NOP or DESELECT is required after the clock is restarted before a valid command can be issued.

Figure 60: Clock Stop Mode



Notes:
1. Prior to Ta1, the device is in clock stop mode. To exit, at least one NOP is required before issuing any valid command.
2. Any valid command is supported; device is not in clock suspend mode.

Revision History

Rev. F – 6/12

- Updated CSD register [119:112] from 0Fh 10ms to 5Fh 50ms in CSD Register

Rev. E, Production – 2/12

- Changed status to production.

Rev. D, Advance – 1/12

- In the MLC e·MMC section
  – Added State Diagrams section.
  – Added notes 3 and 4 to the ECSD Register Field Parameters table.

Rev. C, Advance – 11/11

- Updated content.

Rev. B, Advance – 9/11

- Deleted part number MT29KZZZ4D4RGFAK-75 W.6Y4 on front page.

Rev. A, Advance – 8/11

- Initial release.

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